

PCTEST ENGINEERING LABORATORY, INC.

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HEARING AID COMPATIBILITY

Applicant Name:

Samsung Electronics Co., Ltd. 129, Samsung-ro, Maetan dong, Yeongtong-gu, Suwon-si Gyeonggi-do 16677, Korea Date of Testing: 06/24/2019 - 06/28/2019 Test Site/Location: PCTEST Lab, Columbia, MD, USA Test Report Serial No.: 1M1907090118-12.A3L Date of Issue: 07/29/2019

FCC ID:

A3LSMF900F

APPLICANT:

SAMSUNG ELECTRONICS CO., LTD.

Scope of Test: Application Type: FCC Rule Part(s): HAC Standard:

DUT Type: Model: Test Device Serial No.: Class II Permissive Change(s): RF Emissions Testing Class II Permissive Change CFR §20.19(b) ANSI C63.19-2011 285076 D01 HAC Guidance v05 285076 D02 T-Coil testing for CMRS IP v03 Portable Handset SM-F900F *Pre-Production Sample* [S/N: 53436, 55399] See FCC Change Document

C63.19-2011 HAC Category:

M4 (RF EMISSIONS CATEGORY)

This wireless portable device has been shown to be hearing-aid compatible under the above rated category, specified in ANSI/IEEE Std. C63.19-2011 and has been tested in accordance with the specified measurement procedures. Hearing-Aid Compatibility is based on the assumption that all production units will be designed electrically identical to the device tested in this report. Test results reported herein relate only to the item(s) tested. North America bands only.

I attest to the accuracy of data. All measurements reported herein were performed by me or were made under my supervision and are correct to the best of my knowledge and belief. I assume full responsibility for the completeness of these measurements and vouch for the qualifications of all persons taking them.

Randy Ortanez President



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1. INTRODUCTION

On July 10, 2003, the Federal Communications Commission (FCC) adopted new rules requiring wireless manufacturers and service providers to provide digital wireless phones that are compatible with hearing aids. The FCC has modified the exemption for wireless phones under the Hearing Aid Compatibility Act of 1998 (HAC Act) in WT Docket 01-309 RM-8658¹ to extend the benefits of wireless telecommunications to individuals with hearing disabilities. These benefits encompass business, social and emergency communications, which increase the value of the wireless network for everyone. An estimated more than 10% of the population in the United States show signs of hearing impairment and of that fraction, almost 80% use hearing aids. Approximately 500 million people worldwide suffer from hearing loss.

Compatibility Tests Involved:

The standard calls for wireless communications devices to be measured for:

- RF Electric-field emissions
- T-coil mode, magnetic-signal strength in the audio band
- T-coil mode, magnetic-signal frequency response through the audio band
- T-coil mode, magnetic-signal and noise articulation index

The hearing aid must be measured for:

- RF immunity in microphone mode
- RF immunity in T-coil mode

In the following tests and results, this report includes the evaluation for a wireless communications device.



Figure 1-1 Hearing Aid *in-vitu*

¹ FCC Rule & Order, WT Docket 01-309 RM-8658

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2. DUT DESCRIPTION



FCC ID:	A3LSMF900F		
Manufacturer:	Samsung Electronics Co., Ltd.		
	129, Samsung-ro, Maetan dong,		
	Yeongtong-gu, Suwon-si		
	Gyeonggi-do 16677, Korea		
Model:	SM-F900F		
Serial Number:	53436, 55399		
Antenna Configurations:	Internal Antenna		
DUT Type:	Portable Handset		
Class II Permissive Change(s):	See FCC Change Document		

I. Power Reduction for WIFI

This device uses an independent fixed level power reduction mechanism for all WIFI operations during voice or VoIP held to ear scenarios. Reduced powers were used to evaluate for low-power exemption in Section 9.II for WIFI. Detailed descriptions of the power reduction mechanism are included in the operational description.

II. LTE Band Selection

This device supports the following pair of LTE bands with similar frequencies: LTE B2 & B25, B5 & B26, and B4 & B66. These pairs of LTE bands have the same target power and share the same transmission paths. Since the supported frequency span for the smaller LTE bands are completely covered by the larger LTE bands, only the larger LTE bands (LTE B25, B26, and B66) were evaluated for hearing-aid compliance.

III. Device Serial Numbers

Several samples with identical hardware were used to support HAC testing. The manufacturer has confirmed that the device(s) tested have the same physical, mechanical, and thermal characteristics are within operational tolerances expected for production units. The serial numbers used for each test are indicated alongside the results in Section 11.

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Air-Interface	Band (MHz)	Type Transport	HAC Tested	Simultaneous But Not Tested	Name of Voice Service
GSM	850 1900	vo	Yes	Yes: WIFI or BT	CMRS Voice
	GPRS/EDGE	VD	No ¹	Yes: WIFI or BT	Google Duo
	850				
LINATO	1700	VD	No ¹	Yes: WIFI or BT	CMRS Voice
UMTS	1900				
	HSPA	VD	No ¹	Yes: WIFI or BT	Google Duo
	680 (B71)		No ^{1 2}		
	700 (B12)		No ¹		VoLTE, Google Duo
	780 (B13)			Yes: WIFI or BT	
LTE (FDD)	790 (B14)	VD			
	850 (B5)				
	850 (B26)				
	1700 (B4)				
	1700 (B66)				
	1900 (B2)				
	1900 (B25)				
	2300 (B30)				
	2500 (B7)				
LTE (TDD)	2600 (B38)	VD	Yes	Yes: WIFI or BT	VoLTE, Google Duo
	2600 (B41)	VD	Tes		VOLTE, GOOgle Duo
	2450				
	5200 (U-NII 1)				
WIFI	5300 (U-NII 2A)	VD	No ¹	Yes: GSM, UMTS, or LTE	VoWIFI, Google Duo
	5500 (U-NII 2C)				
	5800 (U-NII 3)				
BT	2450	DT	No	Yes: GSM, UMTS, or LTE	N/A
vpe Transport Ο = Voice Only Γ = Digital Dat		Voice Services		or MIF and low-power exemption. ile outside the scope of ANSI C63.19 and FCC HA	C regulations, was additionally

tested according to the existing HAC procedures with currently available test equipment.

VD = CMRS and/or IP Voice over Data Transport

Table 2-1 A3LSMF900F HAC Air Interfaces

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3. ANSI/IEEE C63.19 PERFORMANCE CATEGORIES

I. RF EMISSIONS

The ANSI Standard presents performance requirements for acceptable interoperability of hearing aids with wireless communications devices. When these parameters are met, a hearing aid operates acceptably in close proximity to a wireless communications device.

Category	Telephone RF Parameters				
Near field Category	E-field emissions CW dB(V/m)				
	f < 960 MHz				
M1	50 to 55				
M2	45 to 50				
M3	40 to 45				
M4	< 40				
f > 960 MHz					
M1	40 to 45				
M2	35 to 40				
M3	30 to 35				
M4	< 30				
Table 3-1WD near-field categories as defined in ANSI C63.19-2011					

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4. SYSTEM SPECIFICATIONS

EF3DV3 E-Field Probe Description

Construction:	One dipole parallel, two dipoles normal to probe axis
Calibration:	Built-in shielding against static charges In air from 30 MHz to 6.0 GHz (absolute accuracy ±5.1%, k=2)
Frequency:	30 MHz to > 6 GHz;
	Linearity: ± 0.2 dB (30 MHz to 6 GHz)
Directivity	± 0.2 dB in air (rotation around probe axis)
-	± 0.4 dB in air (rotation normal to probe axis)
Dynamic Range	2 V/m to > 1000 V/m
, 0	(M3 or better device readings fall well below diode
	compression point)
Linearity:	± 0.2 dB
Dimensions	Overall length: 337 mm (Tip: 20 mm)
	Tip diameter: 4.0 mm (Body: 12 mm)
	Distance from probe tip to dipole centers: 1.5 mm

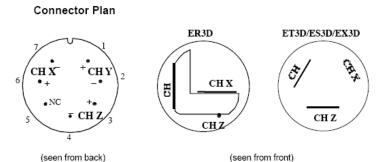


Figure 4-1 E-field Free-space Probe

Probe Tip Description

HAC field measurements take place in the close near field with high gradients. Increasing the measuring distance from the source will generally decrease the measured field values (in case of the validation dipole approx. 10% per mm).

The electric field probes have an irregular internal geometry because it is physically not possible to have the 3 orthogonal sensors situated with the same center. The effect of the different sensor centers is accounted for in the HAC uncertainty budget ("sensor displacement").



The antistatic shielding inside the probe is connected to the probe connector case.

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Instrumentation Chain

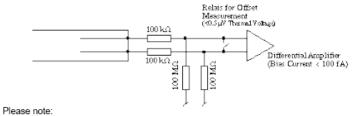
Equation 1 Conversion of Connector Voltage *u_i* to E-Field *E_i*

$$E_i = \sqrt{\frac{u_i + (u_i^2 \cdot CF)/(DCP)}{Norm_i \cdot ConvF}}$$

whereby

Ei:	electric field in V/m
Uj.	voltage of channel i at the connector in μV
Norm	sensitivity of channel i in µV/(V/m) ²
ConvF:	enhancement factor in liquid (ConvF=1 for Air)
DCP:	diode compression point in µV
CF:	signal crest factor (peak power/average power)

Conditions of Calibration



a lower input impedance of the amplifier will result in different sensitivity factors Norm, and DCP

larger bias currents will cause higher offset

Probe Response to Frequency

The E-field sensors have inherently a very flat frequency response. They are calibrated with a number of frequencies resulting in a common calibration factor, with the frequency behavior documented in the calibration certificate (See also below).

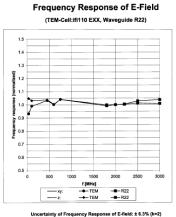


Figure 4-2 E-Field Probe Frequency Response

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SPEAG Robotic System

E-field measurements are performed using the DASY5 automated dosimetric assessment system. The DASY5 is made by Schmid & Partner Engineering AG (SPEAG) in Zurich. Switzerland and consists of high precision robotics system (Staubli), robot controller, Intel CORE i7 computer, near-field probe, probe alignment sensor, and the HAC phantom. The robot is a six-axis industrial robot performing precise movements to position the probe to the location (points) of maximum electromagnetic field (EMF).



Figure 4-3 SPEAG Robotic System

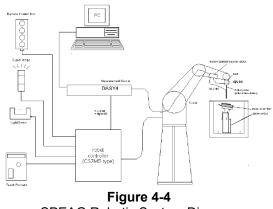
System Hardware

A cell controller system contains the power supply, robot controller, teach pendant (Joystick), and a remote control used to drive the robot motors. The PC consists of the computer with operating system and RF Measurement Software DASY5 v52.8 (with HAC Extension), A/D interface card, monitor, mouse, and keyboard. The Staubli Robot is connected to the cell controller to allow software manipulation of the robot. A data acquisition electronic (DAE) circuit that performs the signal amplification, signal multiplexing, AD-conversion, offset measurements, mechanical surface detection, collision detection, etc. is connected to the Electro-optical coupler (EOC). The EOC performs the conversion from the optical into digital electric signal of the DAE and transfers data to the PC plug-in card.

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System Electronics

The DAE consists of a highly sensitive electrometer-grade preamplifier with auto-zeroing, a channel and gain-switching multiplexer, a fast 16 bit AD-converter and a command decoder and control logic unit. Transmission to the PC-card is accomplished through an optical downlink for data and status information and an optical uplink for commands and clock lines. The mechanical probe mounting device includes two different sensor systems for frontal and sidewise probe contacts. They are also used for mechanical surface detection and probe collision detection. The robot uses its own controller with a built in VME-bus computer.



SPEAG Robotic System Diagram

DASY5 Instrumentation Chain

The first step of the evaluation is a linearization of the filtered input signal to account for the compression characteristics of the detector diode. The compensation depends on the input signal, the diode type and the DC-transmission factor from the diode to the evaluation electronics. If the exciting field is pulsed, the crest factor of the signal must be known to correctly compensate for peak power. The formula for each channel can be given as:

$$V_i = U_i + U_i^2 \cdot \frac{cf}{dcp_i}$$

with	V_i	= compensated signal of channel i	(i = x, y, z)
	U_i	= input signal of channel i	(i = x, y, z)
	cf	= crest factor of exciting field	(DASY parameter)
	dcp_i	= diode compression point	(DASY parameter)

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From the compensated input signals the primary field data for each channel can be evaluated:

E – fieldprobes :
$$E_i = \sqrt{\frac{V_i}{Norm_i \cdot ConvF}}$$

with
$$V_i$$
 = compensated signal of channel i (i = x, y, z)
 $Norm_i$ = sensor sensitivity of channel i (i = x, y, z)
 $\mu V/(V/m)^2$ for E-field Probes
 $ConvF$ = sensitivity enhancement in solution
 E_i = electric field strength of channel i in V/m

The RSS value of the field components gives the total field strength (Hermitian magnitude):

$$E_{tot} = \sqrt{E_x^2 + E_y^2 + E_z^2}$$

The primary field data are used to calculate the derived field units.

The measurement/integration time per point, as specified by the system manufacturer is >500ms.

The signal response time is evaluated as the time required by the system to reach 90% of the expected final value after an on/off switch of the power source with an integration time of 500ms and a probe response time of <5 ms. In the current implementation, DASY5 waits longer than 100ms after having reached the grid point before starting a measurement, i.e., the response time uncertainty is negligible.

If the device under test does not emit a CW signal, the integration time applied to measure the electric field at a specific point may introduce additional uncertainties due to the discretization. The tolerances for the different systems had the worst-case of 2.6%.

Environmental Conditions

Environmental conditions such as temperature and relative humidity are monitored to ensure there are no impacts on system specifications. Proper voltage and power line frequency conditions are maintained with three phase power sources. Environmental noise and reflections are monitored through system checks.

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5. TEST PROCEDURE

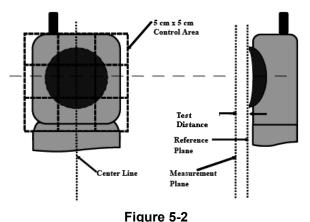
I. RF EMISSIONS

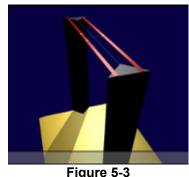
Test Instructions Confirm proper operation of ≻ probes and instrumentation Position WD \geq **Configure WD TX operation** ≻ Per 5.5.1.2 (a-c) Initialize field probe \triangleright ≻ Scan Area Per 5.5.1.2 (d-f) Identify exclusion area. \geq \geq Rescan or reanalyze open area to determine maximum Indirect method: Add the MIF ≻ to the maximum steady state rms field strength and record **RF** Audio Interference Level, in dB(V/m) Per 5.5.1.2 (g-h) & 5.5.1.3 Identify and record the ≻ category Per 5.5.1.2 (i-j)

Figure 5-1 RF Emissions Flow Chart

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Test Setup





HAC Phantom

E-Field Emissions Test Setup Diagram (See Test Photographs for actual WD scan grid overlay)

RF Emissions Test Procedure:

The following illustrate a typical RF emissions test scan over a wireless communications device:

- 1. Proper operation of the field probe, probe measurement system, other instrumentation, and the positioning system was confirmed.
- 2. WD is positioned in its intended test position, acoustic output point of the device perpendicular to the field probe.
- 3. The WD operation for maximum rated RF output power was configured and confirmed with the base station simulator, at the test channel and other normal operating parameters as intended for the test. The battery was ensured to be fully charged before each test.
- 4. The center sub-grid was centered over the center of the acoustic output (also audio band magnetic output, if applicable). The WD audio output was positioned tangent (as physically possible) to the measurement plane.
- 5. A surface calibration was performed before each setup change to ensure repeatable spacing and proper maintenance of the measurement plane using the HAC Phantom.
- 6. The measurement system measured the field strength at the reference location.
- 7. Measurements at 2mm or 5mm increments in the 5 x 5 cm region were performed at a distance 15 mm from the center point of the probe measurement element to the WD. A 360° rotation about the azimuth axis at the maximum interpolated position was measured. For the worst-case condition, the peak reading from this rotation was used in re-evaluating the HAC category.
- 8. The system performed a drift evaluation by measuring the field at the reference location. If the power drift deviated by more than 5%, the HAC test and drift measurements were repeated.

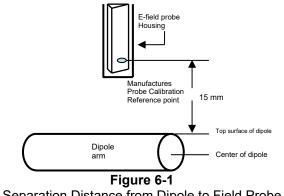
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6. SYSTEM CHECK

System Check Parameters I.

The input signal was an un-modulated continuous wave. The following points were taken into consideration in performing this check:

- Average Input Power P = 100mW RMS (20dBm RMS) after adjustment for return loss
- The test fixture must meet the 2 wavelength separation criterion •
- The proper measurement of the 15 mm probe to dipole separation, which is measured from top surface of the dipole to the calibration reference point of the sensor, defined by the probe manufacturer is shown in the following diagram:



Separation Distance from Dipole to Field Probe

RF power was recorded using both an average reading meter and a peak reading meter. Readings of the probe are provided by the measurement system.

To assure proper operation of the near-field measurement probe the input power to the dipole shall be commensurate with the full rated output power of the wireless device [e.g. - for a cellular phone wireless device the average peak antenna input power will be on the order of 100mW (20dBm) RMS] after adjustment for any mismatch.

II. Validation Procedure

A dipole antenna meeting the requirements given in C63.19 was placed in the position normally occupied by the WD.

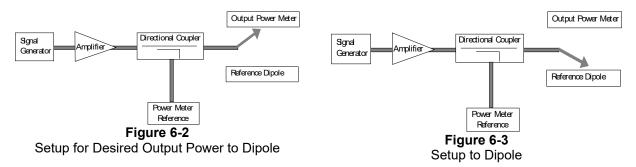
The length of the dipole was scanned, and the average peak value was recorded.

Measurement of CW

Using the near-field measurement system, scan the antenna over the radiating dipole and record the greatest field reading observed. Due to the nature of E-fields about free-space dipoles, the two E-field peaks measured over the dipole are averaged to compensate for non-parallelity of the setup (see manufacturer method on dipole calibration certificates, page 2). Field strength measurements shall be made only when the probe is stationary.

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RF power was recorded using both an average and a peak power reading meter.

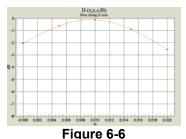


Using this setup configuration, the signal generator was adjusted for the desired output power (100mW) at a specified frequency. The reference power from the coupled port of the directional coupler is recorded. Next, the output cable is connected to the reference dipole, as shown in Figure 6-3.

The input signal level was adjusted until the reference power from the coupled port of the directional coupler was the same as previously recorded, to compensate for the impedance mismatch between the output cable and the reference dipole. To assure proper operation of the near-field measurement probe the input power to the reference dipole was verified to the full rated output power of the wireless device. The dipole was secured in a holder in a manner to meet the 20 dB reflection. The near-field measurement probe was positioned over the dipole. The antenna was scanned over the appropriate sized area to cover the dipole from end to end. SPEAG uses 2D interpolation algorithms between the measured points. Please see below two dimensional plots showing that the interpolated values interpolate smoothly between 5mm steps for a free-space RF dipole:



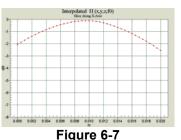
2-D Raw Data from scan along dipole axis



2-D Raw Data from scan along transverse axis



2-D Interpolated points from scan along dipole axis



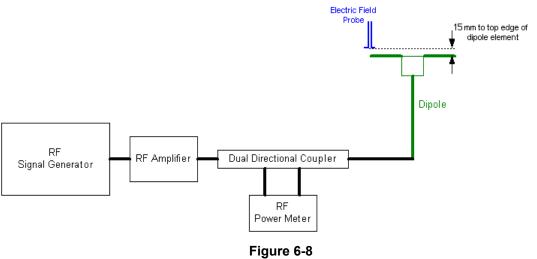
2-D Interpolated points from scan along transverse axis

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III. System Check Results

Validation Results

Date	Frequency (MHz)	Probe S/N	DAE S/N	Dipole S/N	Input Power (dBm)	E-field Result (V/m)	Target Field (V/m)	% Deviation
	835	4035	1415	1003	20.0	105.8	105.2	0.6%
6/24/2019	1880	4035	1415	1137	20.0	86.8	87.8	-1.2%
	2600	4035	1415	1012	20.0	85.8	85.2	0.7%



System Check Setup

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7. MODULATION INTERFERENCE FACTOR

I. Measuring Modulation Interference Factors

For any specific fixed and repeatable modulated signal, a modulation interference factor (MIF, expressed in dB) may be determined that relates its interference potential to its steady-state RMS signal level or average power level. This factor is a function only of the audio-frequency amplitude modulation characteristics of the signal and is the same for field-strength and conducted power measurements. The MIF is valid only for a specific repeatable audio-frequency amplitude modulation characteristic; any change in modulation characteristic requires determination and application of a new MIF.

The MIF may be determined using a radiated RF field or a conducted RF signal:

- a. Using RF illumination or conducted coupling, apply the specific modulated signal in question to the measurement system at a level within its confirmed operating dynamic range.
- b. Measure the steady-state RMS level at the output of the fast probe or sensor.
- c. Measure the steady-state average level at the weighting output.
- d. Without changing the square-law detector or weighting system, and using RF illumination or conducted coupling, substitute for the specific modulated signal a 1 kHz, 80% amplitude modulated carrier at the same frequency and adjust its strength until the level at the weighting output equals the step c) measurement.
- e. Without changing the carrier level from step d), remove the 1 kHz modulation and again measure the steady-state RMS level indicated at the output of the fast probe or sensor.
- f. The MIF for the specific modulation characteristic is provided by the ratio of the step e) measurement to the step b) measurement, expressed in dB (20 × log[(step e)/(step b)]).

The following procedure was used to measure the MIF using the SPEAG Audio Interference Analyzer (AIA), Type No: SE UMS 170 CB, Serial No.: 1010:

- 1. The device was placed into a simulated call using a base station simulator or set to transmit using test software for a given mode.
- 2. The device was then set to continuously transmit at maximum power.
- 3. Using a coupler if needed, the device output signal was connected to the RF In port of the AIA, which was connected to a desktop computer. Alternatively, a radiated RF signal may be used with the AIA's built-in antenna.
- 4. The MIF measurement procedure in the DASY software was run, and the resulting MIF value was recorded.
- 5. Steps 1-4 were repeated for all CMRS air interfaces, frequency bands, and modulations.

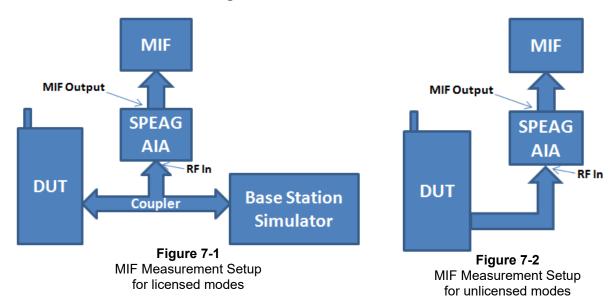
The modulation interference factors obtained were applied to readings taken of the actual wireless device in order to obtain an accurate audio interference level reading using the formula:

Audio Interference Level [dB(V/m)] = 20 * log[Raw Field Value (V/m)] + MIF (dB)

Because the MIF value is output power independent, MIF values for a given mode should be constant across all devices; however, per C63.19-2011 §D.7, MIF values should be measured for each device being evaluated. The voice modes for this device have been investigated in this section of the report.

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II. MIF Measurement Block Diagrams



III. Measured Modulation Interference Factors:

Table 7-1										
GSM Modulation Interference Factors ¹										
Мо	do		GSM850		GSM1900					
IVIC	ode	128	128 190 251			661	810			
GSM	Voice	3.53	3.53	3.53	3.51	3.51	3.50			
	EDGE	3.68	3.66	3.66	3.56	3.53	3.50			

Table 7-2							
UMTS Modulation Interference Factors ¹							

M	Mode UMTS V				UMTS IV		UMTS II			
Woue		4132	4183	4233	1312	1412	1513	9262	9400	9538
	12.2 kbps RMC	-23.05	-23.26	-23.32	-23.40	-23.18	-23.53	-22.75	-23.82	-22.67
UMTS	12.2 kbps AMR	-24.00	-23.79	-23.45	-23.81	-23.16	-23.05	-23.15	-23.65	-23.27
	HSUPA Subtest1	-22.68	-22.69	-22.26	-22.22	-22.02	-22.62	-22.77	-23.10	-22.96

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

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LTE Band	Frequency [MHz]	Channel	Bandwidth [MHz]	Modulation	RB Size	RB Offset	MIF [dB]
71	680.5	133297	20	16QAM	1	0	-9.55
12	707.5	23095	10	16QAM	1	0	-9.74
13	782.0	23230	10	16QAM	1	0	-10.01
14	793.0	23330	10	16QAM	1	0	-10.70
26	831.5	26865	15	16QAM	1	0	-9.88
66	1745.0	132322	20	16QAM	1	0	-10.22
25	1882.5	26365	20	16QAM	1	0	-9.81
30	2310.0	27710	10	16QAM	1	0	-10.58
7	2535.0	21100	20	16QAM	1	0	-10.14
71	680.5	133297	20	64QAM	1	0	-9.04
71	680.5	133297	20	QPSK	1	0	-14.56
71	680.5	133297	20	16QAM	1	50	-8.83
71	680.5	133297	20	16QAM	1	99	-9.04
71	680.5	133297	20	16QAM	50	0	-16.36
71	680.5	133297	20	16QAM	100	0	-16.85
71	680.5	133297	15	16QAM	1	36	-9.68
71	680.5	133297	10	16QAM	1	25	-8.71
71	680.5	133297	5	16QAM	1	12	-9.71
71	668.0	133172	10	16QAM	1	25	-8.97
71	693.0	133422	10	16QAM	1	25	-10.16

 Table 7-3

 LTE FDD Modulation Interference Factors^{1,2}

LTE FDD Uplink Carrier Aggregation Modulation Interference Factor^{1,3}

				PCC							SCC				1
Combination	PCC Band	PCC Bandwidth [MHz]	PCC (UL) Channel	PCC (UL) Frequency [MHz]	Modulation	PCC UL# RB	PCC UL RB Offset	SCC Band	SCC Bandwidth [MHz]	SCC (UL) Channel	SCC (UL) Frequency [MHz]	Modulation	SCC UL# RB	SCC UL RB Offset	MIF (dB)
CA_7C	LTE B7	20	21100	2535.0	16QAM	1	0	LTE B7	20	20902	2515.2	16QAM	1	99	-9.86
CA_66B	LTE B66	10	132322	1745.0	16QAM	1	0	LTE B66	10	132223	1735.1	16QAM	1	49	-10.33
CA_66C	LTE B66	20	132322	1745.0	16QAM	1	0	LTE B66	20	132124	1725.2	16qAM	1	99	-9.73

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

² Note: All FDD LTE bands were found to have substantially similar MIF values given similar RB, BW, and modulation configurations.

³ Note: LTE FDD ULCA was evaluated to ensure LTE FDD standalone was the worst-case scenario. The configurations in Table 7-4 were determined from Table 7-3 and satisfy the configuration requirements as defined in 3GPP 36.101.

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LTE Band	Frequency [MHz]	Channel	Bandwidth [MHz]	Modulation	RB Size	RB Offset	MIF [dB]
41	2593.0	40620	20	16QAM	1	0	3.58
41	2593.0	40620	20	QPSK	1	0	3.66
41	2593.0	40620	20	64QAM	1	0	3.65
41	2593.0	40620	20	QPSK	1	50	3.66
41	2593.0	40620	20	QPSK	1	99	3.67
41	2593.0	40620	20	QPSK	50	0	3.62
41	2593.0	40620	20	QPSK	100	0	3.62
41	2593.0	40620	15	QPSK	1	74	3.79
41	2593.0	40620	10	QPSK	1	49	3.78
41	2593.0	40620	5	QPSK	1	24	3.65
41	2506.0	39750	15	QPSK	1	74	3.59
41	2549.5	40185	15	QPSK	1	74	3.56
41	2636.5	41055	15	QPSK	1	74	3.77
41	2680.0	41490	15	QPSK	1	74	3.58

 Table 7-5

 LTE TDD B41 Power Class 3 Modulation Interference Factors^{1,2}

 Table 7-6

 LTE TDD B38 Modulation Interference Factors^{1,2}

LTE Band	Frequency [MHz]	Channel	Bandwidth [MHz]	Modulation	RB Size	RB Offset	MIF [dB]
38	2595.0	38000	20	16QAM	1	0	3.67
38	2595.0	38000	20	QPSK	1	0	3.74
38	2595.0	38000	20	64QAM	1	0	3.75
38	2595.0	38000	20	64QAM	1	50	3.74
38	2595.0	38000	20	64QAM	1	99	3.74
38	2595.0	38000	20	64QAM	50	0	3.58
38	2595.0	38000	20	64QAM	100	0	3.57
38	2595.0	38000	15	64QAM	1	0	3.88
38	2595.0	38000	10	64QAM	1	0	3.87
38	2595.0	38000	5	64QAM	1	0	3.66
38	2577.5	37825	15	64QAM	1	0	3.73
38	2612.5	38175	15	64QAM	1	0	3.66

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

² Note: LTE TDD MIFs were taken using UL-DL Configuration 5. More information about the chosen UL-DL Configuration can be found in Section 10.

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Table 7-7								
802.11b (2.4GHz, SISO) Modulation Interference Factors ^{1,2}								
802.11b MIF Measurements [dB]								
	Mode	Data Rate [Mbps]						
		1	2	5.5	11			

		2	5.5	
802.11b	-9.99	- 9.15	-7.34	-6.37

802.11g (2.4GHz, SISO) Modulation Interference Factors^{1,2}

		802.11g MIF Measurements [dB]								
Mode		Data Rate [Mbps] 6 9 12 18 24 36 48 54								
	6									
802.11g	-7.65									

Table 7-9

802.11g (2.4GHz, MIMO) Modulation Interference Factors^{1,2}

			802.1	1g MIF Mea	asurement	s [dB]		
Mode	Data Rate [Mbps]							
	12 18 24 36 48 72 92 10							108
802.11g	-7.60	-6.91	-6.32	-5.43	-4.96	-4.67	-4.86	-4.91

Table 7-10

802.11n (2.4GHz, SISO) Modulation Interference Factors^{1,2}

			802.11n (2	.4GHz) MIF	Measure	nents [dB]			
Mode		Data Rate [Mbps]							
	6.5 13 19.5 26 39 52 58.5							65	
802.11n	-7.69	-6.47	-5.82	-5.01	-4.76	-4.81	-4.90	-5.02	

Table 7-11

802.11n (2.4GHz, MIMO) Modulation Interference Factors^{1,2}

802.11n (2.4GHz) MIF Measurements [dB]									
Mode		Data Rate [Mbps]							
	13 26 39 52 78 104 117 130								
802.11n	-7.60	7.60 -6.43 -5.72 -4.97 -4.69 -4.75 -4.87 -4.98							

Table 7-12

802.11ax (2.4GHz, SU, SISO) Modulation Interference Factors^{1,2}

		20MHz 802.11ax (2.4GHz) MIF Measurements [dB]										
Mode		Data Rate [Mbps]										
	4	10	24	33	49	65	73	81	98	108		
802.11ax	-6.89	-6.89 -5.79 -5.14 -4.85 -4.69 -4.77 -4.88 -4.95 -5.07 -5.21										

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

² Note: WIFI MIF values were found to be independent of the transmit channel.

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	802.11ax (2.4GHZ, SU, MIMO) Modulation interference Factors ^{1,2}											
	20MHz 802.11ax (2.4GHz) MIF Measurements [dB]											
Mode		Data Rate [Mbps]										
	8	8 32 48 66 98 130 146 162 196 216										
802.11ax	-5.67	-4.76	-4.65	-4.74	-5.00	-5.28	-5.35	-5.53	-5.61	-5.72		

Table 7-13										
802.11ax (2.4GHz, SU, MIMO)	Modulation Interference Factors ^{1,2}									

802.11a (5GHz, 20MHz BW, SISO) Modulation Interference Factors^{1,2}

	802.11a MIF Measurements [dB]									
Mode		Data Rate [Mbps]								
	6 9 12 18 24 36 48									
802.11a	-7.54	7.54 -6.82 -6.24 -5.55 -5.11 -4.87 -4.98 -5.04								

Table 7-15

802.11a (5GHz, 20MHz BW, MIMO) Modulation Interference Factors^{1,2}

			802.11	1a MIF Mea	asurement	s [dB]			
Mode		Data Rate [Mbps]							
	12 18 24 36 48 72 92							108	
802.11a	-7.42	7.42 -6.77 -6.19 -5.48 -5.05 -4.78 -4.92 -5.02							

Table 7-16

802.11n (5GHz, 20MHz BW, SISO) Modulation Interference Factors^{1,2}

		20MHz BW 802.11n (5GHz) MIF Measurements [dB]									
Mode		Data Rate [Mbps]									
	6.5 13 19.5 26 39 52 58.5										
802.11n	-7.47	-6.19	-5.53	-5.12	-4.84	-4.88	-4.99	-5.11			

Table 7-17

802.11n (5GHz, 20MHz BW, MIMO) Modulation Interference Factors^{1,2}

	20MHz BW 802.11n (5GHz) MIF Measurements [dB]									
Mode		Data Rate [Mbps]								
	13 26 39 52 78 104 117 130									
802.11n	-7.34	-7.34 -6.13 -5.44 -5.07 -4.78 -4.85 -4.97 -5.08								

Table 7-18

802.11ac (5GHz, 20MHz BW, SISO) Modulation Interference Factors^{1,2}

	20MHz BW 802.11ac (5GHz) MIF Measurements [dB]										
Mode	Data Rate [Mbps]										
6.5 13 19.5 26 39 52 58.5 65									78		
802.11ac	-7.49 -6.24 -5.55 -5.12 -4.83 -4.87 -4.95 -5.07 -5.25										

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

² Note: WIFI MIF values were found to be independent of the transmit channel.

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802.11ac (5GHz, 20MHz BW, MIMO) Modulation Interference Factors ^{1,2}											
20MHz BW 802.11ac (5GHz) MIF Measurements [dB]											
Mode	Data Rate [Mbps]										
	13 26 39 52 78 104 117 130 156										
802.11ac	-6.20 -5.16 -4.83 -4.84 -5.21 -5.56 -5.71 -5.84 -6.07										

Table 7-20

802.11ax (5GHz, 20MHz BW, SU, SISO) Modulation Interference Factors^{1,2}

				201	1Hz 802.11	ax (5GHz)	MIF Measu	urements [dB]				
Mode		Data Rate [Mbps]											
	4	16	24	33	49	65	73	81	98	108	122	135	
802.11ax	★ -6.95 -5.84 -5.18 -4.91 -4.77 -4.84 -4.96 -5.06 -5.19 -5.31 -5.42 -5.58												

Table 7-21

802.11ax (5GHz, 20MHz BW, SU, MIMO) Modulation Interference Factors^{1,2}

				201	1Hz 802.11	ax (5GHz)	MIF Measu	urements [dB]					
Mode		Data Rate [Mbps]												
	8	32	48	66	98	130	146	162	196	216	244	270		
802.11ax	-5.78	-4.88	-4.74	-4.84	-5.10	-5.40	-5.50	-5.64	-5.69	-5.80	-5.89	-6.06		

Table 7-22

802.11n (5GHz, 40MHz BW, SISO) Modulation Interference Factors ^{1,2}
40MHz BW 802.11n	(5GHz) MIF Measurements [dB]

Mode		Data Rate [Mbps]									
	13.5 27 40.5 54 81 108 121.5 135										
802.11n	-5.93	-4.92	-4.69	-4.78	-5.26	-5.74	-5.90	-6.08			

Table 7-23

802.11n (5GHz, 40MHz BW, MIMO) Modulation Interference Factors^{1,2}

		40MI	Hz BW 802	.11n (5GHz	:) MIF Mea	surements	; [dB]		
Mode	Mode Data Rate [Mbps] 27 54 81 108 162 216 243 270								
802.11n	-5.98	-4.92	-4.69	-4.81	-5.29	-5.76	-5.92	-6 .10	

Table 7-24
802.11ac (5GHz, 40MHz BW, SISO) Modulation Interference Factors ^{1,2}
40MHz BW 802 11ac (5GHz) MIE Measurements [dB]

		40MHZ BW 802.11aC (SGHZ) MIF Measurements [db]										
Mode	Data Rate [Mbps]											
	13.5 27 40.5 54 81 108 121.5 135 180											
802.11ac	-5.94	-4.90	-4.68	-4.74	-5.19	-5.68	-5.83	-5.97	-6.45			

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

² Note: WIFI MIF values were found to be independent of the transmit channel.

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	802.11ac (5GHz, 40MHz BW, MIMO) Modulation Interference Factors ^{1,2}												
	40MHz BW 802.11ac (5GHz) MIF Measurements [dB]												
Mode		Data Rate [Mbps]											
	27	54	81	108	162	216	243	270	360				
802.11ac	-4.93												

Table 7-26

802.11ax (5GHz, 40MHz BW, SU, SISO) Modulation Interference Factors^{1,2}

		40MHz 802.11ax (5GHz) MIF Measurements [dB]											
Mode Data Rate [Mbps]													
	8	33	49	65	98	130	146	163	195	217	244	271	
802.11ax	-5.70	-4.72 -4.63 -4.76 -5.10 -5.47 -5.54 -5.74 -5.81 -5.95 -6.07 -6.27											

Table 7-27

802.11ax (5GHz, 40MHz BW, SU, MIMO) Modulation Interference Factors^{1,2}

		40MHz 802.11ax (5GHz) MIF Measurements [dB]											
Mode						Data Rat	e [Mbps]						
	16	66	98	130	196	260	292	326	390	434	488	542	
802.11ax	-4.79												

Table 7-28

802.11ac (5GHz, 80MHz BW, SISO) Modulation Interference Factors^{1,2}

		80MHz BW 802.11ac (5GHz) MIF Measurements [dB]										
Mode		Data Rate [Mbps]										
	29.3	58.5	87.8	117	175.5	234	263.3	292.5	351	390		
802.11ac	-4.87	37 -4.83 -5.27 -5.65 -6.24 -6.64 -6.80 -6.95 -7.04 -7.24										

Table 7-29

802.11ac (5GHz, 80MHz BW, MIMO) Modulation Interference Factors^{1,2}

	80MHz BW 802.11ac (5GHz) MIF Measurements [dB]												
Mode Data Rate [Mbps]													
	58.5	117	175.5	234	351	468	526.5	585	702	780			
802.11ac	-4.85	5 -5.68 -6.12 -6.51 -6.96 -7.25 -7.20 -7.38 -7.33 -7.54											

Table 7-30

802.11ax (5GHz, 80MHz BW, SU, SISO) Modulation Interference Factors^{1,2}

	80MHz 802.11ax (5GHz) MIF Measurements [dB]												
Mode		Data Rate [Mbps]											
	17	68	102	136	204	272	306	340	408	453	510	567	
802.11ax	-4.73												

Table 7-31

802.11ax (5GHz, 80MHz BW, SU, MIMO) Modulation Interference Factors^{1,2}

				80N	1Hz 802.11	ax (5GHz)	MIF Measu	urements [dB]				
Mode		Data Rate [Mbps]											
	34	136	204	272	408	544	612	680	816	906	1020	1134	
802.11ax	-4.78												

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

²Note: WIFI MIF values were found to be independent of the transmit channel.

Table 7-32

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802.11ax (2.4GHz, RU, SISO) Modulation Interference Factors^{1,2}

		20MHz 802.11ax (2.4GHz) MIF Measurements [dB] RU Index (Data Rate: 49Mbps)										
Mode												
	0	8	37	40	53	54	61					
802.11ax	-7.88	7.88 -8.08 -6.54 -6.78 -5.27 -5.41 -4.67										

802.11ax (2.4GHz, RU, MIMO) Modulation Interference Factors^{1,2}

			20MHz 802.11ax (2.4GHz) MIF Measurements [dB]											
Mod	le	RU Index (Data Rate: 48Mbps)												
		0	8	37	40	53	54	61						
802.1	1ax	-9.26	9.26 -9.00 -8.38 -8.31 -7.15 -7.13 -5.73											

Table 7-34

802.11ax (5GHz, 20MHz BW, RU, SISO) Modulation Interference Factors^{1,2} 20MHz 802.11ax (5GHz) MIF Measurements [dB]

Mode			•	,	: 49Mbps)		
	0	8	37	40	53	54	61
802.11ax	-7.94	-7.99	-6.65	-6.66	-5.42	-5.41	-4.70

Table 7-35

802.11ax (5GHz, 20MHz BW, RU, MIMO) Modulation Interference Factors^{1,2}

Mode		RU Index (Data Rate: 48Mbps)										
	0	8	37	40	53	54	61					
802.11ax	-7.76	7.76 -7.81 -6.65 -6.58 -5.44 -5.39 -4.72										

Table 7-36

802.11ax (5GHz, 40MHz BW, RU, SISO) Modulation Interference Factors^{1,2}

		40MHz 802.11ax (5GHz) MIF Measurements [dB]										
Mode	RU Index (Data Rate: 49Mbps)											
	0	17	37	44	53	56	61	65				
802.11ax	- 9.10	-9.10 -9.08 -7.98 -7.99 -6.59 -6.62 -5.22 -4.63										

	Table 7-37									
802.11ax (5GHz, 40MHz BW, RU, MIMO) Modulation Interference Factors ^{1,2}										
	40MHz 802.11ax (5GHz) MIF Measurements [dB]									
Mode			RU li	ndex (Data	Rate: 66N	lbps)				
	0	17	37	44	53	56	61	65		
802.11ax	-8.57	-8.43	-7.42	-7.45	-6.14	-6.18	-4.93	-4.74		

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

² Note: WIFI MIF values were found to be independent of the transmit channel.

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	802.11ax (5GHz, 80MHz BW, RU, SISO) Modulation Interference Factors ^{1,2}										
		80MHz 802.11ax (5GHz) MIF Measurements [dB]									
Mode	RU Index (Data Rate: 17Mbps)										
	0	36	37	52	53	60	61	65	66	67	
802.11ax	-11.98	1.98 -11.71 -9.45 -9.39 -8.40 -8.47 -7.03 -5.72 -5.64 -4.71									

Table 7-38802.11ax (5GHz, 80MHz BW, RU, SISO) Modulation Interference Factors^{1,2}

Table 7-39

802.11ax (5GHz, 80MHz BW, RU, MIMO) Modulation Interference Factors^{1,2}

		80MHz 802.11ax (5GHz) MIF Measurements [dB]										
Mode	RU Index (Data Rate: 34Mbps)											
	0	36	37	52	53	60	61	65	66	67		
802.11ax	-9.14	9.14 -9.05 -8.44 -8.38 -7.28 -7.22 -5.84 -4.87 -4.85 -4.73										

Table 7-40

Simultaneous 2.4GHz and 5GHz WIFI Modulation Interference Factors^{1,2,3}

# Tx		z WIFI Bm]		lz WIFI 3m]	Measured MIF (dB)
1.	Ant1	Ant2	Ant1	Ant2	(00)
2	x	-	-	x	-4.62
2	-	x	x	-	-4.67
2	x	-	x	-	-4.66
2	-	x	-	x	-4.67
3	x	x	x	-	-4.56
3	x	x	-	x	-4.59
3	х	-	x	x	-5.17
3	-	x	x	x	-5.17
4	x	x	x	x	-5.50

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

² Note: WLAN MIF values were found to be independent of the transmit channel.

³ Note: The configuration for each scenario (e.g. bandwidth, data rate, etc.) was determined using the worst-case configuration from SISO and MIMO MIF measurements.

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8. RF CONDUCTED POWER MEASUREMENTS

I. Procedures Used to Establish RF Signal for HAC Testing

The handset was placed into a simulated call using a base station simulator in a shielded chamber. Such test signals offer a consistent means for testing HAC and are recommended for evaluating HAC. Measurements were taken with a fully charged battery. In order to verify that the device was tested and maintained at full power, this was configured with the base station simulator.

II. HAC Measurement Conditions

Output Power Verification

Maximum output power is verified on the High, Middle and Low channels for all applicable air interfaces. See Table 8-1 for air interface specific settings of transmit power parameters.

Power Control Parameters and Settings by Air Interface									
Air Interface: Parameter Name: Parameter Set To:									
GSM	PCL	GSM850: "5"; GSM1900: "0"							
UMTS	TPC	"All 1's"							
LTE	TPC	"Max Power"							
WIFI	PLS	Mfr Specified							

Table 8-1

III. Setup Used to Measure RF Conducted Powers

Power measurements for licensed modes were performed using a base station simulator under digital average power. Power measurements for unlicensed modes were performed using a power meter and power sensor.



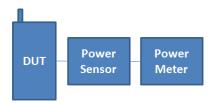
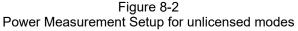


Figure 8-1 Power Measurement Setup for licensed modes



IV. GSM Conducted Powers

Band	Channel	GSM [dBm] CS (1 Slot)	EDGE [dBm] 1 Tx Slot
	128	32.55	26.70
GSM 850	190	32.36	26.62
	251	32.61	26.86
	512	30.82	25.98
GSM 1900	661	30.70	26.29
	810	30.64	25.83

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V. UMTS Conducted Powers

Mode 3GPP 34.121		Cellular Band [dBm]			AWS Band [dBm]			PCS Band [dBm]		
	Subtest		4183	4233	1312	1412	1513	9262	9400	9538
WCDMA	12.2 kbps RMC	24.27	24.23	24.25	24.18	24.27	24.10	23.61	23.60	23.51
WCDIVIA	12.2 kbps AMR	24.23	24.31	24.21	24.19	24.29	24.12	23.58	23.53	23.50
HSUPA	Subtest 1	23.16	23.31	23.49	23.54	23.66	23.43	22.77	22.85	22.51

VI. LTE Conducted Powers

a. LTE Band 71

Table 8-2 LTE Band 71 (680.5MHz) Conducted Powers – 20MHz Bandwidth									
LTE Ba	nd 71 (68	30.5MHz)		owers – 20MH	z Bandwidth				
Modulation	RB Size	RB Offset	Mid Channel 133297 (680.5 MHz) Conducted Power	MPR Allowed per 3GPP [dB]	MPR [dB]				
			[dBm]						
	1	0	24.62		0				
	1	50	24.52	0	0				
	1	99	24.48		0				
QPSK	50	0	23.75		1				
	50	25	23.70	0-1	1				
	50	50	23.71	0-1	1				
	100	0	23.68		1				
	1	0	24.20		1				
	1	50	24.10	0-1	1				
	1	99	23.82		1				
16QAM	50	0	22.70		2				
	50	25	22.68	0-2	2				
	50	50	22.67	0-2	2				
	100	0	22.56		2				
	1	0	22.99		2				
	1	50	22.91	0-2	2				
	1	99	22.84	1	2				
64QAM	50	0	21.78		3				
	50	25	21.79	0-3	3				
	50	50	21.77	0-3	3				
	100	0	21.69	1	3				

Note: Since LTE Band 71 at 20MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

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			Mid Channel			
Modulation	RB Size	RB Offset	133297 (680.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]	
			Conducted Power [dBm]			
	1	0	24.43		0	
	1	36	24.35	0	0	
	1	74	24.41		0	
QPSK	36	0	23.62		1	
	36	18	23.65	0-1	1	
	36	37	23.60	0-1	1	
	75	0	23.62		1	
	1	0	24.07		1	
	1	36	24.09	0-1	1	
	1	74	24.08		1	
16QAM	36	0	22.57		2	
	36	18	22.57	0-2	2	
	36	37	22.58	0-2	2	
	75	0	22.59]	2	
	1	0	22.56		2	
	1	36	22.53	0-2	2	
	1	74	22.58		2	
64QAM	36	0	21.62		3	
	36	18	21.64	0-3	3	
	36	37	21.63	0-3	3	
	75	0	21.60]	3	

 Table 8-3

 LTE Band 71 (680.5MHz) Conducted Powers – 15MHz Bandwidth

Note: Since LTE Band 71 at 15MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

	Table 8-4						
L	FE Band	71 ((680.5MHz)	Conducted Po	wers – 10MHz	Bandwidth	

Modulation	RB Size	RB Offset	Low Channel 133172 (668.0 MHz)	Mid Channel 133297 (680.5 MHz)	High Channel 133422 (693.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			C	Conducted Power [dBm	1		
	1	0	24.42	24.44	24.18		0
	1	25	24.29	24.30	24.29	0	0
	1	49	24.32	24.43	24.30		0
QPSK	25	0	23.40	23.41	23.43		1
	25	12	23.42	23.42	23.43	0-1	1
	25	25	23.39	23.39	23.38	0-1	1
	50	0	23.36	23.41	23.40		1
	1	0	23.60	23.92	23.82	0-1	1
	1	25	23.66	23.87	23.81		1
	1	49	23.58	23.98	23.88		1
16QAM	25	0	22.43	22.44	22.49		2
	25	12	22.41	22.46	22.44	0-2	2
	25	25	22.39	22.47	22.46	02	2
	50	0	22.34	22.39	22.43		2
	1	0	22.40	22.51	22.34		2
	1	25	22.34	22.38	22.41	0-2	2
	1	49	22.30	22.55	22.36		2
64QAM	25	0	21.49	21.46	21.45		3
	25	12	21.45	21.45	21.42	0.3	3
	25	25	21.44	21.43	21.44	0-3	3
	50	0	21.39	21.42	21.46		3

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LTE Banu / I (600.3MHZ) COnducted Powers – SMHZ Banuwiuth							
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	133147 (665.5 MHz)	133297 (680.5 MHz)	133447 (695.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			c	Conducted Power [dBm]		
	1	0	24.17	24.11	24.32		0
	1	12	24.26	24.27	24.48	0	0
	1	24	24.25	24.29	24.44		0
QPSK	12	0	23.45	23.34	23.38		1
	12	6	23.46	23.44	23.47	0-1	1
	12	13	23.41	23.43	23.50	0-1	1
	25	0	23.41	23.47	23.38		1
	1	0	23.50	23.57	23.72	0-1	1
	1	12	23.59	23.73	23.85		1
	1	24	23.65	23.72	23.80		1
16QAM	12	0	22.37	22.36	22.50		2
	12	6	22.47	22.44	22.58	0-2	2
	12	13	22.47	22.48	22.64	0-2	2
	25	0	22.50	22.51	22.34		2
	1	0	22.36	22.46	22.49		2
	1	12	22.48	22.62	22.58	0-2	2
	1	24	22.55	22.63	22.55		2
64QAM	12	0	21.41	21.40	21.29		3
	12	6	21.48	21.52	21.38	0-3	3
	12	13	21.50	21.51	21.43		3
	25	0	21.48	21.44	21.35		3

Table 8-5 LTE Band 71 (680.5MHz) Conducted Powers – 5MHz Bandwidth

b. LTE Band 12

	LTE Band 12 (707.5MHz) Conducted Powers – 10MHz Bandwidth									
LIEB	and 12 (7	07.5MHZ	Conducted Po	owers – 10MHz	Bandwidth					
			Mid Channel							
			23095	MPR Allowed per						
Modulation	RB Size	RB Offset	(707.5 MHz)	3GPP [dB]	MPR [dB]					
			Conducted Power							
			[dBm]							
	1	0	23.81		0					
	1	25	24.26	0	0					
	1	49	24.12		0					
QPSK	25	0	23.48		1					
-	25	12	23.43	0-1	1					
	25	25	23.31	0-1	1					
	50	0	23.43		1					
	1	0	23.14		1					
	1	25	23.54	0-1	1					
	1	49	23.55		1					
16QAM	25	0	22.48		2					
	25	12	22.40	0-2	2					
	25	25	22.42	0-2	2					
	50	0	22.38		2					
	1	0	22.01		2					
	1	25	22.41	0-2	2					
	1	49	22.51		2					
64QAM	25	0	21.47		3					
	25	12	21.48	0.2	3					
	25	25	21.44	0-3	3					
	50	0	21.45		3					

Table 8-6

Note: Since LTE Band 12 at 10MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

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			Low Channel	Mid Channel	High Channel		
Mashulatian			23035	23095	23155	MPR Allowed per	
Modulation	RB Size	RB Offset	(701.5 MHz)	(707.5 MHz)	(713.5 MHz)	3GPP [dB]	MPR [dB]
			(Conducted Power [dBm]		
	1	0	23.79	24.36	24.27		0
	1	12	23.70	24.50	24.00	0	0
	1	24	23.93	24.40	23.80		0
QPSK	12	0	23.41	23.45	23.39		1
	12	6	23.53	23.54	23.48	0-1	1
	12	13	23.44	23.53	23.45	0-1	1
	25	0	23.48	23.52	23.40		1
	1	0	23.09	23.44	23.64	0-1	1
	1	12	22.81	23.58	23.35		1
	1	24	23.25	23.54	23.07		1
16QAM	12	0	22.46	22.48	22.61		2
	12	6	22.52	22.59	22.70	0-2	2
	12	13	22.53	22.55	22.61	0-2	2
	25	0	22.56	22.52	22.46		2
	1	0	21.93	22.65	22.43		2
	1	12	21.87	22.78	22.09	0-2	2
	1	24	22.12	22.71	21.78		2
64QAM	12	0	21.49	21.55	21.40		3
	12	6	21.65	21.64	21.46	0-3	3
	12	13	21.57	21.60	21.42		3
	25	0	21.53	21.58	21.48		3

Table 8-7 LTE Band 12 (707.5MHz) Conducted Powers – 5MHz Bandwidth

 Table 8-8

 LTE Band 12 (707.5MHz) Conducted Powers – 3MHz Bandwidth

Modulation	RB Size	RB Offset	Low Channel 23025 (700.5 MHz)	Mid Channel 23095 (707.5 MHz)	High Channel 23165 (714.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]	
			C	Conducted Power [dBm	1]			
	1	0	23.82	24.28	23.83		0	
	1	7	23.63	24.44	23.65	0	0	
	1	14	23.66	24.36	23.66		0	
QPSK	8	0	23.41	23.44	23.34	-	1	
	8	4	23.47	23.51	23.45	0-1	1	
	8	7	23.46	23.47	23.37	- 0-1	1	
	15	0	23.50	23.48	23.42		1	
	1	0	22.99	23.84	23.26	0-1	1	
	1	7	22.81	23.83	22.92		1	
	1	14	22.62	23.87	22.99		1	
16QAM	8	0	22.46	22.57	22.48		2	
	8	4	22.54	22.67	22.58	0-2	2	
	8	7	22.45	22.62	22.50	0-2	2	
	15	0	22.40	22.50	22.52		2	
	1	0	21.67	22.37	22.17		2	
	1	7	21.62	22.44	21.91	0-2	2	
	1	14	21.65	22.46	21.92		2	
64QAM	8	0	21.48	21.50	21.34		3	
	8	4	21.60	21.59	21.44	0-3	3	
	8	7	21.57	21.58	21.49	0-3	3	
	15	0	21.62	21.48	21.48		3	

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			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	23017	23095	23173	MPR Allowed per	MPR [dB]
Wouldtion	ND 5126	IND Onset	(699.7 MHz)	(707.5 MHz)	(715.3 MHz)	3GPP [dB]	
			(Conducted Power [dBm]		
	1	0	23.81	24.39	23.60		0
	1	2	23.83	24.45	23.67		0
	1	5	23.66	24.46	23.66		0
QPSK	3	0	23.74	24.35	23.67	0	0
	3	2	23.76	24.47	23.69		0
	3	3	23.69	24.38	23.65		0
	6	0	23.38	23.41	23.34	0-1	1
	1	0	22.98	23.61	22.95	0-1	1
	1	2	23.03	23.69	23.02		1
	1	5	22.88	23.66	23.03		1
16QAM	3	0	22.94	23.57	22.68	0-1	1
	3	2	22.94	23.65	22.72		1
	3	3	22.87	23.64	22.68		1
	6	0	22.38	22.60	22.36	0-2	2
	1	0	21.73	22.81	21.88		2
	1	2	21.76	22.92	21.94		2
	1	5	21.55	22.86	21.91	0-2	2
64QAM	3	0	21.82	22.62	21.82	0-2	2
	3	2	21.83	22.71	21.87		2
	3	3	21.78	22.60	21.82		2
	6	0	21.47	21.42	21.38	0-3	3

Table 8-9 LTE Band 12 (707.5MHz) Conducted Powers – 1.4MHz Bandwidth

c. LTE Band 13

Table 8-10 LTE Band 13 (780.0MHz) Conducted Powers – 10MHz Bandwidth

		<u>, , , , , , , , , , , , , , , , , , , </u>	Oomaaotea I		2 Dunamatin
			Mid Channel		
			23230	MPR Allowed per	
Modulation	RB Size	RB Offset	(782.0 MHz)	3GPP [dB]	MPR [dB]
			Conducted Power		
			[dBm]		
	1	0	23.91		0
	1	25	23.90	0	0
	1	49	24.02		0
QPSK	25	0	23.11		1
	25	12	23.08	0-1	1
	25	25	23.09	0-1	1
	50	0	23.08		1
	1	0	23.22		1
	1	25	23.25	0-1	1
	1	49	23.32		1
16QAM	25	0	22.11		2
	25	12	22.13	0-2	2
	25	25	22.10	0-2	2
	50	0	22.09		2
	1	0	22.30		2
	1	25	22.16	0-2	2
	1	49	22.19		2
64QAM	25	0	21.09		3
	25	12	21.08	0-3	3
	25	25	21.06	0-3	3
	50	0	21.11]	3

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LIEB	and 13 (7	80.0WHZ) Conducted P	<u>owers – SiviHz</u>	Bandwidth
			Mid Channel		
Modulation	RB Size	RB Offset	23230 (782.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			Conducted Power [dBm]		
	1	0	23.94		0
	1	12	23.88	0	0
	1	24	23.87		0
QPSK	12	0	23.01		1
	12	6	22.99	0-1	1
	12	13	22.98	0-1	1
	25	0	22.95		1
	1	0	23.20		1
	1	12	23.13	0-1	1
	1	24	23.17		1
16QAM	12	0	22.13		2
	12	6	22.14	0-2	2
	12	13	22.11	0-2	2
	25	0	21.99		2
	1	0	22.02		2
	1	12	22.00	0-2	2
	1	24	21.93		2
64QAM	12	0	20.92		3
	12	6	20.88	0-3	3
	12	13	20.91	0-3	3
	25	0	20.95	-	3

Table 8-11 LTE Band 13 (780 0MHz) Conducted Powers – 5MHz Bandwidth

Note: Since LTE Band 13 at 5MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

d. LTE Band 14

LTE Band 14 (793.0MHz) Conducted Powers – 10MHz Bandwidth									
Modulation	RB Size	RB Offset	Mid Channel 23330 (793.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]				
			Conducted Power [dBm]						
	1	0	24.23		0				
	1	25	24.17	0	0				
	1	49	24.11		0				
QPSK	25	0	23.28		1				
	25	12	23.30	0-1	1				
	25	25	23.05	0-1	1				
	50	0	23.19		1				
	1	0	23.45		1				
	1	25	23.04	0-1	1				
	1	49	23.15		1				
16QAM	25	0	22.39		2				
	25	12	22.28	0-2	2				
	25	25	22.07	0-2	2				
	50	0	22.25		2				
	1	0	22.26		2				
	1	25	22.40	0-2	2				
	1	49	22.15]	2				
64QAM	25	0	21.36		3				
	25	12	21.38	0-3	3				
	25	25	21.12] 0-3	3				
	50	0	21.23]	3				

	Table 8-12								
LTE Ba	LTE Band 14 (793.0MHz) Conducted Powers - 10MHz Bandwidth								

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	and 14 (<i>1</i>	93.0WHZ	<u>owers – SiviHz</u>	Bandwidth	
			Mid Channel		
Modulation	RB Size	RB Offset	23330 (793.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			Conducted Power [dBm]		
	1	0	23.95		0
	1	12	23.97	0	0
	1	24	23.92		0
QPSK	12	0	23.09		1
	12	6	23.18	0-1	1
	12	13	23.08	0-1	1
	25	0	23.12		1
	1	0	23.27		1
	1	12	23.31	0-1	1
	1	24	23.25		1
16QAM	12	0	22.11		2
	12	6	22.16	0-2	2
	12	13	22.13	0-2	2
	25	0	22.19		2
	1	0	22.17		2
	1	12	22.20	0-2	2
	1	24	22.17		2
64QAM	12	0	21.19		3
	12	6	21.25	0-3	3
	12	13	21.15	0-3	3
	25	0	21.12		3

Table 8-13 I TE Band 14 (793 0MHz) Conducted Powers - 5MHz Bandwidth

Note: Since LTE Band 14 at 5MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

e. LTE Band 26

LTE Ba	LTE Band 26 (831.5MHz) Conducted Powers – 15MHz Bandwidth									
Modulation	RB Size	RB Offset	Mid Channel 26865 (831.5 MHz) Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]					
	1	0	24.22		0					
	1	36	24.17	0	0					
	1	74	24.16		0					
QPSK	36	0	23.26		1					
	36	18	23.25	0-1	1					
	36	37	23.27	0-1	1					
	75	0	23.24		1					
	1	0	23.47		1					
	1	36	23.45	0-1	1					
	1	74	23.40		1					
16QAM	36	0	22.27		2					
	36	18	22.26	0-2	2					
	36	37	22.23	0-2	2					
	75	0	22.29		2					
	1	0	22.44		2					
	1	36	22.46	0-2	2					
	1	74	22.42		2					
64QAM	36	0	21.31		3					
	36	18	21.28	0-3	3					
	36	37	21.32	0-5	3					
	75	0	21.19		3					

Table 8-14

Note: Since LTE Band 26 at 15MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

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Modulation	RB Size	RB Offset	Low Channel 26740 (819.0 MHz)	Mid Channel 26865 (831.5 MHz)	High Channel 26990 (844.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
			C	Conducted Power [dBm]				
	1	0	24.59	24.31	24.50		0		
	1	25	24.61	24.24	24.30	0	0		
	1	49	24.66	24.24	24.10		0		
QPSK	25	0	23.82	23.41	23.54		1		
	25	12	23.87	23.43	23.57	0-1	1		
	25	25	23.79	23.39	23.51	0-1	1		
	50	0	23.81	23.43	23.52		1		
	1	0	23.68	23.54	23.75		1		
	1	25	23.76	23.59	23.68	0-1	1		
	1	49	23.94	23.49	23.58		1		
16QAM	25	0	22.86	22.43	22.55		2		
	25	12	22.84	22.46	22.57	0-2	2		
	25	25	22.81	22.39	22.52	0-2	2		
	50	0	22.78	22.45	22.52		2		
	1	0	22.16	22.46	22.43		2		
	1	25	22.19	22.33	22.33	0-2	2		
	1	49	22.64	22.16	22.15	1	2		
64QAM	25	0	21.40	21.45	21.29		3		
	25	12	21.33	21.46	21.36		3		
	25	25	21.26	21.39	21.16	0-3	3		
	50	0	21.26	21.40	21.21		3		

 Table 8-15

 LTE Band 26 (831.5MHz) Conducted Powers – 10MHz Bandwidth

Table 8-16

LTE Band 26 (831.5MHz) Conducted Powers – 5MHz Bandwidth

Modulation	RB Size	RB Offset	Low Channel 26715 (816.5 MHz)	Mid Channel 26865 (831.5 MHz)	High Channel 27015 (846.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			. ,	Conducted Power [dBm	. ,		
	1	0	24.35	24.27	24.30		0
	1	12	24.45	24.33	24.27	0	0
	1	24	24.38	24.31	24.13	-	0
QPSK	12	0	23.76	23.47	23.43		1
	12	6	23.87	23.52	23.53	0-1	1
	12	13	23.83	23.49	23.46	0-1	1
	25	0	23.84	23.47	23.40		1
	1	0	23.47	23.60	23.63		1
	1	12	23.73	23.70	23.39	0-1	1
	1	24	23.61	23.66	23.09		1
16QAM	12	0	22.58	22.52	22.44		2
	12	6	22.71	22.55	22.57	0-2	2
	12	13	22.67	22.52	22.52	0-2	2
	25	0	22.57	22.43	22.40		2
	1	0	22.14	22.61	22.46		2
	1	12	22.27	22.61	22.22	0-2	2
	1	24	22.18	22.40	22.15		2
64QAM	12	0	21.47	21.49	21.35		3
	12	6	21.68	21.54	21.24	0-3	3
	12	13	21.50	21.53	21.06	0-3	3
	25	0	21.41	21.46	21.18		3

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Modulation	RB Size	RB Offset	Low Channel	Mid Channel	High Channel	MPR Allowed per	MPR [dB]		
			26705	26865	27025				
modulation	ND 0120	TED Onset	(815.5 MHz)	(831.5 MHz)	(847.5 MHz)	3GPP [dB]	mi iv [ab]		
			(Conducted Power [dBm]				
	1	0	24.14	24.40	24.34	0	0		
	1	7	24.26	24.44	24.25		0		
QPSK	1	14	24.30	24.46	24.07		0		
	8	0	23.44	23.51	23.46	0-1	1		
	8	4	23.53	23.58	23.50		1		
	8	7	23.45	23.60	23.42		1		
	15	0	23.50	23.54	23.45		1		
	1	0	23.26	23.78	23.45	0-1	1		
	1	7	23.49	23.75	23.34		1		
	1	14	23.53	23.77	23.17		1		
16QAM	8	0	22.42	22.59	22.54	0-2	2		
	8	4	22.63	22.60	22.57		2		
	8	7	22.53	22.60	22.49		2		
	15	0	22.47	22.53	22.44		2		
	1	0	22.08	22.68	22.07	0-2	2		
	1	7	22.18	22.52	22.15		2		
	1	14	22.32	22.56	22.01		2		
64QAM	8	0	21.17	21.63	21.25	0-3	3		
	8	4	21.39	21.63	21.11		3		
	8	7	21.43	21.65	21.25		3		
	15	0	21.42	21.57	21.28		3		

Table 8-17 LTE Band 26 (831.5MHz) Conducted Powers – 3MHz Bandwidth

Table 8-18

LTE Band 26 (831.5MHz) Conducted Powers – 1.4MHz Bandwidth

			20 (00			E Bunamath	
Modulation	RB Size	RB Offset	Low Channel 26697 (814.7 MHz)	Mid Channel 26865 (831.5 MHz)	High Channel 27033 (848.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm	1		
QPSK	1	0	24.40	24.22	24.30	0	0
	1	2	24.53	24.34	24.39		0
	1	5	24.49	24.26	24.15		0
	3	0	24.47	24.27	24.30		0
	3	2	24.58	24.33	24.25		0
	3	3	24.56	24.26	24.14		0
	6	0	23.71	23.36	23.36	0-1	1
16QAM	1	0	23.59	23.51	23.46	0-1	1
	1	2	23.73	23.63	23.39		1
	1	5	23.73	23.53	23.24		1
	3	0	23.38	23.30	23.36		1
	3	2	23.54	23.40	23.31		1
	3	3	23.58	23.31	23.20		1
	6	0	22.79	22.41	22.43	0-2	2
64QAM	1	0	22.26	22.50	22.26	0-2	2
	1	2	22.32	22.57	22.29		2
	1	5	22.48	22.43	22.11		2
	3	0	22.34	22.40	22.19		2
	3	2	22.43	22.40	22.22		2
	3	3	22.25	22.37	22.11		2
	6	0	21.34	21.40	21.69	0-3	3

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f. LTE Band 66

ETE Dana do (1745.0012) Conducted Towers – Zomriz Danawidth										
			Low Channel	Mid Channel	High Channel					
Modulation	RB Size	RB Offset	132072	132322	132572	MPR Allowed per	MPR [dB]			
modulation	IND OIZE	IND ONSET	(1720.0 MHz)	(1745.0 MHz)	(1770.0 MHz)	3GPP [dB]	Mill IX [GD]			
			(Conducted Power [dBm]					
	1	0	24.32	24.16	24.08		0			
	1	50	24.25	24.13	24.05	0	0			
	1	99	23.97	24.26	24.14		0			
QPSK	50	0	23.26	23.41	23.29		1			
	50	25	23.24	23.34	23.30	0.1	1			
	50	50	23.21	23.32	23.27	0-1	1			
	100	0	23.21	23.38	23.40		1			
	1	0	23.25	23.32	23.24	0-1	1			
	1	50	23.14	23.50	23.23		1			
	1	99	23.25	23.14	23.27		1			
16QAM	50	0	22.29	22.38	22.50		2			
	50	25	22.30	22.41	22.36	0-2	2			
	50	50	22.22	22.36	22.31	0-2	2			
	100	0	22.16	22.38	22.40		2			
	1	0	22.26	22.38	22.43		2			
	1	50	22.18	22.24	22.50	0-2	2			
	1	99	22.32	22.29	22.33		2			
64QAM	50	0	21.39	21.48	21.32		3			
	50	25	21.15	21.36	21.34	0-3	3			
	50	50	21.26	21.35	21.28		3			
	100	0	21.18	21.46	21.41		3			

Table 8-19 LTE Band 66 (1745.0MHz) Conducted Powers – 20MHz Bandwidth

Table 8-20

LTE Band 66 (1745.0MHz) Conducted Powers – 15MHz Bandwidth

			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	132047 (1717.5 MHz)	132322 (1745.0 MHz)	132597 (1772.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm]		
	1	0	24.22	24.30	24.33		0
	1	36	24.12	24.25	24.24	0	0
	1	74	24.11	24.32	24.09		0
QPSK	36	0	23.35	23.49	23.37		1
	36	18	23.33	23.48	23.38	0-1	1
	36	37	23.29	23.43	23.32	- 0-1	1
	75	0	23.33	23.47	23.35		1
	1	0	23.30	23.41	23.34	0-1	1
	1	36	23.26	23.36	23.36		1
	1	74	23.25	23.39	23.23		1
16QAM	36	0	22.15	22.28	22.20		2
	36	18	22.15	22.28	22.17	0-2	2
	36	37	22.07	22.24	22.13	0-2	2
	75	0	22.10	22.28	22.18		2
	1	0	22.25	22.40	22.34		2
	1	36	22.19	22.37	22.28	0-2	2
	1	74	22.26	22.40	22.09		2
64QAM	36	0	21.18	21.31	21.23		3
	36	18	21.17	21.33	21.17	0-3	3
	36	37	21.14	21.27	21.18	0-5	3
	75	0	21.12	21.26	21.20		3

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			Low Channel 132022	Mid Channel 132322	High Channel 132622	MPR Allowed per		
Modulation	RB Size	RB Offset	(1715.0 MHz)	(1745.0 MHz)	(1775.0 MHz)	3GPP [dB]	MPR [dB]	
			. ,	Conducted Power [dBm				
	1	0	23.85	24.10	23.77		0	
	1	25	23.94	24.10	23.94	0	0	
	1	49	24.02	24.07	23.96		0	
QPSK	25	0	23.10	23.28	23.18	0-1	1	
	25	12	23.10	23.28	23.11		1	
	25	25	23.04	23.28	23.12		1	
	50	0	23.10	23.32	23.17		1	
	1	0	23.26	23.45	23.39	0-1	1	
	1	25	23.30	23.43	23.31		1	
	1	49	23.34	23.50	23.31		1	
16QAM	25	0	22.16	22.34	22.21	-	2	
	25	12	22.15	22.35	22.21	0-2	2	
	25	25	22.12	22.31	22.18	0-2	2	
	50	0	22.12	22.36	22.21		2	
	1	0	22.24	22.40	22.28		2	
	1	25	22.33	22.43	22.31	0-2	2	
	1	49	22.28	22.45	22.33		2	
64QAM	25	0	21.17	21.35	21.26		3	
	25	12	21.17	21.39	21.25	0-3	3	
	25	25	21.09	21.31	21.19		3	
	50	0	21.17	21.35	21.23		3	

Table 8-21 LTE Band 66 (1745.0MHz) Conducted Powers – 10MHz Bandwidth

Table 8-22

LTE Band 66 (1745.0MHz) Conducted Powers – 5MHz Bandwidth

			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	131997 (1712.5 MHz)	132322 (1745.0 MHz)	132647 (1777.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Conducted Power [dBm	•		
	1	0	23.94	24.12	24.00		0
	1	12	24.02	24.20	24.04	0	0
	1	24	24.07	24.28	23.99		0
QPSK	12	0	23.08	23.27	23.15	0-1	1
	12	6	23.17	23.29	23.19		1
	12	13	23.13	23.36	23.17		1
	25	0	23.16	23.33	23.20		1
	1	0	23.24	23.36	23.23	0-1	1
	1	12	23.41	23.42	23.32		1
	1	24	23.45	23.46	23.26		1
16QAM	12	0	22.14	22.35	22.26		2
	12	6	22.14	22.36	22.28	0-2	2
	12	13	22.12	22.37	22.26	0-2	2
	25	0	22.15	22.33	22.20		2
	1	0	22.22	22.35	22.30		2
	1	12	22.35	22.47	22.32	0-2	2
	1	24	22.34	22.50	22.33		2
64QAM	12	0	21.17	21.33	21.23		3
	12	6	21.17	21.34	21.22	0-3	3
	12	13	21.14	21.32	21.24		3
	25	0	21.16	21.28	21.21		3

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			Low Channel	Mid Channel	High Channel				
Modulation	RB Size	RB Offset	131987	132322	132657	MPR Allowed per	MPR [dB]		
woodation	ND 5126	KD Oliset	(1711.5 MHz)	(1745.0 MHz)	(1778.5 MHz)	3GPP [dB]			
			(Conducted Power [dBm]				
	1	0	24.19	24.27	24.27		0		
	1	7	24.27	24.34	24.21	0	0		
	1	14	24.30	24.36	24.23		0		
QPSK	8	0	23.31	23.48	23.43		1		
	8	4	23.42	23.43	23.47		1		
	8	7	23.42	23.46	23.44	0-1	1		
	15	0	23.42	23.43	23.43		1		
	1	0	23.26	23.36	23.37	0-1	1		
	1	7	23.38	23.40	23.38		1		
	1	14	23.38	23.42	23.33		1		
16QAM	8	0	22.21	22.38	22.34		2		
	8	4	22.29	22.40	22.33	0-2	2		
	8	7	22.27	22.40	22.33	0-2	2		
	15	0	22.20	22.29	22.27		2		
	1	0	22.30	22.38	22.32		2		
	1	7	22.45	22.50	22.38	0-2	2		
	1	14	22.38	22.47	22.31		2		
64QAM	8	0	21.21	21.37	21.35		3		
	8	4	21.33	21.43	21.31	0-3	3		
	8	7	21.32	21.45	21.29		3		
	15	0	21.25	21.30	21.27		3		

Table 8-23 LTE Band 66 (1745.0MHz) Conducted Powers – 3MHz Bandwidth

 Table 8-24

 LTE Band 66 (1745.0MHz) Conducted Powers – 1.4MHz Bandwidth

			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	131979 (1710.7 MHz)	132322 (1745.0 MHz)	132665 (1779.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm]		
	1	0	24.14	24.26	24.14		0
	1	2	24.25	24.33	24.19		0
	1	5	24.21	24.29	24.18	0	0
QPSK	3	0	24.22	24.38	24.21		0
	3	2	24.30	24.45	24.30		0
	3	3	24.26	24.38	24.23		0
	6	0	23.36	23.50	23.35		1
	1	0	23.26	23.38	23.28	0-1	1
	1	2	23.36	23.49	23.32		1
	1	5	23.31	23.47	23.31		1
16QAM	3	0	23.25	23.32	23.17		1
	3	2	23.27	23.38	23.23		1
	3	3	23.19	23.35	23.17		1
	6	0	22.23	22.36	22.27	0-2	2
	1	0	22.27	22.40	22.31		2
	1	2	22.39	22.47	22.32		2
	1	5	22.33	22.44	22.29	0-2	2
64QAM	3	0	22.26	22.35	22.26	- 0-2	2
	3	2	22.34	22.42	22.27		2
	3	3	22.28	22.41	22.27		2
	6	0	21.18	21.30	21.17	0-3	3

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g. LTE Band 25

Modulation	RB Size	RB Offset	Low Channel 26140 (1860.0 MHz)	Mid Channel 26365 (1882.5 MHz) Conducted Power [dBn	High Channel 26590 (1905.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]	
	1	0	23.63	23.67	23.51		0	
	1	-				0		
	1	50	23.67	23.69	23.54	0	0	
	1	99	23.72	23.56	23.45		0	
QPSK	50	0	22.71	22.68	22.49		1	
	50	25	22.82	22.79	22.59	0-1	1	
	50	50	22.83	22.75	22.63		1	
	100	0	22.77	22.72	22.58		1	
	1	0	22.91	22.87	22.59	0-1	1	
	1	50	22.86	22.85	22.66		1	
	1	99	22.97	22.56	22.72		1	
16QAM	50	0	21.75	21.70	21.47		2	
	50	25	21.67	21.73	21.59	0-2	2	
	50	50	21.70	21.75	21.60	0-2	2	
	100	0	21.72	21.71	21.54		2	
	1	0	21.82	21.64	21.53		2	
	1	50	21.86	21.91	21.76	0-2	2	
	1	99	21.86	21.84	21.78		2	
64QAM	50	0	20.70	20.65	20.55		3	
	50	25	20.70	20.78	20.64	0-3	3	
	50	50	20.77	20.81	20.64	0-3	3	
L	100	0	20.72	20.69	20.58		3	

Table 8-25 LTE Band 25 (1882.5MHz) Conducted Powers – 20MHz Bandwidth

Table 8-26

LTE Band 25 (1882.5MHz) Conducted Powers – 15MHz Bandwidth

			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	26115	26365	26615	MPR Allowed per	MPR [dB]
modulation	112 0120		(1857.5 MHz)	(1882.5 MHz)	(1907.5 MHz)	3GPP [dB]	in refact
			(Conducted Power [dBm]		
	1	0	23.66	23.83	23.63	0	0
	1	36	23.77	23.80	23.63		0
	1	74	23.84	23.81	23.71		0
QPSK	36	0	22.87	22.88	22.66	0-1	1
	36	18	22.92	22.95	22.79		1
	36	37	22.96	22.98	22.80		1
	75	0	22.95	22.92	22.77		1
	1	0	22.84	23.00	22.76	0-1	1
	1	36	22.90	22.91	22.76		1
	1	74	22.96	22.91	22.78		1
16QAM	36	0	21.78	21.76	21.55		2
	36	18	21.83	21.85	21.62	0-2	2
	36	37	21.86	21.83	21.66	0-2	2
	75	0	21.78	21.80	21.60		2
	1	0	21.80	21.97	21.70		2
	1	36	21.93	21.98	21.71	0-2	2
	1	74	21.99	21.86	21.82		2
64QAM	36	0	20.69	20.80	20.57	0-3	3
	36	18	20.81	20.88	20.66		3
	36	37	20.84	20.87	20.71		3
	75	0	20.82	20.79	20.62		3

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Modulation	RB Size	RB Offset	Low Channel 26090 (1855.0 MHz)	Mid Channel 26365 (1882.5 MHz)	High Channel 26640 (1910.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Conducted Power [dBn			
	1	0	23.73	23.77	23.53		0
	1	25	23.66	23.76	23.57	0	0
	1	49	23.78	23.76	23.67		0
QPSK	25	0	22.86	22.90	22.66		1
	25	12	22.94	22.93	22.72	0-1	1
	25	25	22.96	22.88	22.73	0-1	1
	50	0	22.88	22.90	22.71		1
	1	0	22.79	22.86	22.64	0-1	1
	1	25	22.84	22.87	22.70		1
	1	49	22.90	22.89	22.89		1
16QAM	25	0	21.70	21.75	21.52		2
	25	12	21.72	21.80	21.58	0-2	2
	25	25	21.75	21.79	21.61	0-2	2
	50	0	21.74	21.75	21.54		2
	1	0	21.80	21.90	21.59		2
	1	25	21.80	21.90	21.71	0-2	2
	1	49	21.92	21.81	21.76		2
64QAM	25	0	20.70	20.75	20.53	0-3	3
	25	12	20.72	20.79	20.57		3
	25	25	20.72	20.80	20.60		3
L	50	0	20.76	20.78	20.58		3

Table 8-27 LTE Band 25 (1882.5MHz) Conducted Powers – 10MHz Bandwidth

Table 8-28 LTE Band 25 (1882.5MHz) Conducted Powers – 5MHz Bandwidth

			Low Channel 26065	Mid Channel 26365	High Channel 26665	MPR Allowed per		
Modulation	RB Size	RB Offset	(1852.5 MHz)	(1882.5 MHz)	(1912.5 MHz)	3GPP [dB]	MPR [dB]	
				Conducted Power [dBm]				
	1	0	23.76	23.82	23.61		0	
	1	12	23.84	23.90	23.70	0	0	
	1	24	23.89	23.83	23.65		0	
QPSK	12	0	22.92	22.96	22.75		1	
	12	6	22.95	22.99	22.86	0-1	1	
	12	13	22.99	22.97	22.85	0-1	1	
	25	0	22.99	22.93	22.82		1	
	1	0	22.87	22.94	22.65	0-1	1	
	1	12	22.92	23.00	22.78		1	
	1	24	22.95	22.98	22.74		1	
16QAM	12	0	21.71	21.78	21.57		2	
	12	6	21.85	21.86	21.68	0-2	2	
	12	13	21.86	21.81	21.70	0-2	2	
	25	0	21.72	21.72	21.63		2	
	1	0	21.83	21.87	21.65		2	
	1	12	21.97	21.94	21.74	0-2	2	
	1	24	21.93	21.89	21.69	1	2	
64QAM	12	0	20.74	20.79	20.57	0-3	3	
	12	6	20.71	20.81	20.56		3	
	12	13	20.75	20.79	20.58		3	
	25	0	20.83	20.75	20.62		3	

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Modulation	RB Size	RB Offset	Low Channel 26055 (1851.5 MHz)	Mid Channel 26365 (1882.5 MHz)	High Channel 26675 (1913.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]	
				Conducted Power [dBm		• • •		
	1	0	23.73	23.77	23.52		0	
	1	7	23.76	23.89	23.65	0	0	
	1	14	23.80	23.83	23.66		0	
QPSK	8	0	22.90	22.97	22.76		1	
	8	4	22.98	22.99	22.83	0-1	1	
	8	7	22.96	22.97	22.83	0-1	1	
	15	0	22.95	22.99	22.77		1	
	1	0	22.82	22.93	22.60	0-1	1	
	1	7	22.94	23.00	22.75		1	
	1	14	22.91	22.95	22.80		1	
16QAM	8	0	21.77	21.79	21.60		2	
	8	4	21.82	21.87	21.65	0-2	2	
	8	7	21.84	21.87	21.68	0-2	2	
	15	0	21.74	21.82	21.57		2	
	1	0	21.82	21.84	21.69		2	
	1	7	21.82	21.87	21.73	0-2	2	
	1	14	21.91	21.97	21.78		2	
64QAM	8	0	20.76	20.82	20.58	0-3	3	
	8	4	20.75	20.78	20.58		3	
	8	7	20.77	20.82	20.58		3	
	15	0	20.75	20.78	20.60		3	

Table 8-29 LTE Band 25 (1882.5MHz) Conducted Powers – 3MHz Bandwidth

 Table 8-30

 LTE Band 25 (1882.5MHz) Conducted Powers – 1.4MHz Bandwidth

Modulation	RB Size	RB Offset	Low Channel 26047 (1850.7 MHz)	Mid Channel 26365 (1882.5 MHz)	High Channel 26683 (1914.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm]		
	1	0	23.68	23.76	23.57		0
	1	2	23.78	23.82	23.68		0
	1	5	23.75	23.75	23.64	0	0
QPSK	3	0	23.76	23.80	23.62	U	0
	3	2	23.81	23.87	23.66	0-1	0
	3	3	23.81	23.80	23.63		0
	6	0	22.83	22.89	22.69		1
	1	0	22.83	22.83	22.67	0-1	1
	1	2	22.92	22.86	22.79		1
	1	5	22.87	22.87	22.77		1
16QAM	3	0	22.71	22.78	22.61		1
	3	2	22.81	22.84	22.65		1
	3	3	22.71	22.81	22.61		1
	6	0	21.68	21.83	21.57	0-2	2
	1	0	21.86	21.86	21.66		2
	1	2	21.86	21.94	21.78		2
	1	5	21.82	21.87	21.75	0-2	2
64QAM	3	0	21.74	21.83	21.60		2
	3	2	21.75	21.81	21.63		2
	3	3	21.73	21.81	21.61		2
	6	0	20.70	20.74	20.51	0-3	3

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h. LTE Band 30

Modulation	RB Size	RB Offset	Mid Channel 27710 (2310.0 MHz) Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	24.64		0
	1	25	24.68	0	0
	1	49	24.57		0
QPSK	25	0	23.76		1
	25	12	23.70	0-1	1
	25	25	23.68	0-1	1
	50	0	23.73		1
	1	0	23.74		1
	1	25	23.39	0-1	1
	1	49	23.73		1
16QAM	25	0	22.73		2
	25	12	22.69	0-2	2
	25	25	22.70	0-2	2
	50	0	22.74		2
	1	0	22.62		2
	1	25	22.75	0-2	2
	1	49	22.91		2
64QAM	25	0	21.67		3
	25	12	21.72	0-3	3
	25	25	21.77	0-3	3
	50	0	21.71		3

Table 8-31 LTE Band 30 (2310.0MHz) Conducted Powers – 10MHz Bandwidth

Table 8-32 LTE Band 30 (2310.0MHz) Conducted Powers - 5MHz Bandwidth

Modulation	RB Size	RB Offset	Mid Channel 27710 (2310.0 MHz) Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	24.50		0
	1	12	24.48	0	0
	1	24	24.39		0
QPSK	12	0	23.78		1
	12	6	23.74	0-1	1
	12	13	23.69	0-1	1
	25	0	23.74		1
	1	0	23.93		1
	1	12	23.81	0-1	1
	1	24	23.68		1
16QAM	12	0	22.81		2
	12	6	22.75	0-2	2
	12	13	22.70	0-2	2
	25	0	22.69		2
	1	0	22.86		2
	1	12	22.89	0-2	2
	1	24	22.73		2
64QAM	12	0	21.80		3
	12	6	21.77	0-3	3
	12	13	21.70	0-3	3
	25	0	21.71		3

Note: Since LTE Band 30 at 5MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

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i. LTE Band 7

	LIE Band / (2535.0MHZ) Conducted Powers – 20MHZ Bandwidth								
			Low Channel	Mid Channel	High Channel				
Modulation	RB Size	RB Offset	20850	21100	21350	MPR Allowed per	MPR [dB]		
modulation		ND Onset	(2510.0 MHz)	(2535.0 MHz)	(2560.0 MHz)	3GPP [dB]			
				Conducted Power [dBm]				
	1	0	24.09	24.30	24.06		0		
	1	50	24.09	24.12	24.11	0	0		
	1	99	24.13	24.09	24.37		0		
QPSK	50	0	23.18	23.37	23.34		1		
	50	25	23.28	23.33	23.33	0-1	1		
	50	50	23.34	23.25	23.38	0-1	1		
	100	0	23.28	23.31	23.33		1		
	1	0	23.35	23.44	23.31	0-1	1		
	1	50	23.37	23.32	23.37		1		
	1	99	23.37	23.37	23.60		1		
16QAM	50	0	22.18	22.32	22.32		2		
	50	25	22.28	22.28	22.32	0-2	2		
	50	50	22.34	22.22	22.35	0-2	2		
	100	0	22.24	22.25	22.30		2		
	1	0	22.26	22.47	22.26		2		
	1	50	22.29	22.30	21.96	0-2	2		
	1	99	22.31	22.33	22.43		2		
64QAM	50	0	21.14	21.31	20.90		3		
	50	25	21.26	21.30	20.88	0-3	3		
	50	50	21.32	21.24	21.18		3		
	100	0	21.23	21.28	21.05		3		

Table 8-33 LTE Band 7 (2535.0MHz) Conducted Powers – 20MHz Bandwidth

Table 8-34

LTE Band 7 (2535.0MHz) Conducted Powers – 15MHz Bandwidth

Modulation	RB Size	RB Offset	Low Channel 20825 (2507.5 MHz)	Mid Channel 21100 (2535.0 MHz)	High Channel 21375 (2562.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			C	Conducted Power [dBm]		
	1	0	24.03	24.22	24.16		0
	1	36	24.01	24.07	24.19	0	0
	1	74	24.16	23.95	24.36		0
QPSK	36	0	23.26	23.37	23.32		1
	36	18	23.30	23.36	23.39	0-1	1
	36	37	23.32	23.22	23.44	0-1	1
	75	0	23.28	23.28	23.40		1
	1	0	23.32	23.52	23.44	0-1	1
	1	36	23.33	23.40	23.50		1
	1	74	23.40	23.34	23.57		1
16QAM	36	0	22.25	22.37	22.36		2
	36	18	22.31	22.33	22.38	0-2	2
	36	37	22.34	22.26	22.44	0-2	2
	75	0	22.28	22.32	22.39		2
	1	0	22.33	22.50	22.04		2
	1	36	22.35	22.44	21.89	0-2	2
	1	74	22.40	22.26	22.18		2
64QAM	36	0	21.25	21.41	20.88	0-3	3
	36	18	21.32	21.36	20.97		3
	36	37	21.32	21.26	21.21		3
	75	0	21.26	21.31	20.87		3

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			. (2000.0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.0.	oonaaotoa i t		2 Bunamath		
Modulation	RB Size	RB Offset	Low Channel 20800 (2505.0 MHz)	Mid Channel 21100 (2535.0 MHz)	High Channel 21400 (2565.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]	
			(Conducted Power [dBm]			
	1	0	24.11	24.29	24.14		0	
	1	25	24.18	24.22	24.12	0	0	
	1	49	24.18	24.11	24.37		0	
QPSK	25	0	23.40	23.48	23.35		1	
	25	12	23.39	23.46	23.38	0-1	1	
	25	25	23.38	23.34	23.43	0-1	1	
	50	0	23.39	23.44	23.38		1	
	1	0	23.54	23.56	23.41		1	
	1	25	23.53	23.50	23.52	0-1	1	
	1	49	23.60	23.44	23.58		1	
16QAM	25	0	22.39	22.48	22.35		2	
	25	12	22.40	22.48	22.40	0-2	2	
	25	25	22.37	22.38	22.41	0-2	2	
	50	0	22.40	22.43	22.40		2	
	1	0	22.53	22.58	21.96		2	
	1	25	22.42	22.46	22.39	0-2	2	
	1	49	22.49	22.43	22.31		2	
64QAM	25	0	21.39	21.50	21.07		3	
	25	12	21.43	21.45	21.28	0.2	3	
	25	25	21.41	21.37	21.28	0-3	3	
	50	0	21.40	21.45	21.03		3	

Table 8-35 LTE Band 7 (2535.0MHz) Conducted Powers – 10MHz Bandwidth

 Table 8-36

 LTE Band 7 (2535.0MHz) Conducted Powers – 5MHz Bandwidth

Modulation	RB Size	RB Offset	Low Channel 20775 (2502.5 MHz)	Mid Channel 21100 (2535.0 MHz) Conducted Power [dBm	High Channel 21425 (2567.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]			
	1	0	24.07	24.14	24.14		0			
-	1	12	24.07	24.14	24.14	0	0			
	1	24				0				
ODOK	•		24.06	24.19	24.43		0			
QPSK	12	0	23.31	23.36	23.35		1			
	12	6	23.35	23.43	23.53	0-1	1			
	12	13	23.29	23.37	23.57		1			
	25	0	23.28	23.39	23.45		1			
	1	0	23.41	23.53	23.46	0-1	1			
	1	12	23.51	23.57	23.60		1			
	1	24	23.51	23.52	23.58		1			
16QAM	12	0	22.34	22.40	22.39		2			
	12	6	22.42	22.49	22.59		2			
	12	13	22.34	22.42	22.58	0-2	2			
	25	0	22.28	22.40	22.43		2			
	1	0	22.43	22.47	22.16		2			
	1	12	22.50	22.55	22.39	0-2	2			
	1	24	22.45	22.51	22.23	Ţ	2			
64QAM	12	0	21.36	21.40	21.38		3			
	12	6	21.44	21.46	21.51	0-3	3			
	12	13	21.35	21.44	21.30	0-3	3			
	25	0	21.25	21.40	21.24		3			

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j. LTE Band 41 – Power Class 3

			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel				
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
				Co	nducted Power [dE	Bm]					
	1	0	23.53	23.38	23.16	23.42	23.35		0		
	1	50	23.60	23.34	23.17	23.28	23.41	0	0		
	1	99	23.63	23.36	23.14	23.01	23.55		0		
QPSK	50	0	22.78	22.59	22.38	22.45	22.55		1		
	50	25	22.84	22.58	22.38	22.47	22.61	0-1	1		
	50	50	22.83	22.55	22.35	22.37	22.70	0-1	1		
	100	0	22.72	22.58	22.41	22.55	22.70		1		
	1	0	22.78	22.55	22.45	22.78	22.66		1		
	1	50	22.69	22.62	22.46	22.58	22.56	0-1	1		
	1	99	22.90	22.57	22.43	22.48	22.92		1		
16QAM	50	0	21.78	21.50	21.41	21.60	21.66		2		
	50	25	21.85	21.62	21.50	21.46	21.66	0-2	2		
	50	50	21.82	21.55	21.42	21.41	21.69	0-2	2		
	100	0	21.83	21.58	21.36	21.47	21.71		2		
	1	0	21.62	21.53	21.22	21.32	21.34		2		
	1	50	21.49	21.35	21.23	21.31	21.41	0-2	2		
	1	99	21.69	21.14	21.08	21.18	21.65]	2		
64QAM	50	0	20.78	20.60	20.44	20.57	20.74		3		
	50	25	20.89	20.58	20.35	20.53	20.37	0-3	3		
	50	50	20.84	20.60	20.39	20.46	20.72	0-3	3		
	100	0	20.79	20.53	20.43	20.53	20.64]	3		

Table 8-37 LTE Band 41 (2593.0MHz) Conducted Powers – 20MHz Bandwidth

 Table 8-38

 LTE Band 41 (2593.0MHz) Conducted Powers – 15MHz Bandwidth

			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [dE	3m]			
	1	0	23.57	23.46	23.24	23.47	23.34		0
	1	36	23.47	23.38	23.18	23.27	23.36	0	0
	1	74	23.51	23.39	23.17	23.16	23.49		0
QPSK	36	0	22.70	22.61	22.37	22.48	22.53		1
	36	18	22.73	22.63	22.40	22.47	22.58	0-1	1
	36	37	22.73	22.59	22.40	22.38	22.62	0-1	1
	75	0	22.72	22.64	22.42	22.46	22.58		1
	1	0	22.66	22.52	22.29	22.51	22.40		1
	1	36	22.54	22.45	22.25	22.34	22.41	0-1	1
	1	74	22.57	22.41	22.25	22.22	22.62		1
16QAM	36	0	21.69	21.62	21.36	21.48	21.51		2
	36	18	21.73	21.63	21.40	21.46	21.58	0-2	2
	36	37	21.73	21.58	21.38	21.38	21.59	0-2	2
	75	0	21.74	21.62	21.40	21.44	21.58		2
	1	0	21.31	21.13	21.23	21.12	21.03		2
	1	36	21.21	21.11	21.18	20.97	21.07	0-2	2
	1	74	21.27	21.09	21.07	20.87	21.26		2
64QAM	36	0	20.66	20.57	20.35	20.44	20.48		3
	36	18	20.71	20.60	20.39	20.44	20.53	0-3	3
	36	37	20.68	20.55	20.36	20.36	20.56	0-3	3
	75	0	20.74	20.61	20.42	20.46	20.58]	3

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			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel					
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]			
				Co	nducted Power [dB	im]						
	1	0	23.52	23.46	23.33	23.39	23.39		0			
	1	25	23.48	23.50	23.34	23.36	23.38	0	0			
	1	49	23.44	23.37	23.17	23.22	23.27		0			
QPSK	25	0	22.68	22.62	22.46	22.53	22.53		1			
	25	12	22.69	22.63	22.46	22.51	22.54	0-1	1			
	25	25	22.63	22.57	22.42	22.46	22.48	0-1	1			
	50	0	22.68	22.64	22.48	22.53	22.53		1			
	1	0	22.67	22.55	22.41	22.48	22.43		1			
	1	25	22.59	22.56	22.40	22.40	22.45	0-1	1			
	1	49	22.63	22.51	22.33	22.37	22.36		1			
16QAM	25	0	21.60	21.57	21.39	21.44	21.44		2			
	25	12	21.62	21.56	21.39	21.44	21.44	0-2	2			
	25	25	21.57	21.53	21.34	21.38	21.40	0-2	2			
	50	0	21.71	21.64	21.49	21.54	21.53		2			
	1	0	21.29	21.14	21.05	21.10	21.10		2			
	1	25	21.24	21.20	21.04	21.08	21.08	0-2	2			
	1	49	21.19	21.14	20.97	21.01	21.00		2			
64QAM	25	0	20.70	20.68	20.51	20.56	20.56		3			
	25	12	20.72	20.67	20.50	20.55	20.56	0-3	3			
	25	25	20.67	20.64	20.44	20.52	20.52	0-3	3			
	50	0	20.69	20.65	20.47	20.53	20.54		3			

Table 8-39 LTE Band 41 (2593.0MHz) Conducted Powers – 10MHz Bandwidth

Table 8-40 LTE Band 41 (2593.0MHz) Conducted Powers – 5MHz Bandwidth

			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel					
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]			
				Co	onducted Power [dB	im]						
	1	0	23.62	23.50	23.31	23.32	23.57		0			
	1	12	23.61	23.45	23.35	23.38	23.57	0	0			
	1	24	23.61	23.43	23.35	23.35	23.60		0			
QPSK	12	0	22.68	22.52	22.29	22.37	22.60		1			
	12	6	22.73	22.58	22.35	22.40	22.69	0-1	1			
	12	13	22.70	22.54	22.37	22.45	22.65	0-1	1			
	25	0	22.70	22.50	22.33	22.39	22.67		1			
	1	0	22.67	22.55	22.33	22.42	22.60		1			
	1	12	22.68	22.52	22.33	22.45	22.59	0-1	1			
	1	24	22.67	22.50	22.40	22.46	22.62		1			
16QAM	12	0	21.74	21.55	21.32	21.40	21.59		2			
	12	6	21.74	21.57	21.36	21.39	21.70	0-2	2			
	12	13	21.72	21.51	21.39	21.45	21.68	0-2	2			
	25	0	21.64	21.45	21.27	21.33	21.57		2			
	1	0	21.34	21.17	21.07	21.25	21.31		2			
	1	12	21.29	21.16	20.97	21.00	21.25	0-2	2			
	1	24	21.32	21.14	21.02	21.02	21.27		2			
64QAM	12	0	20.71	20.55	20.35	20.38	20.59		3			
	12	6	20.74	20.58	20.35	20.41	20.68	0-3	3			
	12	13	20.75	20.52	20.41	20.45	20.67	0-3	3			
	25	0	20.76	20.55	20.37	20.42	20.67		3			

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k. LTE Band 38

_					
			Mid Channel		
			38000	MPR Allowed per	
Modulation	RB Size	RB Offset	(2595.0 MHz)	3GPP [dB]	MPR [dB]
			Conducted Power		
			[dBm]		
	1	0	24.00		0
	1	50	23.89	0	0
	1	99	23.87		0
QPSK	50	0	22.98		1
	50	25	23.00	0-1	1
	50	50	22.94	0-1	1
	100	0	22.95		1
	1	0	23.00		1
	1	50	22.86	0-1	1
	1	99	22.87		1
16QAM	50	0	21.99		2
	50	25	22.00	0-2	2
	50	50	21.95	0-2	2
	100	0	22.00		2
	1	0	21.71		2
	1	50	21.51	0-2	2
	1	99	21.48		2
64QAM	50	0	21.00		3
	50	25	20.99	0-3	3
	50	50	20.96	0-3	3
	100	0	20.94		3

 Table 8-41

 LTE Band 38 (2595.0MHz) Conducted Powers – 20MHz Bandwidth

 Table 8-42

 LTE Band 38 (2595.0MHz) Conducted Powers – 15MHz Bandwidth

			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	37825	38000	38175	MPR Allowed per	MPR [dB]
modulation			(2577.5 MHz)	(2595.0 MHz)	(2612.5 MHz)	3GPP [dB]	
			(Conducted Power [dBm	1]		
	1	0	24.31	24.03	24.07		0
	1	36	24.12	23.99	24.00	0	0
	1	74	24.06	23.96	23.93	1	0
QPSK	36	0	23.22	23.18	23.20		1
	36	18	23.31	23.20	23.24	0-1	1
	36	37	23.22	23.17	23.16	0-1	1
	75	0	23.26	23.21	23.21		1
	1	0	23.12	22.96	23.16	0-1	1
	1	36	23.03	22.94	23.00		1
	1	74	23.08	22.92	22.97		1
16QAM	36	0	22.24	22.03	22.14		2
	36	18	22.38	22.08	22.15	0-2	2
	36	37	22.25	21.97	22.10	0-2	2
	75	0	22.24	22.17	22.20		2
	1	0	22.00	21.81	21.85		2
	1	36	21.85	21.65	21.81	0-2	2
	1	74	21.78	21.83	21.70		2
64QAM	36	0	21.30	21.15	21.19	l	3
	36	18	21.31	21.06	21.22	0-3	3
	36	37	21.26	21.07	21.16	0-3	3
	75	0	21.32	21.12	21.19		3

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				Conductour		Banamaan		
			Low Channel	Mid Channel	High Channel			
Modulation	RB Size	RB Offset	37800	38000	38200	MPR Allowed per	MPR [dB]	
wouldtion		KD Oliset	(2575.0 MHz)	(2595.0 MHz)	(2615.0 MHz)	3GPP [dB]		
			(Conducted Power [dBm	1]			
	1	0	24.08	23.95	24.01		0	
	1	25	24.16	23.87	23.88	0	0	
	1	49	24.05	23.85	23.96		0	
QPSK	25	0	23.22	22.98	23.09		1	
	25	12	23.12	23.01	23.11	0-1	1	
	25	25	23.10	23.00	23.07	0-1	1	
	50	0	23.19	23.02	23.12		1	
	1	0	23.02	22.78	22.88		1	
	1	25	23.09	22.80	22.95	0-1	1	
	1	49	22.99	22.83	22.91		1	
16QAM	25	0	22.48	21.95	22.17		2	
	25	12	22.25	22.06	22.18	0-2	2	
	25	25	22.30	22.09	22.10	0-2	2	
	50	0	22.33	22.01	22.13		2	
	1	0	21.71	21.62	21.69		2	
	1	25	21.87	21.53	21.65	0-2	2	
	1	49	21.69	21.56	21.63		2	
64QAM	25	0	21.06	20.95	21.09		3	
	25	12	21.25	21.03	21.08	0-3	3	
	25	25	21.19	20.97	21.01	0-5	3	
	50	0	21.29	21.08	21.18		3	

Table 8-43 LTE Band 38 (2595.0MHz) Conducted Powers – 10MHz Bandwidth

Table 8-44

LTE Band 38 (2595.0MHz) Conducted Powers – 5MHz Bandwidth

			Low Channel	Mid Channel	High Channel			
Modulation	RB Size	RB Offset	37775	38000	38225	MPR Allowed per	MPR [dB]	
wouldtion	KD SIZE	KB Oliset	(2572.5 MHz)	(2595.0 MHz)	(2617.5 MHz)	3GPP [dB]		
			Conducted Power [dBm]					
	1	0	24.22	23.89	23.98		0	
	1	12	24.18	23.92	24.09	0	0	
	1	24	24.16	24.05	24.05		0	
QPSK	12	0	23.26	22.88	23.02		1	
	12	6	23.30	23.04	23.02	0-1	1	
	12	13	23.29	23.08	23.13	0-1	1	
	25	0	23.22	23.03	23.06		1	
	1	0	23.15	22.85	22.95		1	
	1	12	23.11	22.98	23.04	0-1	1	
	1	24	23.10	23.00	23.07		1	
16QAM	12	0	22.22	21.89	21.96		2	
	12	6	22.19	22.05	22.04	0-2	2	
	12	13	22.14	22.01	22.06	0-2	2	
	25	0	22.34	22.04	22.10		2	
	1	0	21.95	21.55	21.68		2	
	1	12	21.89	21.69	21.81	0-2	2	
	1	24	21.85	21.65	21.86		2	
64QAM	12	0	21.06	20.91	20.98		3	
	12	6	21.24	20.99	21.05	0-3	3	
-	12	13	21.22	21.09	21.13	0-3	3	
	25	0	21.26	21.02	21.03		3	

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I. LTE Uplink Carrier Aggregation

										<u> </u>						
					PCC				SCC						Power	
Con	nbination	PCC Band	PCC Bandwidth [MHz]		PCC (UL/DL) Frequency [MHz]		PCC UL# RB	PCC UL RB Offset	SCC Band	SCC Bandwidth [MHz]	SCC (UL/DL) Channel	SCC (UL/DL) Frequency [MHz]		SCC UL# RB	SCC UL RB Offset	LTE Tx.Power with UL CA Enabled
(CA_7C	LTE B7	20	21100	2535.0	16QAM	1	0	LTE B7	20	20902	2515.2	16QAM	1	99	23.67
C	A_66B	LTE B66	10	132322	1745.0	16QAM	1	0	LTE B66	10	132223	1735.1	16QAM	1	49	23.45
C	A_66C	LTE B66	20	132322	1745.0	16QAM	1	0	LTE B66	20	132124	1725.2	16qAM	1	99	23.76

Table 8-45 LTE FDD Uplink Two Component Carrier Aggregation Conducted Powers

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VII. WIFI Conducted Powers (SISO/MIMO)

Table 8-46

IEEE 802.11b/g/n/ax (2.4GHz, SISO) Reduced Average RF Power¹

2.4GHz Conducted Power [dBm]							
Freq [MHz]	Channel	IEEE Transmission Mode					
		802.11b	802.11g	802.11n	802.11ax(SU)		
2412	1	16.79	16.22	16.43	12.71		
2437	6	16.68	16.46	16.60	16.72		
2462	11	16.85	14.87	14.72	14.48		

 Table 8-47

 IEEE 802.11g/n/ax (2.4GHz, MIMO) Reduced Average RF Power¹

 2.4GHz Conducted Power [dBm]

	2.4Ghz Conducted Power [dbin]							
Freq [MHz]	Channel	IEEE Transmission Mode						
	Channer	802.11g	802.11n	802.11ax(SU)				
2412	1	19.43	19.24	16.61				
2437	6	19.66	19.69	16.94				
2462	11	18.11	18.11	16.93				

	Table 8-48							
IEE	IEEE 802.11a/n/ac/ax (5GHz, 20MHz BW, SISO) Reduced Average RF Power ¹							
	FOUL (2014) Considerate di Disersen [d/Drm1							

5GHz (20MHz) Conducted Power [dBm]								
Freq [MHz]	Channel		IEEE Transm	ission Mode				
Fied [winz]	onanner	802.11a	802.11n	802.11ac	802.11ax(SU)			
5180	36	13.42	13.96	13.95	13.71			
5200	40	13.93	13.93	13.93	13.90			
5220	44	13.86	13.81	13.97	13.72			
5240	48	13.95	13.95	13.93	13.68			
5260	52	13.96	13.83	13.95	13.67			
5280	56	13.95	13.93	13.91	13.78			
5300	60	13.95	13.87	13.92	13.73			
5320	64	13.82	13.64	13.73	13.67			
5500	100	13.71	13.89	13.60	13.60			
5600	120	13.67	13.67	13.70	13.40			
5620	124	13.93	13.96	13.60	13.91			
5720	144	13.92	13.90	13.95	13.93			
5745	149	13.74	13.62	13.69	13.91			
5785	157	13.80	13.76	13.84	13.64			
5825	165	13.64	13.65	13.64	13.47			

¹ Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios.

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	5GHz (20MHz) 802.11ax Conducted Power [dBm]								
Freq [MHz]	Channel		IEEE Transm	ission Mode					
	Channel	802.11a	802.11n	802.11ac	802.11ax (SU)				
5180	36	16.60	16.92	16.88	15.69				
5200	40	16.93	16.94	16.93	15.73				
5220	44	16.87	16.82	16.90	15.72				
5240	48	16.93	16.96	16.95	15.67				
5260	52	16.79	16.89	16.82	15.58				
5280	56	16.87	16.82	16.86	15.59				
5300	60	16.90	16.85	16.85	15.61				
5320	64	16.79	16.67	16.71	15.54				
5500	100	16.85	16.82	16.76	15.88				
5600	120	16.78	16.70	16.78	15.91				
5620	124	16.86	16.89	16.70	15.97				
5720	144	16.91	16.92	16.92	15.68				
5745	149	16.72	16.68	16.72	15.57				
5785	157	16.80	16.76	16.81	15.60				
5825	165	16.62	16.80	16.62	15.91				

Table 8-49 IEEE 802.11a/n/ac/ax (5GHz, 20MHz BW, MIMO) Reduced Average RF Power¹

Table 8-50

IEEE 802.11n/ac/ax (5GHz, 40MHz BW, SISO) Reduced Average RF Power¹

	5GHz (40MHz) Conducted Power [dBm]								
Freq [MHz]	Channel	IEEE	IEEE Transmission Mode						
Freq [winz]	Channel	802.11n	802.11ac	802.11ax(SU)					
5190	38	13.63	13.63	13.97					
5230	46	13.68	13.65	13.60					
5270	54	13.76	13.64	13.75					
5310	62	13.87	13.84	13.71					
5510	102	13.59	13.57	13.83					
5590	118	13.86	13.87	13.76					
5630	126	13.80	13.97	13.77					
5710	142	13.90	13.89	13.75					
5755	151	13.68	13.69	13.87					
5795	159	13.45	13.56	13.90					

 Table 8-51

 IEEE 802.11n/ac/ax (5GHz, 40MHz BW, MIMO) Reduced Average RF Power¹

	5GHz (40MHz) Conducted Power [dBm]										
Freg [MHz]	Channel	IEEE Transmission Mode									
Freq [winz]	Channer	802.11n	802.11ac	802.11ax (SU)							
5190	38	16.65	16.63	13.57							
5230	46	16.72	16.72	13.89							
5270	54	16.85	16.61	13.75							
5310	62 16.92		16.91	13.72							
5510	102	16.77	16.74	13.85							
5590	118	16.92	16.91	13.59							
5630	126	16.75	16.80	13.75							
5710	142	16.87	16.82	13.87							
5755	151	16.68	16.71	13.55							
5795	159	16.50	16.55	13.58							

¹ Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios.

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Freq [MHz]	Channel	IEEE Transm	ission Mode
		802.11ac	802.11ax(SU)
5210	42	12.69	12.46
5290	58	12.87	12.72
5530	106	12.86	12.75
5610	122	12.78	12.55
5690	138	12.82	12.72
5775	155	12.58	12.83

 Table 8-52

 IEEE 802.11ac/ax (5GHz, 80MHz BW, SISO) Reduced Average RF Power¹

 5GHz (80MHz) Conducted Power [dBm]

Table 8-53									
IEEE 802.11ac/ax (5GHz, 80	MHz BW, MIMO)	Reduced Average I	RF Power ¹						

5GHZ (80MHZ) Conducted Power [dBm]									
Freq [MHz]	Channel	IEEE Transm	ission Mode						
		802.11ac	802.11ax (SU)						
5210	42	12.56	12.92						
5290	58	12.76	12.59						
5530	106	15.84	12.87						
5610	122	15.83	12.81						
5690	138	15.61	12.96						
5775	155	15.73	12.76						

VIII. WIFI Conducted Powers for IEEE 802.11ax RU (SISO/MIMO)

E	E 802.11ax (2.4GHz, RU, SISO) Maximum Average RF P									
	RU Index	Tonnes	Ch. 1	Ch. 6	Ch. 11					
	0	26	13.97	13.65	13.92					
	4	26	13.56	13.71	13.97					
	8	26	13.63	13.99	13.99					
	37	52	14.90	14.83	14.61					
	38	52	14.92	14.89	14.53					
	40	52	14.72	14.97	14.59					
	53	106	15.79	15.72	15.98					
	54	106	15.64	15.87	15.90					
	61	242	11.46	16.58	11.95					

 Table 8-54

 IEEE 802.11ax (2.4GHz, RU, SISO) Maximum Average RF Power²

¹ Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios.

² Note: While this device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios, maximum conducted powers were used as a conservative measure in Section 8.VIII.

FCC ID: A3LSMF900F		HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename: 1M1907090118-12.A3L	Test Dates: 06/24/2019 - 06/28/2019	DUT Type: Portable Handset		Page 53 of 108
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RU Index	Tones	Ch. 1	Ch. 6	Ch. 11
0	26	13.89	13.94	13.53
4	26	13.92	13.57	13.58
8	26	13.44	13.78	13.69
37	52	14.96	14.52	14.38
38	52	14.68	14.81	14.95
40	52	14.58	14.45	14.95
53	106	15.74	15.76	15.54
54	106	15.98	15.76	15.78
61	242	15.40	16.91	15.39

 Table 8-55

 IEEE 802.11ax (2.4GHz, RU, MIMO) Maximum Average RF Power¹

Table 8-56

IEEE 802.11ax (5GHz, 20MHz BW, RU, SISO) Maximum Average RF Power¹

RU Index	Tones		UNII 1		RU Index	Tones	UNII 2A			
		Ch. 36	Ch. 40	Ch. 48			Ch. 52	Ch. 56	Ch. 64	
0	26	10.81	10.91	10.97	0	26	10.76	10.83	10.99	
4	26	10.99	10.98	10.83	4	26	10.97	10.57	10.67	
8	26	10.91	10.93	10.95	8	26	10.74	10.76	10.91	
37	52	12.90	12.98	12.76	37	52	12.75	12.87	12.93	
38	52	12.61	12.73	12.93	38	52	12.92	12.96	12.98	
40	52	12.98	12.99	12.79	40	52	12.79	12.90	12.89	
53	106	14.60	14.67	14.77	53	106	14.76	14.84	14.93	
54	106	14.67	14.70	14.80	54	106	14.78	14.79	14.80	
61	242	15.95	15.65	15.75	61	242	15.98	15.67	15.65	
RU Index	x Tones		UNII 2C		RU Index	Tones	UNII 3			
		01. 400								
-		Ch. 100	Ch. 120	Ch. 144			Ch. 149	Ch. 157	Ch. 165	
0	26	10.72	10.86	Ch. 144 10.75	0	26	Ch. 149 10.81	Ch. 157 10.56	Ch. 165 10.98	
0 4	26 26			-	0 4	26 26	-	-		
-	-	10.72	10.86	10.75		-	10.81	10.56	10.98	
4	26	10.72 10.80	10.86 10.89	10.75 10.90	4	26	10.81 10.77	10.56 10.94	10.98 10.74	
4	26 26	10.72 10.80 10.97	10.86 10.89 10.98	10.75 10.90 10.98	4 8	26 26	10.81 10.77 10.98	10.56 10.94 10.99	10.98 10.74 10.97	
4 8 37	26 26 52	10.72 10.80 10.97 12.89	10.86 10.89 10.98 12.99	10.75 10.90 10.98 12.97	4 8 37	26 26 52	10.81 10.77 10.98 12.81	10.56 10.94 10.99 12.74	10.98 10.74 10.97 12.95	
4 8 37 38	26 26 52 52	10.72 10.80 10.97 12.89 12.72	10.86 10.89 10.98 12.99 12.63	10.75 10.90 10.98 12.97 12.74	4 8 37 38	26 26 52 52	10.81 10.77 10.98 12.81 12.87	10.56 10.94 10.99 12.74 12.92	10.98 10.74 10.97 12.95 12.98	
4 8 37 38 40	26 26 52 52 52 52	10.72 10.80 10.97 12.89 12.72 12.77	10.86 10.89 10.98 12.99 12.63 12.95	10.75 10.90 10.98 12.97 12.74 12.95	4 8 37 38 40	26 26 52 52 52 52	10.81 10.77 10.98 12.81 12.87 12.92	10.56 10.94 10.99 12.74 12.92 12.98	10.98 10.74 10.97 12.95 12.98 12.87	

Table 8-57

IEEE 802.11ax (5GHz, 20MHz BW, RU, MIMO) Maximum Average RF Power¹

		···-, -·		,							
RU Index	Tones	UNII 1			RU Index	Tones	UNII 2A				
RUIndex	Tones	Ch. 36	Ch. 40	Ch. 48	RU Index	Tones	Ch. 52	Ch. 56	Ch. 64		
0	26	10.99	10.69	10.59	0	26	10.85	10.92	10.83		
4	26	10.82	10.76	10.70	4	26	10.58	10.69	10.65		
8	26	10.53	10.61	10.53	8	26	10.83	10.91	10.90		
37	52	12.62	12.58	12.63	37	52	12.99	12.99	12.99		
38	52	12.72	12.76	12.74	38	52	12.56	12.68	12.56		
40	52	12.60	12.53	12.65	40	52	12.98	12.50	12.48		
53	106	14.58	14.70	14.77	53	106	14.98	14.66	14.57		
54	106	14.69	14.71	14.73	54	106	14.49	14.68	14.51		
61	242	15.66	15.65	15.70	61	242	15.99	15.54	15.53		
Dilladau	Tones	UNII 2C			RU Index	Tones	UNII 3				
RU Index		Ch. 100	Ch. 120	Ch. 144	RU Index		Ch. 149	Ch. 157	Ch. 165		
0	26	10.99	10.95	10.99	0	0	0	26	10.85	10.81	10.64
4	26	10.66	10.60	10.74	4	26	10.95	10.92	10.97		
8	26	10.84	10.71	10.80	8	26	10.53	10.53	10.99		
37	52	12.53	12.92	12.99	37	52	12.82	12.78	12.59		
38	52	12.52	12.50	12.67	38	52	12.88	12.89	12.85		
40	52	12.70	12.74	12.90	40	52	12.99	12.99	12.52		
53	106	14.98	14.86	14.58	53	106	14.70	14.62	14.90		
					54	106	14.98	14.99	14.90		
54	106	14.90	14.78	14.95	54	106	14.90	14.99	14.50		

¹ Note: While this device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios, maximum conducted powers were used as a conservative measure in Section 8.VIII.

FCC ID: A3LSMF900F		HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager				
Filename:	Test Dates:	DUT Type:		Page 54 of 108				
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IEE	E 802.11ax (5GHZ, 40101HZ BW, RU					, κυ	, ວ ו	3	50) IV	iaxi	mum		erago	e Kr	· POV	ver				
	RU In	dov	Tor	10.6		UN	ll 1		PI		ndex	То	nnes		UNI	I 2A				
	KU III	uex	101	les	Ch	. 38	Ch	. 46	RU	' '	nuex	101	mes	Ch	. 5 4	Ch	n. 62			
	0		2	6	10	.77	10	.81			0	:	26	10).62	1().71			
	8		2	6	10	.93	10	.99			8		26	10).61	1().75			
	17	7	2	6	10	.81	10	.90			17	:	26	10).55	1().97			
	37	7	5	2	11	.98	11	.66		3	37		52	11	1.86	11	1.83			
	40)	5	2	11	.93	11	.97		4	40	-	52	11	1.65	11	1.77			
	44	Ļ	5	2	11	.99	11	.68		4	44	;	52	11	1.74	11	1.72			
	53	3	10)6	12	.89	12	.99		ţ	53	1	06	12	2.59	12	2.98			
	54	ļ	10)6	12	.95	12	.56		ţ	54	1	06	12	2.63	12	2.67			
	56	6	10)6	12	.84	12	.96		Ę	56	1	06	12	2.98	12	2.96			
	61		24			.95		.75		_	61		42		8.76		3.81			
	62		24			.99		.66			62		42		3.65		3.70			
	65	5	48	34	13	.93	13.98			6	65	484		13.55		1:	13.97			
RU	Index	To	nnes			UNI	I 2C				RU Ir	ndex	Ton	nes		-	II 3			
	muex	lex Ionn		C		Ch.	. 102	Ch. 118		Ch. 142		2					Ch.	151	Ch.	159
	0		26).97		.95	10.			C	-	2	-	10.		10.			
	8		26	-).91	-	.89	10.	-		8	-	2	-	10.		10.			
	17		26		.98	-	.92	10.				7	2	-	10.		10.			
	37		52		.72		.71	11.	-		_	7	5		11.		11.			
	40		52		.98		.94	11.		Ļ	4	-	5		11.		11.			
-	44		52		.65		.98	11.	-		4		5		11.		11.			
	53		06		2.74		.91	12.		1	5	-	10	-	12.		12.			
	54		06		2.88		.80	12.		Ļ	5		10	-	12.		12.			
	56		06		2.76		.86	12.			5	-	10	-	12.		12.			
	61		242		8.97		.98	13.		ł	6		24		13.		13.			
-	62 65		242 184		3.94 3.83		.97 .74	13. 13.			6		24 48		13. 13.		13. 13.			
	05	4	-04	13	0.00	13	.14	13.	92		0	5	40	4	13.	00	13.	09		

 Table 8-58

 IEEE 802.11ax (5GHz, 40MHz BW, RU, SISO) Maximum Average RF Power¹

FCC ID: A3LSMF900F		HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager			
Filename:	Test Dates:	DUT Type:		Dage EE of 100			
1M1907090118-12.A3L	06/24/2019 - 06/28/2019	Portable Handset		Page 55 of 108			
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	RU In				,		<u> </u>								I 2A		
	RUIN	aex	Tor	ies	Ch.	38	Ch.	46	RU	ndex	10	nes	Ch	. 54	Ch	. 62	
	0		2	6	10.	98	10.	94		0	:	26	10).73	10).77	
	8		2	6	10.	99	10.	88		8	:	26	10).68	10).67	
	17	7	2	6	10.	53	10.	99		17	:	26	10).67	10).52	
	37	7	5	2	11.	71	11.	64		37		52	11	1.99	11	.95	
	40)	5	2	11.	59	11.	48		40	4	52	11	1.73	11	.62	
	44		5		11.		11.	-		44		52		1.91		.88	
	53		10	-	12.		12.	-		53		06		2.90		2.84	
	54		10	-	12.		12.			54		06		2.75		2.75	
	56		10	-	12.		12.			56		06		2.72		2.62	
	6		24		13.		13.			61		42		3.99		3.46	
	62		24		13.		13.			62	_	42		3.97		3.47	
	65	5	48	34	13.		13.	50		65	4	84	13	3.66		3.60	
RUI	ndex	То	nes			-	II 2C			RU li	ndex	Tor	nes		-	11 3	
	•		20		102		. 118	Ch.			_	0	_	Ch.		Ch.	
	0 8		26 26).72).64).98		.75		0 B	2	-	10. 10.		10. 11.	
	o 17		20 26).61).59	-).90).61	-	.60		5 7	2	-	10.		11.	
	37		20 52		.99	-	.89	-	.99		7 57	5	-	10.	-	10.	
	40		52		.99		.89		.99		0	5		11.		11.	
	14		52		.82		.88		.00		4	5		11.		11.	
-	53		06		2.68		2.66		.78		53	10		12.	-	12.	
	54		06		2.59		2.99		.66		,0 54	10	-	12		12.	
	56		06		2.82		2.68		.68	-	i6	10	-	12.	-	12.	
	50 61		42		8.54		3.79		.85	-	51	24	-	13.		13.	
	62		42		8.67		3.91		.99		62	24	2	13.		13.	
6	65	4	84	12	2.75	13	3.66	13	.70	6	5	48	34	13.	.86	13.	94

 Table 8-59

 IEEE 802.11ax (5GHz, 40MHz BW, RU, MIMO) Maximum Average RF Power¹

FCC ID: A3LSMF900F		IAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager			
Filename:	Test Dates:	DUT Type:		Dage E6 of 100			
1M1907090118-12.A3L	06/24/2019 - 06/28/2019	Portable Handset		Page 56 of 108			
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IEEE 802.11ax (5GHz, 80MHz BW, RU, SISO) Maximum Average RF Power'							
	RU Index	Tones	UNII 1	RU Index	Tonnes	UNII 2A	
	KU IIIdex	Tones	Ch. 42	KO IIIdex	Tonnes	Ch. 58	
	0	26	10.87	0	26	10.51	
	17	26	10.83	17	26	10.99	
	36	26	10.91	36	26	10.98	
	37	52	10.97	37	52	10.45	
	44	52	10.98	44	52	10.94	
	52	52	10.60	52	52	10.98	
	53	106	11.76	53	106	11.63	
	56	106	11.96	56	106	11.95	
	60	106	11.82	60	106	11.65	
	61	242	12.93	61	242	12.94	
	62	242	12.99	62	242	12.54	
	64	242	12.98	64	242	12.92	
	65	484	12.70	65	484	12.72	
	66	484	12.90	66	484	12.86	
	67	996	12.89	67	996	12.79	
PUIndox	-	996	12.89 UNII 2C	67			UNII 3
RU Index	67 Tones	996 Ch. 106		67 Ch. 138	996 RU Index	12.79 Tones	UNII 3 Ch. 155
RU Index	-		UNII 2C				
	Tones	Ch. 106	UNII 2C Ch. 122	Ch. 138	RU Index	Tones	Ch. 155
0	Tones	Ch. 106 10.75	UNII 2C Ch. 122 10.97	Ch. 138 10.98	RU Index	Tones 26	Ch. 155 10.90
0 17	Tones 26 26	Ch. 106 10.75 10.72	UNII 2C Ch. 122 10.97 10.75	Ch. 138 10.98 10.96	RU Index 0 17	Tones 26 26	Ch. 155 10.90 10.94
0 17 36	Tones 26 26 26 26	Ch. 106 10.75 10.72 10.56	UNII 2C Ch. 122 10.97 10.75 10.60	Ch. 138 10.98 10.96 10.52	RU Index 0 17 36	Tones 26 26 26 26	Ch. 155 10.90 10.94 10.80
0 17 36 37	Tones 26 26 26 26 52	Ch. 106 10.75 10.72 10.56 10.72	UNII 2C Ch. 122 10.97 10.75 10.60 10.70	Ch. 138 10.98 10.96 10.52 10.75	RU Index 0 17 36 37	Tones 26 26 26 52	Ch. 155 10.90 10.94 10.80 10.98
0 17 36 37 44	Tones 26 26 26 52 52	Ch. 106 10.75 10.72 10.56 10.72 10.79	UNII 2C Ch. 122 10.97 10.75 10.60 10.70 10.77	Ch. 138 10.98 10.96 10.52 10.75 10.99	RU Index 0 17 36 37 44	Tones 26 26 26 52 52	Ch. 155 10.90 10.94 10.80 10.98 10.95
0 17 36 37 44 52	Tones 26 26 26 52 52 52	Ch. 106 10.75 10.72 10.56 10.72 10.79 10.76	UNII 2C Ch. 122 10.97 10.75 10.60 10.70 10.77 10.99	Ch. 138 10.98 10.96 10.52 10.75 10.99 10.83	RU Index 0 17 36 37 44 52	Tones 26 26 26 52 52 52	Ch. 155 10.90 10.94 10.80 10.98 10.95 10.92
0 17 36 37 44 52 53	Tones 26 26 26 52 52 52 52 106	Ch. 106 10.75 10.72 10.56 10.72 10.79 10.76 11.72	UNII 2C Ch. 122 10.97 10.75 10.60 10.70 10.77 10.99 11.70	Ch. 138 10.98 10.96 10.52 10.75 10.99 10.83 11.80	RU Index 0 17 36 37 44 52 53	Tones 26 26 26 52 52 52 52 106	Ch. 155 10.90 10.94 10.80 10.98 10.95 10.92 11.70
0 17 36 37 44 52 53 56	Tones 26 26 26 52 52 52 106 106	Ch. 106 10.75 10.72 10.56 10.72 10.79 10.76 11.72 11.77	UNII 2C Ch. 122 10.97 10.75 10.60 10.70 10.77 10.99 11.70 11.85	Ch. 138 10.98 10.96 10.52 10.75 10.99 10.83 11.80 11.99	RU Index 0 17 36 37 44 52 53 56	Tones 26 26 26 52 52 52 106 106	Ch. 155 10.90 10.94 10.80 10.98 10.95 10.92 11.70 11.99
0 17 36 37 44 52 53 56 60	Tones 26 26 26 52 52 52 106 106	Ch. 106 10.75 10.72 10.56 10.72 10.76 11.72 11.77 11.80	UNII 2C Ch. 122 10.97 10.75 10.60 10.70 10.77 10.99 11.70 11.85 11.60	Ch. 138 10.98 10.96 10.52 10.75 10.99 10.83 11.80 11.99 11.98	RU Index 0 17 36 37 44 52 53 56 60	Tones 26 26 26 52 52 52 106 106	Ch. 155 10.90 10.94 10.80 10.95 10.92 11.70 11.99 11.57
0 17 36 37 44 52 53 56 60 61	Tones 26 26 26 52 52 52 106 106 242	Ch. 106 10.75 10.72 10.56 10.72 10.76 11.72 11.77 11.80 12.72	UNII 2C Ch. 122 10.97 10.75 10.60 10.70 10.77 10.99 11.70 11.85 11.60 12.81	Ch. 138 10.98 10.96 10.52 10.75 10.99 10.83 11.80 11.99 11.98 12.99	RU Index 0 17 36 37 44 52 53 56 60 61	Tones 26 26 26 52 52 52 106 106 242	Ch. 155 10.90 10.94 10.80 10.98 10.95 10.92 11.70 11.57 12.94
0 17 36 37 44 52 53 56 60 61 62	Tones 26 26 26 52 52 52 106 106 242 242	Ch. 106 10.75 10.72 10.56 10.72 10.79 10.76 11.72 11.77 11.80 12.72 12.88	UNII 2C Ch. 122 10.97 10.75 10.60 10.70 10.77 10.99 11.70 11.85 11.60 12.81 12.95	Ch. 138 10.98 10.96 10.52 10.75 10.99 10.83 11.80 11.99 12.99 12.98	RU Index 0 17 36 37 44 52 53 56 60 61 62	Tones 26 26 26 52 52 52 106 106 242 242	Ch. 155 10.90 10.94 10.80 10.95 10.92 11.70 11.99 11.57 12.94 12.91
0 17 36 37 44 52 53 56 60 61 62 64	Tones 26 26 52 52 52 106 106 242 242 242 242	Ch. 106 10.75 10.72 10.56 10.72 10.76 11.72 11.77 11.80 12.72 12.88 12.99	UNII 2C Ch. 122 10.97 10.75 10.60 10.70 10.77 10.99 11.70 11.85 11.60 12.81 12.95 12.91	Ch. 138 10.98 10.96 10.52 10.75 10.99 10.83 11.80 11.99 12.99 12.98 12.71	RU Index 0 17 36 37 44 52 53 56 60 61 62 64	Tones 26 26 26 52 52 52 106 106 242 242 242 242	Ch. 155 10.90 10.94 10.80 10.95 10.92 11.70 11.99 11.57 12.94 12.91 12.87

 Table 8-60

 IFEE 802 11ax (5GHz 80MHz BW RU SISO) Maximum Average RE Power¹

FCC ID: A3LSMF900F		AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager			
Filename:	Test Dates:	DUT Type:		Dego EZ of 100			
1M1907090118-12.A3L	06/24/2019 - 06/28/2019	Portable Handset		Page 57 of 108			
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RU Index Tones Ch. 106 Ch. 122 Ch. 138 RU Index Tones Ch 0 26 10.78 10.56 10.71 0 26 1 18 26 10.78 10.62 10.74 18 26 1 36 26 10.52 10.54 10.58 36 26 1 37 52 10.97 10.79 10.86 37 52 1 44 52 10.79 10.73 10.77 52 52 1	111 2 4							
Ch. 42 Ch. 42 Ch. 58 0 26 10.98 0 26 10.60 18 26 10.58 18 26 10.72 36 26 10.94 36 26 10.62 37 52 10.58 37 52 10.72 44 52 10.93 44 52 10.71 52 52 10.57 52 52 10.71 53 106 11.80 53 106 11.62 56 106 11.80 53 106 11.87 60 106 11.84 60 106 11.87 61 242 12.87 62 242 12.86 62 242 12.63 64 242 12.83 65 484 12.91 65 484 12.53 66 484 12.97 66 484 12.63 67 996		UNII 2	Tanaa	Bilinday	UNII 1	Tonos	llindov	Ы
18 26 10.58 18 26 10.72 36 26 10.94 36 26 10.62 37 52 10.58 37 52 10.72 44 52 10.93 44 52 10.71 52 52 10.57 52 52 10.67 53 106 11.80 53 106 11.62 56 106 11.62 56 106 11.87 60 106 11.84 60 106 11.96 61 242 12.87 62 242 12.86 62 242 12.83 64 242 12.83 65 484 12.97 66 484 12.53 66 484 12.97 66 484 12.53 67 996 12.80 67 996 12.97 RU Index Tones Ch. 106 Ch. 102 Ch. 138 <t< th=""><th>h. 58</th><th>Ch. 5</th><th>Tones</th><th>RU Index</th><th>Ch. 42</th><th>Tones</th><th>to muex</th><th>ĸ</th></t<>	h. 58	Ch. 5	Tones	RU Index	Ch. 42	Tones	to muex	ĸ
36 26 10.94 36 26 10.62 37 52 10.58 37 52 10.72 44 52 10.93 44 52 10.71 52 52 10.57 52 52 10.67 53 106 11.80 53 106 11.62 56 106 11.62 56 106 11.87 60 106 11.84 60 106 11.96 61 242 12.87 62 242 12.86 62 242 12.87 62 242 12.88 65 484 12.97 66 484 12.58 66 484 12.97 66 484 12.63 67 996 12.80 67 996 12.97 RU 10.62 10.74 18 26 10.78	0.60	10.6	26	0	10.98	26	0	
37 52 10.58 37 52 10.72 44 52 10.93 44 52 10.71 52 52 10.57 52 52 10.67 53 106 11.80 53 106 11.62 56 106 11.62 56 106 11.87 60 106 11.84 60 106 11.87 61 242 12.87 62 242 12.86 62 242 12.87 62 242 12.89 64 242 12.87 64 242 12.88 65 484 12.97 66 484 12.53 66 484 12.97 66 484 12.97 RU Index Tones UNII 2C RU Index Ru Index $70es$ $70es$ 0 26 10.78 10.62	0.72	10.7	26	18	10.58	26	18	
44 52 10.93 44 52 10.71 52 52 10.57 52 52 10.67 53 106 11.80 53 106 11.62 56 106 11.62 56 106 11.87 60 106 11.84 60 106 11.87 61 242 12.54 61 242 12.86 62 242 12.87 62 242 12.89 64 242 12.63 64 242 12.88 65 484 12.91 65 484 12.53 66 484 12.97 66 484 12.63 67 996 12.80 67 996 12.97 VNII 2C VNI Mex 7 70 26 10.78 10.62 10.74 18 26 1 18 26 10.78 10.62 10.74 1	0.62	10.6	26	36	10.94	26	36	
52 52 10.57 52 52 10.67 53 106 11.80 53 106 11.62 56 106 11.62 56 106 11.87 60 106 11.84 60 106 11.87 60 106 11.84 60 106 11.87 61 242 12.54 61 242 12.86 62 242 12.87 62 242 12.99 64 242 12.63 64 242 12.88 65 484 12.97 66 484 12.58 66 484 12.97 66 484 12.63 67 996 12.80 67 996 12.97 RU Index Tones UNII 2C RU Index Tones U 18 26 10.78 10.62 10.74 18 26 1 36 26 10.52	0.72	10.7	52	37	10.58	52	37	
53 106 11.80 53 106 11.62 56 106 11.62 56 106 11.87 60 106 11.84 60 106 11.87 61 242 12.54 61 242 12.86 62 242 12.87 62 242 12.99 64 242 12.63 64 242 12.88 65 484 12.91 65 484 12.58 66 484 12.97 66 484 12.63 67 996 12.80 67 996 12.97 RU Index Tones UNII 2C RU Index Tones U 0 26 10.78 10.56 10.71 0 26 1 18 26 10.52 10.54 10.58 36 26 1 36 26 10.52 10.54 10.58 36 26 1	0.71	10.7	52	44	10.93	52	44	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	0.67	10.6	52	52	10.57	52	52	
$ \begin{array}{ c c c c c c c c } \hline 60 & 106 & 11.84 & 60 & 106 & 11.96 \\ \hline 61 & 242 & 12.54 & 61 & 242 & 12.86 \\ \hline 62 & 242 & 12.87 & 62 & 242 & 12.99 \\ \hline 64 & 242 & 12.63 & 64 & 242 & 12.88 \\ \hline 65 & 484 & 12.91 & 65 & 484 & 12.58 \\ \hline 66 & 484 & 12.91 & 65 & 484 & 12.58 \\ \hline 66 & 484 & 12.97 & 66 & 484 & 12.63 \\ \hline 67 & 996 & 12.80 & 67 & 996 & 12.97 \\ \hline \hline RU Index & Tones & UNII 2C & RU Index & Tones & UIII 2C \\ \hline 0 & 26 & 10.78 & 10.56 & 10.71 & 0 & 26 & 11 \\ \hline 18 & 26 & 10.78 & 10.62 & 10.74 & 18 & 26 & 11 \\ \hline 36 & 26 & 10.52 & 10.54 & 10.58 & 36 & 26 & 11 \\ \hline 37 & 52 & 10.97 & 10.79 & 10.86 & 37 & 52 & 11 \\ \hline 44 & 52 & 10.99 & 10.63 & 10.97 & 44 & 52 & 11 \\ \hline 52 & 52 & 10.79 & 10.73 & 10.77 & 52 & 52 & 11 \\ \hline \end{array}$	1.62	11.6	106	53	11.80	106	53	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	1.87	11.8	106	56	11.62	106	56	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	1.96	11.9	106	60	11.84	106	60	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	2.86	12.8	242	61	12.54	242	61	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	2.99	12.9	242	62	12.87	242	62	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	2.88	12.8	242	64	12.63	242	64	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	2.58	12.5	484	65	12.91	484	65	
RU Index Tones UNII 2C RU Index Tones UU 0 26 10.78 10.56 10.71 0 26 1 18 26 10.78 10.62 10.74 18 266 1 36 26 10.52 10.54 10.58 36 26 1 37 52 10.97 10.79 10.86 37 52 1 44 52 10.79 10.73 10.77 52 52 1	2.63	12.6	484	66	12.97	484	66	
RU Index Tones Ch. 106 Ch. 122 Ch. 138 RU Index Tones Ch 0 26 10.78 10.56 10.71 0 26 1 18 26 10.78 10.62 10.74 18 26 1 36 26 10.52 10.54 10.58 36 26 1 37 52 10.97 10.79 10.86 37 52 1 44 52 10.79 10.73 10.77 52 52 1	2.97	12.9	996	67	12.80	996	67	
Ch. 106 Ch. 122 Ch. 138 Ch. 138 Ch. 138 0 26 10.78 10.56 10.71 0 26 1 18 26 10.78 10.62 10.74 18 26 1 36 26 10.52 10.54 10.58 36 26 1 37 52 10.97 10.79 10.86 37 52 1 44 52 10.99 10.63 10.97 44 52 1 52 52 10.79 10.73 10.77 52 52 1	UNII 3	Tamaa	Dillinday		UNII 2C		Tanaa	Dillinday
182610.7810.6210.7418261362610.5210.5410.5836261375210.9710.7910.8637521445210.9910.6310.9744521525210.7910.7310.7752521	Ch. 155	Iones	RUIndex	Ch. 138	Ch. 122	Ch. 106	Tones	RUINdex
36 26 10.52 10.54 10.58 36 26 1 37 52 10.97 10.79 10.86 37 52 1 44 52 10.99 10.63 10.97 44 52 1 52 52 10.79 10.73 10.77 52 52 1	10.62	26	-				26	0
37 52 10.97 10.79 10.86 37 52 1 44 52 10.99 10.63 10.97 44 52 1 52 52 10.79 10.73 10.77 52 52 1	10.78	26	18	10.74			26	18
44 52 10.99 10.63 10.97 44 52 1 52 52 10.79 10.73 10.77 52 52 1	10.65						_	
52 52 10.79 10.73 10.77 52 52 1	10.73							
	10.44						-	
	10.70		-				-	
	11.78	106	53	11.58	11.96	11.68	106	53
	11.99						_	
	11.86						_	
	12.98	242	61	12.74	12.72	12.87	242	61
	12.74							
62 242 12.96 12.86 12.84 62 242 1	12.65	242		12.86	12.95	12.92		64
62 242 12.96 12.86 12.84 62 242 1 64 242 12.92 12.95 12.86 64 242 1	12.85							
62 242 12.96 12.86 12.84 62 242 1 64 242 12.92 12.95 12.86 64 242 1 65 484 12.67 12.54 12.59 65 484 1	12.94	484					-	
62 242 12.96 12.86 12.84 62 242 1 64 242 12.92 12.95 12.86 64 242 1 65 484 12.67 12.54 12.59 65 484 1 66 484 12.71 12.58 12.67 66 484 1	12.73	996	67	12.91	12.89	12.93	996	67

 Table 8-61

 IEEE 802.11ax (5GHz. 80MHz BW. RU. MIMO) Maximum Average RF Power¹

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IX. WIFI Conducted Powers for Operations with Simultaneous 2.4GHz and 5GHz

Table 8-62 IEEE 802.11b/g/n/ax (2.4GHz, Ant1) Reduced Average RF Power¹

	2.4GHz Conducted Power [dBm]								
Eroa M	Freq [MHz] Channel	Channel	IEEE Transmission Mode						
I led [w		802.11b	802.11g	802.11n	802.11ax (SU)				
2412	2	1	13.94	13.77	13.67	13.19			
2437	7	6	13.88	13.66	13.54	13.82			
2462	2	11	13.92	13.82	13.97	13.96			

Table 8-63 IEEE 802.11b/g/n/ax (2.4GHz, Ant2) Reduced Average RF Power¹

2.4GHz Conducted Power [dBm]								
Freq [MHz]	Channel		IEEE Transm	IEEE Transmission Mode				
Freq [winz]	Channer	802.11b	802.11g	802.11n	802.11ax (SU)			
2412	1	13.92	13.98	13.86	13.19			
2437	6	13.51	13.55	13.53	13.78			
2462	11	13.86	13.61	13.90	13.96			

Table 8-64 IEEE 802.11a/n/ac/ax (5GHz, 20MHz BW, Ant1) Reduced Average RF Power1 CUE (20MUE) Conducted De

	50	GHz (20MHz) Co	nducted Power	[dBm]	
Freq [MHz]	Channel		IEEE Transm	ission Mode	
Freq [MHZ]	Channer	802.11a	802.11n	802.11ac	802.11ax(SU)
5180	36	13.42	13.96	13.95	13.71
5200	40	13.93	13.93	13.93	13.90
5220	44	13.86	13.81	13.97	13.72
5240	48	13.95	13.95	13.93	13.68
5260	52	13.96	13.83	13.95	13.67
5280	56	13.95	13.93	13.91	13.78
5300	60	13.95	13.87	13.92	13.73
5320	64	13.82	13.64	13.73	13.67
5500	100	13.71	13.89	13.60	13.60
5600	120	13.67	13.67	13.70	13.40
5620	124	13.93	13.96	13.60	13.91
5720	144	13.92	13.90	13.95	13.93
5745	149	13.74	13.62	13.69	13.91
5785	157	13.80	13.76	13.84	13.64
5825	165	13.64	13.65	13.64	13.47

¹ Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios.

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	5GHz (20MHz) Conducted Power [dBm]								
Freq [MHz]	Channel		IEEE Transm	ission Mode					
	Gliatiliet	802.11a	802.11n	802.11ac	802.11ax(SU)				
5180	36	13.76	13.85	13.78	13.62				
5200	40	13.91	13.93	13.90	13.56				
5220	44	13.86	13.80	13.81	13.45				
5240	48	13.89	13.94	13.94	13.56				
5260	52	13.60	13.92	13.66	13.83				
5280	56	13.76	13.68	13.78	13.45				
5300	60	13.83	13.80	13.76	13.48				
5320	64	13.73	13.67	13.67	13.54				
5500	100	13.97	13.73	13.90	13.86				
5600	120	13.86	13.70	13.83	13.56				
5620	124	13.76	13.80	13.78	13.47				
5720	144	13.88	13.91	13.87	13.62				
5745	149	13.68	13.72	13.73	13.92				
5785	157	13.78	13.74	13.75	13.64				
5825	165	13.57	13.92	13.58	13.90				

Table 8-65 IEEE 802.11a/n/ac/ax (5GHz, 20MHz BW, Ant2) Reduced Average RF Power¹

Table 8-66

IEEE 802.11n/ac (5GHz, 40MHz BW, Ant1) Reduced Average RF Power¹

	5GHz (40MHz) Conducted Power [dBm]							
Freq [MHz]	Channel	IEEE	Transmission M	lode				
Freq [winz]	Channer	802.11n	802.11ac	802.11ax(SU)				
5190	38	13.63	13.63	13.97				
5230	46	13.68	13.65	13.60				
5270	54	13.76	13.64	13.75				
5310	62	13.87	13.84	13.71				
5510	102	13.59	13.57	13.83				
5590	118	13.86	13.87	13.76				
5630	126	13.80	13.97	13.77				
5710	142	13.90	13.89	13.75				
5755	151	13.68	13.69	13.87				
5795	159	13.45	13.56	13.90				

Table 8-67

IEEE 802.11n/ac (5GHz, 40MHz BW, Ant2) Reduced Average RF Power¹

	5GHz (40MHz) Conducted Power [dBm]							
Freg [MHz]	Channel	IEEE	Transmission M	lode				
Freq [winz]	Channer	802.11n	802.11ac	802.11ax(SU)				
5190	38	13.65	13.60	13.95				
5230	46	13.74	13.76	13.64				
5270	54	13.92	13.55	13.76				
5310	62	13.94	13.95	13.61				
5510	102	13.93	13.88	13.93				
5590	118	13.95	13.92	13.95				
5630	126	13.67	13.61	13.95				
5710	142	13.81	13.72	13.51				
5755	151	13.66	13.71	13.86				
5795	159	13.53	13.52	13.75				

¹ Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios.

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50	5GHz (80MHz) Conducted Power [dBm]								
Freq [MHz]	Channel	IEEE Transm	ission Mode						
		802.11ac 802.11ax(SI							
5210	42	12.69	12.46						
5290	58	12.87 12.72							
5530	106	12.86 12.75							
5610	122	12.78 12.55							
5690	138	12.82 12.72							
5775	155	12.58 12.83							

 Table 8-68

 IEEE 802.11ac (5GHz, 80MHz BW, Ant1) Reduced Average RF Power¹

Table 8-69 IEEE 802.11ac (5GHz, 80MHz BW, Ant2) Reduced Average RF Power¹ 5GHz (80MHz) Conducted Power [dBm]

Freq [MHz]	Channel	IEEE Transmission Mode			
		802.11ac	802.11ax(SU)		
5210	42	12.88	12.55		
5290	58	12.72	12.57		
5530	106	12.80	12.56		
5610	122	12.86	12.47		
5690	138	12.36	12.68		
5775	155	12.85	12.79		

¹ Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios.

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JUSTIFICATION OF HELD TO EAR MODES TESTED 9.

I. Analysis of RF Air Interface Technologies

An analysis was performed, following the guidance of §4.3 and §4.4 of the ANSI standard, of the RF air interface technologies being evaluated. The factors that will affect the RF interference potential were evaluated, and the worst-case operating modes were identified and used in the evaluation. A WD's interference potential is a function both of the WD's average near-field field strength and of the signal's audio-frequency amplitude modulation characteristics. Per §4.4, RF air interface technologies that have low power have been found to produce sufficiently low RF interference potential, so it is possible to exempt them from the product testing specified in Clause 5 of the ANSI standard. An RF air interface technology of a device is exempt from testing when its average antenna input power plus its MIF is ≤17dBm for all of its operating modes. RF air interface technologies exempted from testing in this manner are automatically assigned an M4 rating to be used in determining the overall rating for the WD.

The worst-case MIF plus the worst-case average antenna input power for all modes are investigated below to determine the testing requirements for this device.

Table 9-1

- ---

Max Power + MIF calculation	Max Power + MIF calculations for Low Power Exemptions							
Air Interface	Maximum Average Power (dBm)	Worst Case MIF (dB)	Total (Power + MIF, dB)	C63.19 Testing Required				
GSM850	23.58*	3.53	27.11	Yes				
GSM1900	21.79*	3.51	25.30	Yes				
EDGE850	17.83*	3.68	21.51	Yes***				
EDGE1900	17.26*	3.56	20.82	Yes***				
UMTS - RMC	24.27	-22.67	1.60	No				
UMTS - AMR	24.29	-23.05	1.24	No				
HSPA	23.66	-22.02	1.64	No				
LTE - FDD	24.68	-8.71	15.97	No				
LTE FDD - Uplink Carrier Aggregation	23.76	-9.73	14.03	No				
LTE Band 41 - TDD (PC3)	13.93*	3.79	17.72	Yes				
LTE Band 38 - TDD	14.60*	3.88	18.48	Yes				
2.4GHz WIFI	16.94	-4.65	12.29	No				
5GHz WIFI	16.96	-4.63	12.33	No				
Simultaneous 2.4GHz and 5GHz WIFI Operations	19.99**	-4.56	15.43	No				

II. Individual Mode Evaluations

* Note: ANSI C63.19-2011 Sec. 4.4 Footnote 20 indicates the use of a long averaging time for measuring the antenna input power when using this method of exclusion. Therefore, the frame averaged power was calculated for these modes in this investigation.

** Note: This value is calculated as the linear sum of the worst-case power for each band and antenna combination while in simultaneous 2.4GHz and 5GHz operation. This calculation is conservative and for use in this investigation only.

*** Note: EDGE data modes were considered but not tested as GSM voice modes were found to be the worst-case modes for the GSM air interface.

III. Low-Power Exemption Conclusions

Per ANSI C63.19-2011, RF Emissions testing for this device is required only for GSM voice modes as well as LTE TDD (Power Class 3) data modes. All other air interfaces are exempt.

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10. LTE TDD UPLINK-DOWNLINK CONFIGURATION

I. Uplink-Downlink Configuration Additional Testing

Additional testing was performed on each supported power class for LTE TDD to determine the worst-case Uplink-Downlink configuration for RFE testing.

Per 3GPP TS 36.211, the total frame length for each TDD radio frame of length $T_f = 307200 \cdot T_s = 10$ ms, where T_s is a number of time units equal to $1/(15000 \times 2048)$ seconds. Additionally, each radio frame consists of 10 subframes, each of length $30720 \cdot T_s = 1$ ms, and subframes can be designated as uplink (U), downlink (D), or special subframe (S), depending on the Uplink-Downlink configuration as indicated in Table 4.2-2 of 3GPP TS 36.211. In the transmission duty factor calculation, the special subframe configuration with the shortest UpPTS duration within the special subframe is used and will be applied for measurement. From 3GPP TS 36.211 Table 4.2-1, the shortest UpPTS is 2192 \cdot Ts which occurs in the normal cyclic prefix and special subframe configuration 4.

See table below outlining the calculated transmission duty cycles for each Uplink-Downlink configuration:

Uplink-downlink	Downlink-to-Uplink					Calculated Transmission						
configuration	Switch-point periodicity	0	1	2	3	4	5	6	7	8	9	Duty Cycle (%)
0	5 ms	D	S	U	υ	U	D	S	U	υ	U	61.4%
1	5 ms	D	S	U	υ	D	D	S	U	υ	D	41.4%
2	5 ms	D	S	U	D	D	D	S	U	D	D	21.4%
3	10 ms	D	S	U	υ	U	D	D	D	D	D	30.7%
4	10 ms	D	S	U	U	D	D	D	D	D	D	20.7%
5	10 ms	D	S	U	D	D	D	D	D	D	D	10.7%
6	5 ms	D	S	U	U	U	D	S	U	U	D	51.4%

Table 10-1 Uplink-Downlink Configurations for Type 2 Frame Structures

II. Power Class 3 Uplink-Downlink Configuration Additional Testing

LTE TDD was evaluated with the following radio configuration: channel 40620, 20MHz BW, 16QAM, 1RB, 0RB Offset. For Power Class 3, all configurations (0-6) are supported. The configuration which resulted in the worst-case emission was used for full testing. See Table 10-2 below for results. The configuration determined in the results below was used to measure the MIF values in Table 7-5 and 7-6.

	LTE TDD Power Class 3 UL-DL Configuration Results														
Mode / Band	Bandwidth	Channel	UL-DL Config.		RB Size	RB Offset	Scan Center	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emissi	ons														
	20	40620	0	16QAM	1	0	Acoustic	17.06	24.64	-3.24	21.40	35.00	-13.60	M4	none
	20	40620	1	16QAM	1	0	Acoustic	14.79	23.40	-1.56	21.84	35.00	-13.16	M4	none
	20	40620	2	16QAM	1	0	Acoustic	13.21	22.42	1.46	23.88	35.00	-11.12	M4	none
LTE TDD / Band 41	20	40620	3	16QAM	1	0	Acoustic	14.66	23.32	-1.48	21.84	35.00	-13.16	M4	none
Build 41	20	40620	4	16QAM	1	0	Acoustic	13.96	22.90	0.66	23.56	35.00	-11.44	M4	none
	20	40620	5	16QAM	1	0	Acoustic	13.04	22.31	3.57	25.88	35.00	-9.12	M4	none
	20	40620	6	16QAM	1	0	Acoustic	15.73	23.93	-2.53	21.40	35.00	-13.60	M4	none

 Table 10-2

 LTE TDD Power Class 3 UL-DL Configuration Results

III. Conclusion

Per the results above, UL-DL Configuration 5 was used for LTE TDD Power Class 3 testing.

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11. OVERALL MEASUREMENT SUMMARY

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I. E-FIELD EMISSIONS:

				HAC D	ata Sun	nmary fo	or GSM	E-field				
Mode	Channel	Sample S/N	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emissio	ons											
	128	53436	Acoustic	32.55	31.78	30.04	3.53	33.57	45.00	-11.43	M4	none
GSM850	190	53436	Acoustic	32.36	29.84	29.50	3.53	33.03	45.00	-11.97	M4	none
	251	53436	Acoustic	32.61	25.25	28.05	3.53	31.58	45.00	-13.42	M4	none
	512	53436	Acoustic	30.82	16.14	24.16	3.51	27.67	35.00	-7.33	M4	none
GSM1900	661	53436	Acoustic	30.70	12.33	21.82	3.51	25.33	35.00	-9.67	M4	2,3,4
GSW1900	810	53436	Acoustic	30.64	16.75	24.48	3.50	27.98	35.00	-7.02	M4	none
	810	53436	T-Coil	30.64	16.75	24.48	3.50	27.98	35.00	-7.02	M4	none

Table 11-1 HAC Data Summary for GSM E-field

 Table 11-2

 HAC Data Summary for LTE TDD B41 (PC3) E-field

Mode / Band	Bandwidth	Channel		UL-DL Config.	Mod.	RB Size	RB Offset	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emissio	ons																
	15MHz	39750	1405M	5	QPSK	1	74	Acoustic	23.51	12.71	22.08	3.59	25.67	35.00	-9.33	M4	none
	15MHz	40185	1405M	5	QPSK	1	74	Acoustic	23.39	12.07	21.63	3.56	25.19	35.00	-9.81	M4	none
LTE TDD / Band 41 PC3	15MHz	40620	1405M	5	QPSK	1	74	Acoustic	23.17	11.36	21.11	3.79	24.90	35.00	-10.10	M4	none
	15MHz	41055	1405M	5	QPSK	1	74	Acoustic	23.16	11.47	21.19	3.77	24.96	35.00	-10.04	M4	none
	15MHz	41490	1405M	5	QPSK	1	74	Acoustic	23.49	12.17	21.71	3.58	25.29	35.00	-9.71	M4	none

Table 11-3HAC Data Summary for LTE TDD B38 E-field

Mode / Band	Bandwidth	Channel		UL-DL Config.	Mod.	RB Size	RB Offset	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emissie	ons																
	15MHz	37825	55399	5	64QAM	1	0	Acoustic	22.00	12.83	22.16	3.73	25.89	35.00	-9.11	M4	none
LTE TDD / Band 38	15MHz	38000	55399	5	64QAM	1	0	Acoustic	21.81	12.89	22.21	3.88	26.09	35.00	-8.91	M4	none
	15MHz	38175	55399	5	64QAM	1	0	Acoustic	21.85	12.80	22.14	3.66	25.80	35.00	-9.20	M4	none

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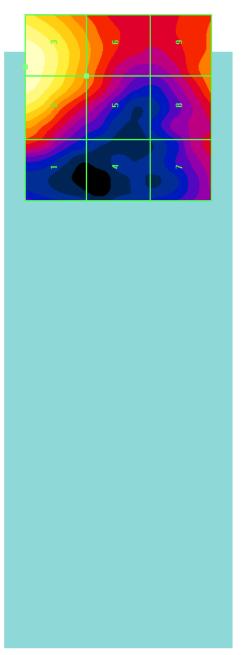


Figure 11-1 Sample E-field Scan Overlay (See Test Setup Photographs for actual WD overlay)

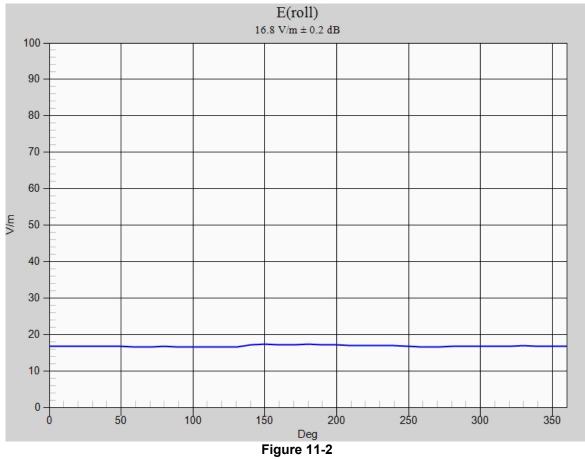
FCC ID: A3LSMF900F		HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename: 1M1907090118-12.A3L	Test Dates: 06/24/2019 - 06/28/2019	DUT Type: Portable Handset		Page 65 of 108
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FCC ID:	A3LSMF900F
S/N:	53436, 55399

II. Worst-case Configuration Evaluation

	Peak Reading 360° Probe Rotation at Azimuth axis										
Mode	Channel	Sample S/N	Scan Center	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
Probe Rotation	at Worst-Case	9									
GSM1900	810	53436	Acoustic	17.35	24.79	3.50	28.29	35.00	-6.71	M4	none

Table 11-4



Worst-Case Probe Rotation about Azimuth axis

* Note: Locations of probe rotation (with and without exclusions) are shown in Figure 11-1 denoted by the green square markers.

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12. EQUIPMENT LIST

Equipment List Manufacturer Model Description Cal Date Cal Interval Cal Due Serial Number MY47420603 Agilent N5182A MXG Vector Signal Generator 11/28/2018 Annual 11/28/2019 E4438C ESG Vector Signal Generator 3/11/2019 Biennial 3/11/2021 MY45090700 Agilent Amplifier Research 15S1G6 Amplifier N/A CBT* N/A 433978 ML2496A Power Meter 10/21/2018 10/21/2019 1138001 Anritsu Annual 11/20/2019 1339007 Anritsu MA2411B **Pulse Power Sensor** 11/20/2018 Annual Anritsu MA2411B Pulse Power Sensor 11/20/2018 Annual 11/20/2019 1339008 MA24106A 1/31/2019 1/31/2020 1520503 Anritsu **USB** Power Sensor Annual MA24106A **USB** Power Sensor 1/31/2019 1/31/2020 1520501 Anritsu Annual 2/28/2020 150761911 **Control Company** 4040 Temperature / Humidity Monitor 2/28/2018 Biennial CBT* Mini-Circuits NLP-1200+ Low Pass Filter DC to 1000 MHz N/A N/A N/A Mini-Circuits NLP-2950+ Low Pass Filter DC to 2700 MHz N/A CBT* N/A N/A Mini-Circuits **BW-N20W5** Power Attenuator N/A CBT* N/A 1226 PE2237-20 N/A CBT* N/A Pasternack N/A **Bidirectional Coupler** 8/3/2018 8/3/2019 140144 Rohde & Schwarz CMW500 Radio Communication tester Annual Rohde & Schwarz CMW500 Wideband Radio Communication Tester 1/30/2019 Annual 1/30/2020 162125 5/23/2018 5/23/2020 Seekonk NC-100 Torque Wrench (8" lb) Biennial N/A SPEAG Audio Interference Analzyer N/A CBT* N/A 1010 AIA EF3DV3 SPEAG 1/16/2019 1/16/2020 4035 Freespace E-field Probe Annual SPEAG DAE4 **Dasy Data Acquisition Electronics** 3/13/2019 Annual 3/13/2020 1415 SPEAG CD835V3 Freespace 835 MHz Dipole 2/19/2019 Biennial 2/19/2021 1003 SPEAG CD1880V3 Freespace 1880 MHz Dipole 2/19/2019 Biennial 2/19/2021 1137 SPEAG CD2600V3 Freespace 2600MHz Dipole 2/19/2019 2/19/2021 1012 Biennial

Table 12-1

Calibration traceable to the National Institute of Standards and Technology (NIST).

*Note: CBT (Calibrated Before Testing). Prior to testing, the measurement paths containing a cable, attenuator, coupler or filter were connected to a calibrated source (i.e. a signal generator) to determine the losses of the measurement path. The power meter offset was then adjusted to compensate for the measurement system losses. This level offset is stored within the power meter before measurements are made. This calibration verification procedure applies to the system verification and output power measurements. The calibrated reading is then taken directly from the power meter after compensation of the losses for all final power measurements.

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13. MEASUREMENT UNCERTAINTY

Table 13-1

Uncertainty Estimation Table

	Wireless C	Communication			asurement		
		Uncer	tainty Estima	ation			
Uncertainty Component	Data (dB)	Data Type	Prob. Dist.	Divisor	Ci (E)	Unc. (dB)	Notes/Comments
Measurement System	-	-				-	-
RF System Reflections	0.50	Tolerance	Ν	1.00	1	0.50	* Refl. < -20 dB
Field Probe Calibration	0.21	Tolerance	Ν	1.00	1	0.21	
Field Probe Isotropy	0.01	Tolerance	Ν	1.00	1	0.01	
Field Probe Frequency Response	0.135	Tolerance	Ν	1.00	1	0.14	
Field Probe Linearity	0.013	Tolerance	Ν	1.00	1	0.01	
Modulation Interference Factor	0.20	Tolerance	R	1.73	1	0.12	Applicable for M-rating testing
Boundary Effects	0.105	Accuracy	R	1.73	1	0.06	*
Probe Positioning Accuracy	0.20	Accuracy	R	1.73	1	0.12	*
Probe Positioner	0.050	Accuracy	R	1.73	1	0.03	*
Extrapolation/Interpolation	0.045	Tolerance	R	1.73	1	0.03	*
Resolution to 2mm error	0.21	Tolerance	Ν	1.00	1	0.21	
System Detection Limit	0.05	Tolerance	R	1.73	1	0.03	*
Readout Electronics	0.015	Tolerance	Ν	1.00	1	0.02	*
Integration Time	0.11	Tolerance	R	1.73	1	0.06	*
Response Time	0.033	Tolerance	R	1.73	1	0.02	*
Phantom Thickness	0.10	Tolerance	R	1.73	1	0.06	*
System Repeatability (Field x 2=power)	0.17	Tolerance	Ν	1.00	1	0.17	*
Test Sample Related		-					-
Device Positioning Vertical	0.2	Tolerance	R	1.73	1	0.12	*
Device Positioning Lateral	0.045	Tolerance	R	1.73	1	0.03	*
Device Holder and Phantom	0.1	Tolerance	R	1.73	1	0.06	*
Power Drift	0.21	Tolerance	R	1.73	1	0.12	
Combined Standard Uncertainty (k=1)		-				0.66	16.3%
Expanded Uncertainty [95% confidence]				1.31	32.6%		
Expanded Uncertainty [95% confidence]	on Field					0.66	16.3%

Notes:

Test equipments are calibrated according to techniques outlined in NIS81, NIS3003 and NIST Tech Note 1297. All
equipments have traceability according to NIST. Measurement Uncertainties are defined in further detail in NIS 81
and NIST Tech Note 1297 and UKAS M3003.

2. * Uncertainty specifications from Schmidt & Partner Engineering AG (not site specific)

Measurement uncertainty reflects the quality and accuracy of a measured result as compared to the true value. Such statements are generally required when stating results of measurements so that it is clear to the intended audience that the results may differ when reproduced by different facilities. Measurement results vary due to the measurement uncertainty of the instrumentation, measurement technique, and test engineer. Most uncertainties are calculated using the tolerances of the instrumentation used in the measurement, the measurement setup variability, and the technique used in performing the test. While not generally included, the variability of the equipment under test also figures into the overall measurements (so-called Type A uncertainty). This may mean that the Hearing Aid immunity tests may have to be repeated by taking down the test setup and resetting it up so that there are a statistically significant number of repeat measurements to identify the measurement uncertainty. By combining the repeat measurements to identify the measurement uncertainty. By combining the repeat measurements with that of the instrumentation chain using the technique contained in NIS 81 and NIS 3003, the overall measurement uncertainty was estimated.

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14. TEST DATA

See following Attached Pages for Test Data.

FCC ID: A3LSMF900F		HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
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Date: 6/24/2019



PCTEST Hearing-Aid Compatibility Facility

DUT: CD835V3 - SN1003

Type: CD835V3 Serial: 1003

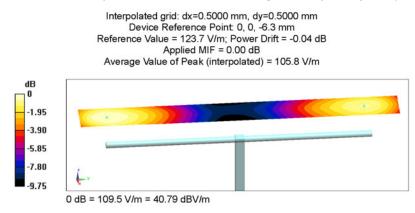
Communication System: CW; Frequency: 835 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: 0mm (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

835 MHz / 100mW HAC Dipole Validation at 15mm/Hearing Aid Compatibility Test (41x361x1):



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PCTEST Hearing-Aid Compatibility Facility

DUT: CD1880V3 - SN1137

Type: CD1880V3 Serial: 1137

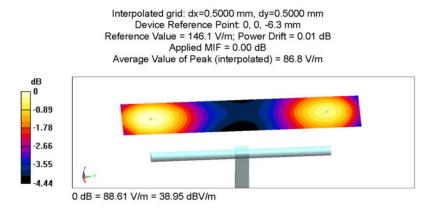
Communication System: CW; Frequency: 1880 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: 0mm (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

1880 MHz / 100mW HAC Dipole Validation at 15mm/Hearing Aid Compatibility Test (41x181x1):



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PCTEST Hearing-Aid Compatibility Facility

DUT: CD2600V3 - SN1012

Type: CD2600V3 Serial: 1012

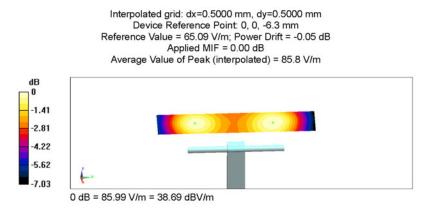
Communication System: CW; Frequency: 2600 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: 0mm (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

2600 MHz / 100mW HAC Dipole Validation at 15mm/Hearing Aid Compatibility Test (41x181x1):



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DUT: A3LSMF900F

Type: Portable Handset Serial: 53436 Backlight off Duty Cycle: 1:8.3

Communication System: GSM; Frequency: 824.2 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/7/2018
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

GSM850 Low Channel / Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 34.52 V/m; Power Drift = 0.17 dB Applied MIF = 3.53 dB RF audio interference level = 33.57 dBV/m **Emission category: M4**

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
32.15 dBV/m	33.48 dBV/m	33.57 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
31.63 dBV/m	33.14 dBV/m	33.17 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
31.27 dBV/m	32.72 dBV/m	32.77 dBV/m



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DUT: A3LSMF900F

Type: Portable Handset Serial: 53436 Backlight off Duty Cycle: 1:8.3

Communication System: GSM; Frequency: 1909.8 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/7/2018
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

GSM1900 High Channel / Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 7.279 V/m; Power Drift = -0.10 dB Applied MIF = 3.50 dB RF audio interference level = 27.98 dBV/m **Emission category: M4**

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
23.24 dBV/m	27.88 dBV/m	27.98 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
19 dBV/m	23.94 dBV/m	24.37 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
22.19 dBV/m	23.93 dBV/m	23.93 dBV/m



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DUT: A3LSMF900F

Type: Portable Handset Serial: 53436 Backlight off Duty Cycle: 1:9.35

Communication System: LTE TDD41; Frequency: 2506 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/7/2018
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

LTE TDD Band 41 PC3, Mid Channel, 15MHz BW, ULDL 5, QPSK, 1RB, 74RB Offset Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 14.42 V/m; Power Drift = 0.03 dB Applied MIF = 3.59 dB RF audio interference level = 25.67 dBV/m **Emission category: M4**

MIF scaled E-field

Grid 1 M	4 G	rid 2	M4	Grid 3	M4
25.29 df	3V/m 2	5.41	dBV/m	25.36	dBV/m
Grid 4 M	4 G	rid 5	M4	Grid 6	M4
25.43 dE	3V/m 2	5.25	dBV/m	24.82	dBV/m
Grid 7 M	4 G	rid 8	M4	Grid 9	M4
25.67 dE	3V/m 2	5.06	dBV/m	24.99	dBV/m



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DUT: A3LSMF900F

Type: Portable Handset Serial: 55399 Backlight off Duty Cycle: 1:9.35

Communication System: LTE TDD38; Frequency: 2595 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

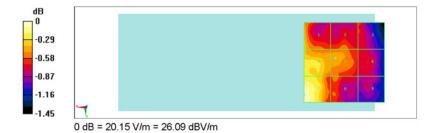
- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

LTE TDD Band 38 Mid Channel, 15MHz BW, UL-DL 5, 64QAM, 1RB, 0RB Offset Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 14.34 V/m; Power Drift = 0.11 dB Applied MIF = 3.88 dB RF audio interference level = 26.09 dBV/m **Emission category: M4**

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
25.77 dBV/m	25.57 dBV/m	25.45 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
25.88 dBV/m	25.68 dBV/m	25.41 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
26.09 dBV/m	25.56 dBV/m	25.34 dBV/m



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15. CALIBRATION CERTIFICATES

The following pages include the probe calibration used to evaluate HAC for the DUT.

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Calibration Laboratory of

PC Test

Client

Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland



Schweizerischer Kalibrierdienst Service suisse d'étalonnage Servizio svizzero di taratura Swiss Calibration Service

Issued: January 17, 2019

Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS) The Swiss Accreditation Service is one of the signatories to the EA Multilateral Agreement for the recognition of calibration certificates

Certificate N	10: EF3-40	035 Jan19
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CALIBRATION	CERTIFICATE		
Object	EF3DV3- SN:403	5	
Calibration procedure(s)	QA CAL-02.v9, Q Calibration procec evaluations in air	A CAL-25.v7 lure for E-field probes optimized f	for close near field //JUA ปาเป็นอาจ
Calibration date:	January 16, 2019		2/11/2019
The measurements and the unc	certainties with confidence pro ucted in the closed laboratory	nal standards, which realize the physical units bability are given on the following pages and facility: environment temperature $(22 \pm 3)^\circ$ C a	are part of the certificate.
Primary Standards	ID	Cal Date (Certificate No.)	Scheduled Calibration
Power meter NRP	SN: 104778	04-Apr-18 (No. 217-02672/02673)	Apr-19
Power sensor NRP-Z91	SN: 103244	04-Apr-18 (No. 217-02672)	Apr-19
Power sensor NRP-Z91	SN: 103245	04-Apr-18 (No. 217-02673)	Apr-19
Reference 20 dB Attenuator	SN: S5277 (20x)	04-Apr-18 (No. 217-02682)	Apr-19
DAE4	SN: 789	14-Jan-19 (No. DAE4-789_Jan19)	Jan-20
Reference Probe ER3DV6	SN: 2328	09-Oct-18 (No. ER3-2328_Oct18)	Oct-19
Secondary Standards	ID	Check Date (in house)	
Power meter E4419B	SN: GB41293874	06-Apr-16 (in house check Jun-18)	Scheduled Check
Power sensor E4412A	SN: MY41498087	06-Apr-16 (in house check Jun-18)	In house check: Jun-20 In house check: Jun-20
Power sensor E4412A	SN: 000110210	06-Apr-16 (in house check Jun-18)	In house check: Jun-20
RF generator HP 8648C	SN: US3642U01700	04-Aug-99 (in house check Jun-18)	In house check: Jun-20
Network Analyzer E8358A	SN: US41080477	31-Mar-14 (in house check Oct-18)	In house check: Oct-19
alibrated by:	Name Manu Seitz	Function Laboratory Technician	Signature
approved by:	Katja Pokovic	- Technical Manager	Carton Carton
Approved by:	Katja Pokovic	Technical Manager	LAG-

Certificate No: EF3-4035_Jan19

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Accreditation No.: SCS 0108

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Glossary:

NORMx,y,z DCP CF A, B, C, D En Ep Polarization o	sensitivity in free space diode compression point crest factor (1/duty_cycle) of the RF signal modulation dependent linearization parameters incident E-field orientation normal to probe axis incident E-field orientation parallel to probe axis
	φ rotation around probe axis
Polarization 9	ϑ rotation around an axis that is in the plane normal to probe axis (at measurement center), i.e., $\vartheta = 0$ is normal to probe axis
Connector Angle	information used in DASY system to align probe sensor X to the robot coordinate system

Calibration is Performed According to the Following Standards:

- IEEE Std 1309-2005, "IEEE Standard for calibration of electromagnetic field sensors and probes, excluding antennas, from 9 kHz to 40 GHz", December 2005
- b) CTIA Test Plan for Hearing Aid Compatibility, Rev 3.1.1, May 2017

Methods Applied and Interpretation of Parameters:

- NORMx,y,z: Assessed for E-field polarization 9 = 0 for XY sensors and 9 = 90 for Z sensor (f ≤ 900 MHz in TEM-cell; f > 1800 MHz: R22 waveguide).
- NORM(f)x,y,z = NORMx,y,z * frequency_response (see Frequency Response Chart).
- DCPx,y,z: DCP are numerical linearization parameters assessed based on the data of power sweep with CW signal (no uncertainty required). DCP does not depend on frequency nor media.
- PAR: PAR is the Peak to Average Ratio that is not calibrated but determined based on the signal characteristics
- Ax,y,z; Bx,y,z; Cx,y,z; Dx,y,z; VRx,y,z: A, B, C, D are numerical linearization parameters assessed based on the data of power sweep for specific modulation signal. The parameters do not depend on frequency nor media. VR is the maximum calibration range expressed in RMS voltage across the diode.
- Spherical isotropy (3D deviation from isotropy): in a locally homogeneous field realized using an open waveguide setup.
- Sensor Offset: The sensor offset corresponds to the offset of virtual measurement center from the probe tip (on probe axis). No tolerance required.
- Connector Angle: The angle is assessed using the information gained by determining the NORMx (no
 uncertainty required).

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DASY/EASY - Parameters of Probe: EF3DV3 - SN:4035

Basic Calibration Parameters

	Sensor X	Sensor Y	Sensor Z	Unc (k=2)
Norm $(\mu V/(V/m)^2)$	0.90	0.74	1.20	± 10.1 %
DCP (mV) ^B	96.8	98.5	95.3	

Calibration results for Frequency Response (30 MHz - 6 GHz)

Frequency MHz	Target E-Field V/m	Measured E-field (En) V/m	Deviation E-normal in %	Measured E-field (Ep) V/m	Deviation E-normal in %	Unc (k=2) %
30	77.3	76.8	-0.6%	77.3	0.1%	± 5.1 %
100	77.3	78.2	1.2%	77.8	0.7%	± 5.1 %
450	77.1	78.2	1.5%	77.8	0.9%	± 5.1 %
600	77.1	77.8	0.9%	77.5	0.5%	± 5.1 %
750	77.3	77.7	0.5%	77.2	-0.1%	± 5.1 %
1800	140.3	136.9	-2.4%	137.2	-2.2%	± 5.1 %
2000	133.0	129.4	-2.8%	129.4	-2.7%	± 5.1 %
2200	124.8	121.5	-2.7%	122.7	-1.7%	± 5.1 %
2500	123.7	120.7	-2.4%	121.9	-1.5%	± 5.1 %
3000	78.8	74.8	-5.0%	76.1	-3.5%	± 5.1 %
3500	256.3	248.1	-3.2%	246.0	-4.0%	± 5,1 %
3700	249.7	239.2	-4.2%	239.0	-4.3%	± 5.1 %
5200	50.7	50.7	-0.1%	51.2	0.9%	± 5.1 %
5500	49.6	48.9	-1.5%	48.7	-1.9%	± 5.1 %
5800	48.9	49.1	0.4%	49.3	0.8%	± 5.1 %

Calibration Results for Modulation Response

UID	Communication System Name		A dB	B dBõV	С	D dB	VR mV	Max dev.	Unc [⊭] (k=2)
0	CW	X	0.0	0.0	1.0	0.00	141.5	+ 3.3 %	±4.7 %
		Y	0.0	0.0	1.0		125.6		
		Y	0.0	0.0	1.0		125.1		

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%.

^B Numerical linearization parameter: uncertainty not required.
^E Uncertainty is determined using the max. deviation from linear response applying rectangular distribution and is expressed for the square of the

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EF3DV3 - SN:4035

DASY/EASY - Parameters of Probe: EF3DV3 - SN:4035

Sensor Frequency Model Parameters

	Sensor X	Sensor Y	Sensor Z
Frequency Corr. (LF)	0.28	0.21	5.68
Frequency Corr. (HF)	2.82	2.82	2.82

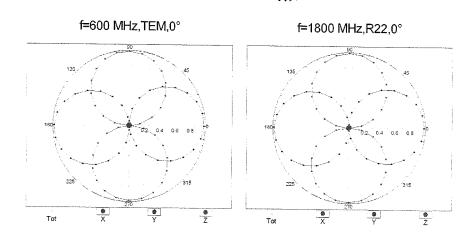
Other Probe Parameters

Sensor Arrangement	Rectangular
Connector Angle (°)	57.9
Mechanical Surface Detection Mode	enabled
Optical Surface Detection Mode	disabled
Probe Overall Length	335 mm
Probe Body Diameter	12 mm
Tip Length	25 mm
Tip Diameter	4 mm
Probe Tip to Sensor X Calibration Point	1.5 mm
Probe Tip to Sensor Y Calibration Point	1.5 mm
Probe Tip to Sensor Z Calibration Point	1.5 mm

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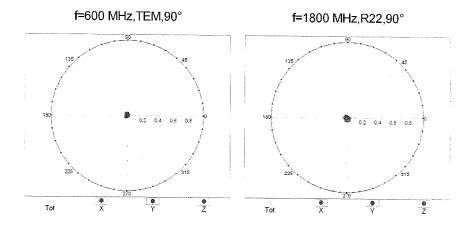
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Receiving Pattern (ϕ), $\vartheta = 0^{\circ}$

Receiving Pattern (ϕ), ϑ = 90°

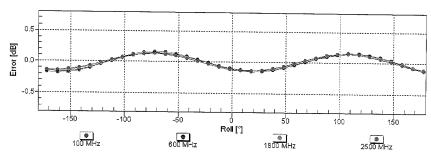


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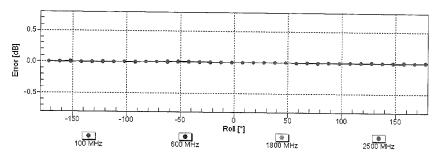
January 16, 2019



Receiving Pattern (ϕ), $\vartheta = 0^{\circ}$



Receiving Pattern (ϕ), $\vartheta = 90^{\circ}$



Uncertainty of Axial Isotropy Assessment: ± 0.5% (k=2)

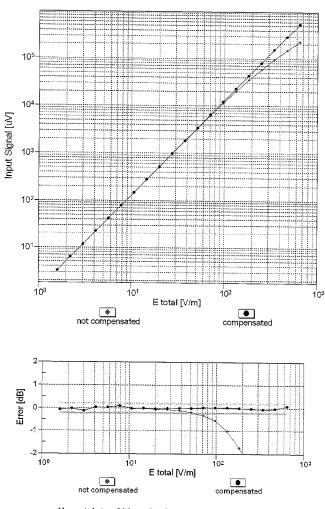
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EF3DV3 - SN:4035

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Dynamic Range f(E-field) (TEM cell, f = 900 MHz)

Uncertainty of Linearity Assessment: ± 0.6% (k=2)

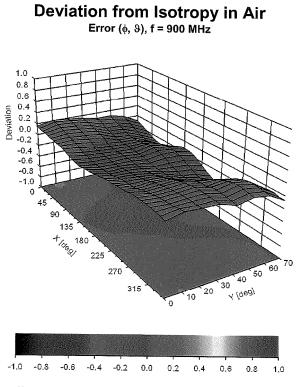
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EF3DV3 - SN:4035

January 16, 2019



Uncertainty of Spherical Isotropy Assessment: ± 2.6% (k=2)

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Client PC Test

Certificate No: CD835V3-1003_Feb19

Object	CD835V3 - SN:	1003	
Calibration procedure(s)	QA CAL-20.v7 Calibration Proc	edure for Validation Sources in a	ir /04 3/19/201
Calibration date:	February 19, 20	19	
The measurements and the unc	ertainties with confidence pucted in the closed laborate	lional standards, which realize the physical un probability are given on the following pages ar pry facility: environment temperature (22 \pm 3)°	nd are part of the certificate.
Primary Standards	ID #	Cal Data (Cartificata Na.)	
Power meter NRP	SN: 104778	Cal Date (Certificate No.) 04-Apr-18 (No. 217-02672/02673)	Scheduled Calibration
ower sensor NRP-Z91	SN: 103244	04-Apr-18 (No. 217-02672/02673) 04-Apr-18 (No. 217-02672)	Apr-19
ower sensor NRP-Z91	SN: 103245	04-Apr-18 (No. 217-02072)	Apr-19
eference 20 dB Attenuator	SN: 5058 (20k)	04-Apr-18 (No. 217-02682)	Apr-19
ype-N mismatch combination	SN: 5047.2 / 06327	04-Apr-18 (No. 217-02682) 04-Apr-18 (No. 217-02683)	Apr-19
robe EF3DV3	SN: 4013	03-Jan-19 (No. EF3-4013_Jan19)	Apr-19
AE4	SN: 781	09-Jan-19 (No. DAE4-781_Jan19)	Jan-20 Jan-20
econdary Standards	ID#	Check Date (in house)	Scheduled Check
ower meter Agilent 4419B	SN: GB42420191	09-Oct-09 (in house check Oct-17)	
ower sensor HP E4412A	SN: US38485102	05-Jan-10 (in house check Oct-17)	In house check: Oct-20
ower sensor HP 8482A	SN: US37295597	09-Oct-09 (in house check Oct-17)	In house check: Oct-20
F generator R&S SMT-06	SN: 832283/011	27-Aug-12 (in house check Oct-17)	In house check: Oct-20 In house check: Oct-20
etwork Analyzer HP 8358A	SN: US41080477	31-Mar-14 (in house check Oct-18)	In house check: Oct-19
	Name	Function	Signature
	Claudio Leubler	Laboratory Technician	[W
alibrated by:			
alibrated by:			T
alibrated by: pproved by:	Katja Pokovic	Technical Manager	felle

Certificate No: CD835V3-1003_Feb19

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 FCC ID: A3LSMF900F
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References

[1]

ANSI-C63.19-2011

American National Standard, Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids.

Methods Applied and Interpretation of Parameters:

- Coordinate System: y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes. In coincidence with the standards [1], the measurement planes (probe sensor center) are selected to be at a distance of 15 mm above the top metal edge of the dipole arms.
- Measurement Conditions: Further details are available from the hardcopies at the end of the certificate. All
 figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector
 is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a
 directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- Antenna Positioning: The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASY5 Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the accuracy.
- Feed Point Impedance and Return Loss: These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any obstacles.
- E-field distribution: E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 15 mm (in z) above the metal top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, in the plane above the dipole surface.

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%.

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Measurement Conditions

DASY system configuration, as far as not given on page 1.

DASY Version	DASY5	V52.10.2
Phantom	HAC Test Arch	
Distance Dipole Top - Probe Center	15 mm	
Scan resolution	dx, dy = 5 mm	
Frequency	835 MHz ± 1 MHz	
Input power drift	< 0.05 dB	

Maximum Field values at 835 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum
Maximum measured above high end	100 mW input power	105.2 V/m = 40.44 dBV/m
Maximum measured above low end	100 mW input power	105.1 V/m = 40.43 dBV/m
Averaged maximum above arm	100 mW input power	105.2 V/m ± 12.8 % (k=2)

Appendix (Additional assessments outside the scope of SCS 0108)

Antenna Parameters

Frequency	Return Loss	Impedance
800 MHz	17.6 dB	40.4 Ω - 7.2 jΩ
835 MHz	25.8 dB	52.2 Ω + 4.7 jΩ
880 MHz	16.9 dB	62.1 Ω - 10.5 jΩ
900 MHz	16.9 dB	52.2 Ω - 14.6 ϳΩ
945 MHz	21.6 dB	51.8 Ω + 8.3 jΩ

3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

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Impedance Measurement Plot

-		Sw <u>e</u> ep	Calibration	<u>Trace</u> <u>S</u> i	cale M <u>a</u> rker	System	Window	Help		
10.00 5.00	HESIT					1		1:	800.000000 MHz	-17.586 dB
1								3:	- 825.090000 MHz 880.000000 MHz	25.837 dB -16.937 dB
0.00								- 4:	300.000000 MH2	-16.337 dB
5.00					~		/	5	945 (00000 MHz	-21.641.dB
-10.00										1
-15.00 ,										1
						as to	+/-			
-20.00					ī ,	104	\//			ļ]
-25.00					\rightarrow	2/	17			
-30.00						1	ľ			
-35.00	Ch 4 Auro	0.0								
-40.00 Cb1+ 9	Ch 1 Avg = Start 335.000 h			J						
011.0	statt 555,000 f	v)H2						1:	Stop 800.000000 MHz	1.33500 GHz 40.420 Ω
	start 353,000 F	0H2			X			1: ≥2: 3: 4: 5:		

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DASY5 E-field Result

Date: 19.02.2019

Test Laboratory: SPEAG Lab2

DUT: HAC-Dipole 835 MHz; Type: CD835V3; Serial: CD835V3 - SN: 1003

Communication System: UID 0 - CW ; Frequency: 835 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

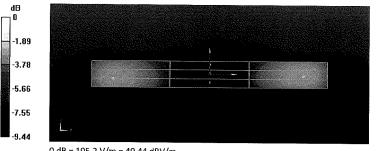
DASY52 Configuration:

- Probe: EF3DV3 SN4013; ConvF(1, 1, 1) @ 835 MHz; Calibrated: 03.01.2019
- ٠ Sensor-Surface: (Fix Surface)
- ٠ Electronics: DAE4 Sn781; Calibrated: 09.01.2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070 .
- DASY52 52.10.2(1495); SEMCAD X 14.6.12(7450)

Dipole E-Field measurement @ 835MHz/E-Scan - 835MHz d=15mm/Hearing Aid Compatibility Test (41x361x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm Reference Value = 127.3 V/m; Power Drift = 0.04 dB Applied MIF = 0.00 dBRF audio interference level = 40.44 dBV/mEmission category: M3

MIF scaled E-fi	eld	
1	Grid 2 M3 40.43 dBV/m	Grid 3 M3 40.43 dBV/m
	Grid 5 M4 35.75 dBV/m	
Grid 7 M3 40.15 dBV/m		Grid 9 M3 40.36 dBV/m



0 dB = 105.2 V/m = 40.44 dBV/m

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2/1/2019

Calibration Laboratory of

PC Test

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Accreditation No.: SCS 0108

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			o: CD1880V3-1137_Fel	b19
CALIBRATION	CERTIFICAT	E		
Object	CD1880V3 - SN	l: 1137		
Calibration procedure(s)	QA CAL-20.v7 Calibration Proc	edure for Validation Sources in a	1 -	100
		edule for validation Sources in a	0	3/19/20
Calibration date:	February 19, 20	19		
The measurements and the unce	ertainties with confidence p cted in the closed laborato	tional standards, which realize the physical un probability are given on the following pages ar pry facility: environment temperature (22 \pm 3)°(nd are part of the certificate.	
Primary Standards	D #			
Power meter NRP	SN: 104778	Cal Date (Certificate No.)	Scheduled Calibration	
Power sensor NRP-Z91	SN: 103244	04-Apr-18 (No. 217-02672/02673)	Apr-19	
		04-Apr-18 (No. 217-02672)	Apr-19	
20wer sensor NRP-791				
	SN: 103245	04-Apr-18 (No. 217-02673)	Apr-19	
Reference 20 dB Attenuator	SN: 5058 (20k)	04-Apr-18 (No. 217-02682)	Apr-19	
Reference 20 dB Attenuator Type-N mismatch combination	SN: 5058 (20k) SN: 5047.2 / 06327	04-Apr-18 (No. 217-02682) 04-Apr-18 (No. 217-02683)	Apr-19 Apr-19	
Power sensor NRP-Z91 Reference 20 dB Attenuator Type-N mismatch combination Probe EF3DV3 DAE4	SN: 5058 (20k)	04-Apr-18 (No. 217-02682)	Apr-19	
Reference 20 dB Attenuator Type-N mismatch combination Probe EF3DV3	SN: 5058 (20k) SN: 5047.2 / 06327 SN: 4013	04-Apr-18 (No. 217-02682) 04-Apr-18 (No. 217-02683) 03-Jan-19 (No. EF3-4013_Jan19) 09-Jan-19 (No. DAE4-781_Jan19)	Apr-19 Apr-19 Jan-20 Jan-20	
Reference 20 dB Attenuator Type-N mismatch combination Probe EF3DV3 DAE4 Secondary Standards	SN: 5058 (20k) SN: 5047.2 / 06327 SN: 4013 SN: 781	04-Apr-18 (No. 217-02682) 04-Apr-18 (No. 217-02683) 03-Jan-19 (No. EF3-4013_Jan19) 09-Jan-19 (No. DAE4-781_Jan19) Check Date (in house)	Apr-19 Apr-19 Jan-20 Jan-20 Scheduled Check	
Reference 20 dB Attenuator Type-N mismatch combination Probe EF3DV3 DAE4 Secondary Standards Power meter Agilent 4419B	SN: 5058 (20k) SN: 5047.2 / 06327 SN: 4013 SN: 781	04-Apr-18 (No. 217-02682) 04-Apr-18 (No. 217-02683) 03-Jan-19 (No. EF3-4013_Jan19) 09-Jan-19 (No. DAE4-781_Jan19) Check Date (in house) 09-Oct-09 (in house check Oct-17)	Apr-19 Apr-19 Jan-20 Jan-20 <u>Scheduled Check</u> In house check: Oct-20	
Reference 20 dB Attenuator Fype-N mismatch combination Probe EF3DV3 DAE4 Secondary Standards Power meter Agilent 4419B Power sensor HP E4412A	SN: 5058 (20k) SN: 5047.2 / 06327 SN: 4013 SN: 781 ID # SN: GB42420191	04-Apr-18 (No. 217-02682) 04-Apr-18 (No. 217-02683) 03-Jan-19 (No. EF3-4013_Jan19) 09-Jan-19 (No. DAE4-781_Jan19) Check Date (in house) 09-Oct-09 (in house check Oct-17) 05-Jan-10 (in house check Oct-17)	Apr-19 Apr-19 Jan-20 Jan-20 Scheduled Check In house check: Oct-20 In house check: Oct-20	
Reference 20 dB Attenuator Fype-N mismatch combination Probe EF3DV3 DAE4 Secondary Standards Power meter Agilent 4419B Power sensor HP E4412A Power sensor HP E442A	SN: 5058 (20k) SN: 5047.2 / 06327 SN: 4013 SN: 781 ID # SN: GB42420191 SN: US38485102	04-Apr-18 (No. 217-02682) 04-Apr-18 (No. 217-02683) 03-Jan-19 (No. EF3-4013_Jan19) 09-Jan-19 (No. DAE4-781_Jan19) Check Date (in house) 09-Oct-09 (in house check Oct-17) 05-Jan-10 (in house check Oct-17) 09-Oct-09 (in house check Oct-17)	Apr-19 Apr-19 Jan-20 Jan-20 Scheduled Check In house check: Oct-20 In house check: Oct-20 In house check: Oct-20	
Reference 20 dB Attenuator Type-N mismatch combination Probe EF3DV3 DAE4 Secondary Standards Power meter Agilent 4419B Power sensor HP E4412A Power sensor HP 8482A RF generator R&S SMT-06	SN: 5058 (20k) SN: 5047.2 / 06327 SN: 4013 SN: 781 ID # SN: GB42420191 SN: US38485102 SN: US37295597	04-Apr-18 (No. 217-02682) 04-Apr-18 (No. 217-02683) 03-Jan-19 (No. EF3-4013_Jan19) 09-Jan-19 (No. DAE4-781_Jan19) Check Date (in house) 09-Oct-09 (in house check Oct-17) 05-Jan-10 (in house check Oct-17)	Apr-19 Apr-19 Jan-20 Jan-20 Scheduled Check In house check: Oct-20 In house check: Oct-20	
Reference 20 dB Attenuator Type-N mismatch combination Probe EF3DV3 DAE4	SN: 5058 (20k) SN: 5047.2 / 06327 SN: 4013 SN: 781 ID # SN: GB42420191 SN: US38485102 SN: US37295597 SN: 832283/011	04-Apr-18 (No. 217-02682) 04-Apr-18 (No. 217-02683) 03-Jan-19 (No. EF3-4013_Jan19) 09-Jan-19 (No. DAE4-781_Jan19) Check Date (in house) 09-Oct-09 (in house check Oct-17) 05-Jan-10 (in house check Oct-17) 09-Oct-09 (in house check Oct-17) 27-Aug-12 (in house check Oct-17)	Apr-19 Apr-19 Jan-20 Jan-20 Scheduled Check In house check: Oct-20 In house check: Oct-20 In house check: Oct-20 In house check: Oct-20 In house check: Oct-20	
Reference 20 dB Attenuator Type-N mismatch combination Probe EF3DV3 DAE4 Secondary Standards Power meter Agilent 4419B Power sensor HP E4412A Power sensor HP 8482A RF generator R&S SMT-06	SN: 5058 (20k) SN: 5047.2 / 06327 SN: 4013 SN: 781 SN: GB42420191 SN: US38485102 SN: US37295597 SN: 832283/011 SN: US41080477	04-Apr-18 (No. 217-02682) 04-Apr-18 (No. 217-02683) 03-Jan-19 (No. EF3-4013_Jan19) 09-Jan-19 (No. DAE4-781_Jan19) Check Date (in house) 09-Oct-09 (in house check Oct-17) 05-Jan-10 (in house check Oct-17) 09-Oct-09 (in house check Oct-17) 27-Aug-12 (in house check Oct-17) 31-Mar-14 (in house check Oct-18)	Apr-19 Apr-19 Jan-20 Jan-20 Scheduled Check In house check: Oct-20 In house check: Oct-20 In house check: Oct-20 In house check: Oct-20 In house check: Oct-20	
Reference 20 dB Attenuator Fype-N mismatch combination Probe EF3DV3 DAE4 Recondary Standards Power meter Agilent 4419B Power sensor HP E4412A Power sensor HP 8482A RF generator R&S SMT-06 letwork Analyzer HP 8358A	SN: 5058 (20k) SN: 5047.2 / 06327 SN: 4013 SN: 781 ID # SN: GB42420191 SN: US38485102 SN: US37295597 SN: 832283/011 SN: US41080477 Name	04-Apr-18 (No. 217-02682) 04-Apr-18 (No. 217-02683) 03-Jan-19 (No. EF3-4013_Jan19) 09-Jan-19 (No. DAE4-781_Jan19) Check Date (in house) 09-Oct-09 (in house check Oct-17) 09-Oct-09 (in house check Oct-17) 09-Oct-09 (in house check Oct-17) 27-Aug-12 (in house check Oct-17) 31-Mar-14 (in house check Oct-18) Function	Apr-19 Apr-19 Jan-20 Jan-20 Scheduled Check In house check: Oct-20 In house check: Oct-20 In house check: Oct-20 In house check: Oct-20 In house check: Oct-20	

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Calibration Laboratory of Schmid & Partner

Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland



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Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS)

The Swiss Accreditation Service is one of the signatories to the EA Multilateral Agreement for the recognition of calibration certificates

References

[1] ANSI-C63.19-2011

American National Standard, Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids,

Methods Applied and Interpretation of Parameters:

- Coordinate System: y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes. In coincidence with the standards [1], the measurement planes (probe sensor center) are selected to be at a distance of 15 mm above the top metal edge of the dipole arms.
- Measurement Conditions: Further details are available from the hardcopies at the end of the certificate. All
 figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector
 is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a
 directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- Antenna Positioning: The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASY5 Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the accuracy.
- Feed Point Impedance and Return Loss: These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any obstacles.
- E-field distribution: E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 15 mm (in z) above the metal top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, in the plane above the dipole surface.

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%.

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Measurement Conditions

DASY system configuration, as far as not given on page 1.

DASY Version	DASY5	V52.10.2
Phantom	HAC Test Arch	
Distance Dipole Top - Probe Center	15 mm	
Scan resolution	dx, dy = 5 mm	
Frequency	1730 MHz ± 1 MHz 1880 MHz ± 1 MHz	
Input power drift	< 0.05 dB	······································

Maximum Field values at 1730 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum
Maximum measured above high end	100 mW input power	95.0 V/m = 39.55 dBV/m
Maximum measured above low end	100 mW input power	94.9 V/m = 39.55 dBV/m
Averaged maximum above arm	100 mW input power	95.0 V/m ± 12.8 % (k=2)

Maximum Field values at 1880 MHz

.

E-field 15 mm above dipole surface	condition	Interpolated maximum
Maximum measured above high end	100 mW input power	88.9 V/m = 38.98 dBV/m
Maximum measured above low end	100 mW input power	86.6 V/m = 38.75 dBV/m
Averaged maximum above arm	100 mW input power	87.8 V/m ± 12.8 % (k=2)

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Appendix (Additional assessments outside the scope of SCS 0108)

Antenna Parameters

Nominal Frequencies

Frequency	Return Loss	Impedance	
1730 MHz	22.5 dB	54.4 Ω + 6.5 jΩ	
1880 MHz	21.1 dB	55.9 Ω + 7.2 jΩ	
1900 MHz	21.0 dB	59.0 Ω + 3.6 jΩ	
1950 MHz	27.3 dB	53.0 Ω - 3.3 jΩ	
2000 MHz	20.3 dB	42.4 Ω + 4.8 jΩ	

3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

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Impedance Measurement Plot

le ⊻iew <u>C</u> hannel Sw <u>e</u> ep Calji	bration <u>T</u> race <u>S</u> cale i	Marker System <u>W</u> inc	łow <u>H</u> elp		
7.00]	I I	1:	1.‡30000 GHz	-22,459 dE
2.00				1.880000 GHz	21.146.66
3.00			3:	4.900000 GHz	-21.002.08
8.00			-Arma	1.950000 GHz	-27.332 dt
				2	20.275.df
13.00					
18.00					
23.00		An A	l l		
		7 3 1 13			
28,00					
83.00	Y	4∨			
8.00					
43,00 Ch 1 Avg = 20					
Ch1: Start 1,38000 GHz		<pre></pre>	1.		
			1:	1.730000 GHz	54.408 Ω
		76	1:		54.408 Ω 6.5341 Ω
Christali 138000 Urz			>2:	1.730000 GHz 601.12 pH	54.408 Ω 6.5341 Ω 55.885 Ω
CIT: Stall 1.35000 GF2				1.730000 GHz 601.12 pH 1.880000 GHz 609.67 pH 1.900000 GHz	54.408 Ω 6.5341 Ω 55.885 Ω 7.2016 Ω 59.017 Ω
CIT: Stall 1.35000 UR2	Á		>2:	1.730000 GHz 601.12 pH 1.880000 GHz 609.67 pH 1.900000 GHz 303.81 pH	2.38000 GHz 54.408 Ω 6.5341 Ω 55.885 Ω 7.2016 Ω 59.017 Ω 3.6269 Ω
CIT: Statt 1.35000 UT2	Å		>2:	1.730000 GHz 601.12 pH 1.880000 GHz 609.67 pH 1.900600 GHz 303.81 pH 1.950000 GHz	54.408 Ω 6.5341 Ω 55.885 Ω 7.2016 Ω 59.017 Ω 3.6269 Ω 52.957 Ω
CIT: Statt 1.35000 UT2			>2: 3: 4:	1.730000 GHz 601.12 pH 1.880000 GHz 603.67 pH 1.300600 GHz 303.81 pH 1.950000 GHz 24.752 pF	54.408 Ω 6.5341 Ω 55.885 Ω 7.2016 Ω 59.017 Ω 3.6269 Ω 52.957 Ω -3.2975 Ω
CHI Statt 133000 UR2	Á		>2:	1.730000 GHz 601.12 pH 1.80000 GHz 609.67 pH 1.900000 GHz 303.81 pH 1.950000 GHz 24.752 pF 2.00000 GHz	54.408 Ω 6.5341 Ω 55.885 Ω 7.2016 Ω 59.017 Ω 3.6269 Ω 52.957 Ω -3.2975 Ω 42.436 Ω
	<u> </u>		>2: 3: 4:	1.730000 GHz 601.12 pH 1.880000 GHz 603.67 pH 1.300600 GHz 303.81 pH 1.950000 GHz 24.752 pF	54.408 Ω 6.5341 Ω 55.885 Ω 7.2016 Ω 59.017 Ω 3.6269 Ω 52.957 Ω -3.2975 Ω
			>2: 3: 4:	1.730000 GHz 601.12 pH 1.80000 GHz 609.67 pH 1.900000 GHz 303.81 pH 1.950000 GHz 24.752 pF 2.00000 GHz	54.408 Ω 6.5341 Ω 55.885 Ω 7.2016 Ω 59.017 Ω 3.6269 Ω 52.957 Ω -3.2975 Ω 42.436 Ω
	<u> </u>		>2: 3: 4:	1.730000 GHz 601.12 pH 1.80000 GHz 609.67 pH 1.900000 GHz 303.81 pH 1.950000 GHz 24.752 pF 2.00000 GHz	54.408 Ω 6.5341 Ω 55.885 Ω 7.2016 Ω 59.017 Ω 3.6269 Ω 52.957 Ω -3.2975 Ω 42.436 Ω
			>2: 3: 4:	1.730000 GHz 601.12 pH 1.80000 GHz 609.67 pH 1.900000 GHz 303.81 pH 1.950000 GHz 24.752 pF 2.00000 GHz	54.408 Ω 6.5341 Ω 55.885 Ω 7.2016 Ω 59.017 Ω 3.6269 Ω 52.957 Ω -3.2975 Ω 42.436 Ω
Ch 1 Avg = 20			>2: 3: 4:	1.730000 GHz 601.12 pH 1.880000 GHz 609.67 pH 1.90000 GHz 303.81 pH 1.950000 GHz 24.752 pF 2.000000 GHz 383.29 pH	54.408 Ω 6.534 Ω 55.885 Ω 7.2016 Ω 53.025 Ω 52.957 Ω -3.2375 Ω -42.436 Ω 4.8166 Ω
			>2: 3: 4:	1.730000 GHz 601.12 pH 1.880000 GHz 609.67 pH 1.90000 GHz 303.81 pH 1.950000 GHz 24.752 pF 2.000000 GHz 383.29 pH	54.408 Ω 6.5341 Ω 55.885 Ω 7.2016 Ω 59.017 Ω 3.6269 Ω 52.957 Ω -3.2975 Ω 42.436 Ω

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DASY5 E-field Result

Date: 19.02.2019

Test Laboratory: SPEAG Lab2

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: CD1880V3 - SN: 1137

Communication System: UID 0 - CW ; Frequency: 1880 MHz, Frequency: 1730 MHz Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY52 Configuration:

- Probe: EF3DV3 SN4013; ConvF(1, 1, 1) @ 1880 MHz, ConvF(1, 1, 1) @ 1730 MHz; Calibrated: 03.01.2019
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 09.01.2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- DASY52 52.10.2(1495); SEMCAD X 14.6.12(7450)

Dipole E-Field measurement @ 1880MHz/E-Scan - 1880MHz d=15mm/Hearing Aid Compatibility Test (41x181x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 151.5 V/m; Power Drift = 0.02 dB Applied MIF = 0.00 dB RF audio interference level = 38.98 dBV/m Emission category: M2

MIF scaled E-field

Grid 1 M2	Grid 2 M2	Grid 3 M2
38.55 dBV/m	38.98 dBV/m	38.93 dBV/m
Grid 4 M2	Grid 5 M2	Grid 6 M2
35.71 dBV/m	35.97 dBV/m	35.96 dBV/m
Grid 7 M2	Grid 8 M2	Grid 9 M2
38.31 dBV/m	38.75 dBV/m	38.73 dBV/m

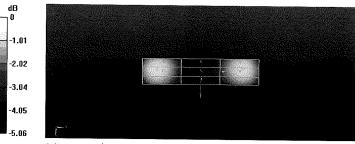
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Dipole E-Field measurement @ 1880MHz /E-Scan - 1730MHz d=15mm/Hearing Aid Compatibility Test (41x181x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 165.0 V/m; Power Drift = 0.03 dB Applied MIF = 0.00 dB RF audio interference level = 39.55 dBV/m Emission category: M2

	Grid 2 M2 39.55 dBV/m	Grid 3 M2 39.51 dBV/m
	Grid 5 M2	
36.57 dBV/m	36.95 dBV/m	36.95 dBV/m
Grid 7 M2	Grid 8 M2	Grid 9 M2
39.05 dBV/m	39.55 dBV/m	39.53 dBV/m



0 dB = 88.87 V/m = 38.98 dBV/m

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Servizio svizzero di taratura Swiss Calibration Service

Accreditation No.: SCS 0108

Certificate No: CD2600V3-1012_Feb19

CALIBRATION (CERTIFICAT		
Object	CD2600V3 - SN	: 1012	
Calibration procedure(s)	QA CAL-20.v7 Calibration Proc	edure for Validation Sources in ai	ir /0.4 3/19/2
			3/19/2
Calibration date:	February 19, 20 ⁻	19	
The measurements and the unce	rtainties with confidence p	ional standards, which realize the physical un robability are given on the following pages ar ry facility: environment temperature (22 ± 3)°(nd are part of the certificate.
Primary Standards			
Power meter NRP	SN: 104778	Cal Date (Certificate No.)	Scheduled Calibration
Power sensor NRP-Z91	SN: 103244	04-Apr-18 (No. 217-02672/02673)	Apr-19
Power sensor NRP-Z91	SN: 103245	04-Apr-18 (No. 217-02672)	Apr-19
Reference 20 dB Attenuator	SN: 5058 (20k)	04-Apr-18 (No. 217-02673)	Apr-19
Type-N mismatch combination	SN: 5047.2 / 06327	04-Apr-18 (No. 217-02682)	Apr-19
Probe EF3DV3	SN: 4013	04-Apr-18 (No. 217-02683)	Apr-19
DAE4	SN: 781	03-Jan-19 (No. EF3-4013_Jan19) 09-Jan-19 (No. DAE4-781_Jan19)	Jan-20 Jan-20
Secondary Standards	ID#	Check Date (in house)	Scheduled Check
Power meter Agilent 4419B	SN: GB42420191	09-Oct-09 (in house check Oct-17)	In house check: Oct-20
Power sensor HP E4412A	SN: US38485102	05-Jan-10 (in house check Oct-17)	In house check: Oct-20
Power sensor HP 8482A	SN: US37295597	09-Oct-09 (in house check Oct-17)	In house check: Oct-20
RF generator R&S SMT-06	SN: 832283/011	27-Aug-12 (in house check Oct-17)	In house check: Oct-20
Network Analyzer HP 8358A	SN: US41080477	31-Mar-14 (in house check Oct-18)	In house check: Oct-19
Calibrated by:	Name	Function	Signature
Cumbrated by.	Claudio Leubler	Laboratory Technician	VKI
Approved by:	Katja Pokovic	Technical Manager	Lelle
		full without written approval of the laboratory.	Issued: February 20, 2019

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References

[1] ANSI-C63.19-2011

American National Standard, Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids,

Methods Applied and Interpretation of Parameters:

- Coordinate System: y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes. In coincidence with the standards [1], the measurement planes (probe sensor center) are selected to be at a distance of 15 mm above the top metal edge of the dipole arms.
- Measurement Conditions: Further details are available from the hardcopies at the end of the certificate. All
 figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector
 is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a
 directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- Antenna Positioning: The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASY5 Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the accuracy.
- Feed Point Impedance and Return Loss: These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any obstacles.
- E-field distribution: E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 15 mm (in z) above the metal top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, in the plane above the dipole surface.

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%.

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Measurement Conditions

DASY system configuration, as far as not given on page 1.

DASY Version	DASY5	V52.10.2
Phantom	HAC Test Arch	
Distance Dipole Top - Probe Center	15 mm	
Scan resolution	dx, dy = 5 mm	·····
Frequency	2600 MHz ± 1 MHz	
Input power drift	< 0.05 dB	

Maximum Field values at 2600 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum
Maximum measured above high end	100 mW input power	85.6 V/m = 38.65 dBV/m
Maximum measured above low end	100 mW input power	84.7 V/m = 38.56 dBV/m
Averaged maximum above arm	100 mW input power	85.2 V/m ± 12.8 % (k=2)

Appendix (Additional assessments outside the scope of SCS 0108)

Antenna Parameters

Frequency	Return Loss	
2450 MHz	20.5 dB	42.7 Ω - 4.8 jΩ
2550 MHz	32.1 dB	48.9 Ω + 2.2 jΩ
2600 MHz	39.6 dB	50.3 Ω + 1.0 jΩ
2650 MHz	30.4 dB	53.0 Ω + 0.9 jΩ
2750 MHz	20.9 dB	48.9 Ω - 8.9 jΩ

3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

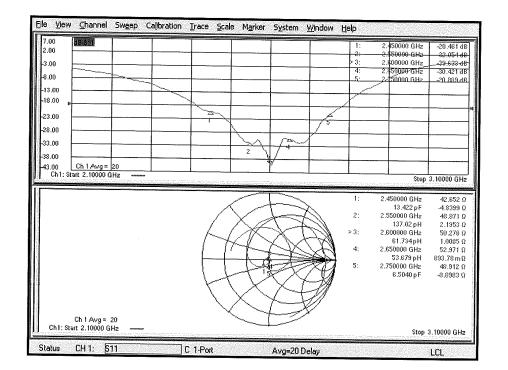
After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

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Impedance Measurement Plot



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DASY5 E-field Result

Date: 19.02.2019

Test Laboratory: SPEAG Lab2

DUT: HAC Dipole 2600 MHz; Type: CD2600V3; Serial: CD2600V3 - SN: 1012

Communication System: UID 0 - CW ; Frequency: 2600 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

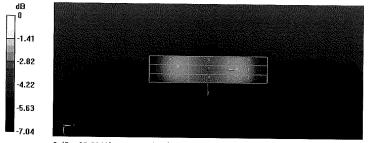
DASY52 Configuration:

- Probe: EF3DV3 SN4013; ConvF(1, 1, 1) @ 2600 MHz; Calibrated: 03.01.2019
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 09.01.2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- DASY52 52.10.2(1495); SEMCAD X 14.6.12(7450)

Dipole E-Field measurement @ 2600MHz - with/E-Scan - 2600MHz d=15mm/Hearing Aid Compatibility Test (41x181x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 62.82 V/m; Power Drift = -0.01 dB Applied MIF = 0.00 dB RF audio interference level = 38.65 dBV/m Emission category: M2

MIF scaled E-field

Grid 1 M2	Grid 2 M2	Grid 3 M2
38.09 dBV/m	38.56 dBV/m	38.54 dBV/m
Grid 4 M2	Grid 5 M2	Grid 6 M2
37.82 dBV/m	38.06 dBV/m	38.02 dBV/m
Grid 7 M2	Grid 8 M2	Grid 9 M2
38.36 dBV/m	38.65 dBV/m	38.56 dBV/m



0 dB = 85.60 V/m = 38.65 dBV/m

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16. CONCLUSION

The measurements indicate that the wireless communications device complies with the HAC limits specified in accordance with the ANSI C63.19 Standard and FCC WT Docket No. 01-309 RM-8658. Precise laboratory measures were taken to assure repeatability of the tests. The tested device complies with the requirements in respect to all parameters specific to the test. The test results and statements relate only to the item(s) tested.

Please note that the M-rating for this equipment only represents the field interference possible against a hypothetical and typical hearing aid. The measurement system and techniques presented in this evaluation are proposed in the ANSI standard as a means of best approximating wireless device compatibility with a hearing-aid. The literature is under continual re-construction.

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